



# Photoemission Study on Topological Semimetals

SPICE Workshop

New Paradigms in Dirac-Weyl Nanoelectronics

June 15<sup>th</sup>, 2016

Zhongkai Liu

# ARPES team



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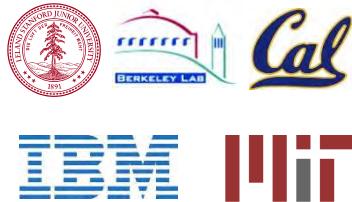


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**Zhongkai Liu,  
Meixiao Wang, Juan Jiang, Chengwei Wang, Guanghao Hong**

# Collaborators



Theory: **Shoucheng Zhang, Xiaoliang Qi**  
Experiments: **Zhi-Xun Shen, Ian Fisher, Yi Cui, Aharon Kapitulnik  
James Analytis**  
Beamlines: **Sung-Kwan Mo, Zahid Hussain  
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**Takao Sasagawa**



**Laurens Molenkamp, Christopher Brune  
Claudia Felser, Binghai Yan  
Alexi Barinov, Moritz Hoesch, Pavel Dudin**

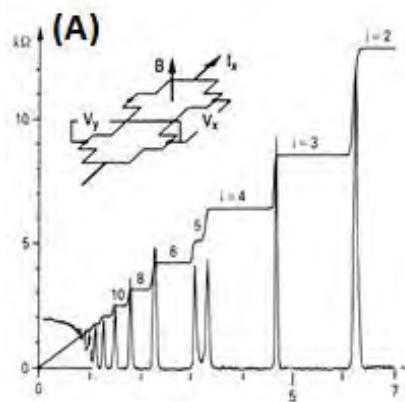


# Outline

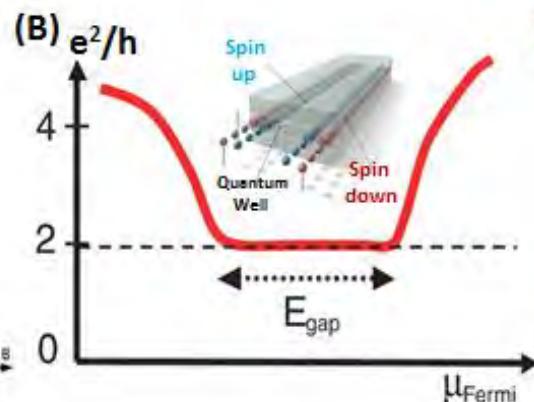
- Probing the electronic structure of TI with ARPES
- ARPES study on Dirac/Weyl Semimetal
- Multi Dimensional ARPES techniques

# Topological Quantum Materials

QH Insulator



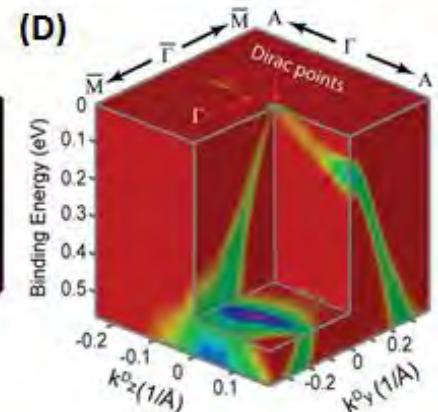
QSH Insulator



Topological  
Insulator



Topological  
Semimetal



1980

2006-2013

2014

Topological invariant:  
“first Chern number”

Topological invariant:  
“ $Z_2$  invariant”

Topological invariant:  
“Chern number (of some sort?)”

# Why “topological”

Topologically distinct objects



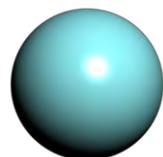
Regular insulator



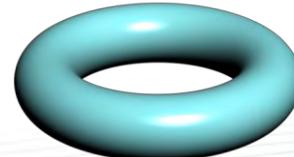
Topological insulator



Sphere

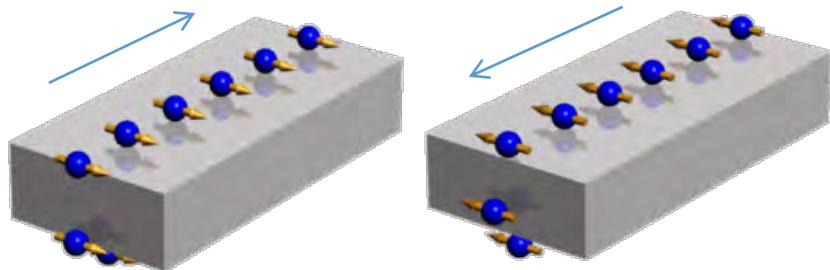


Torus

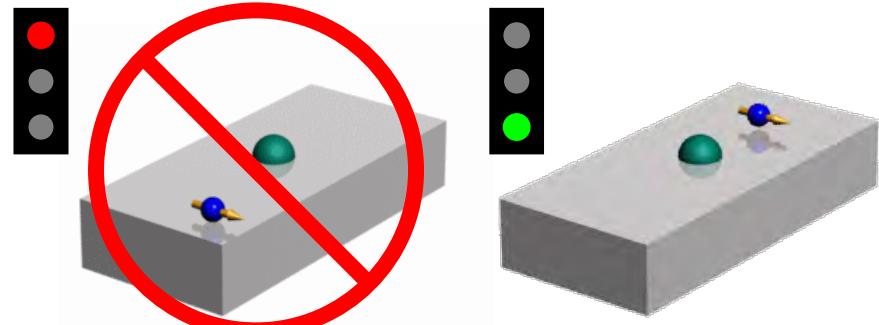


# Unique surface state properties of TIs

“Locking” between current & spin

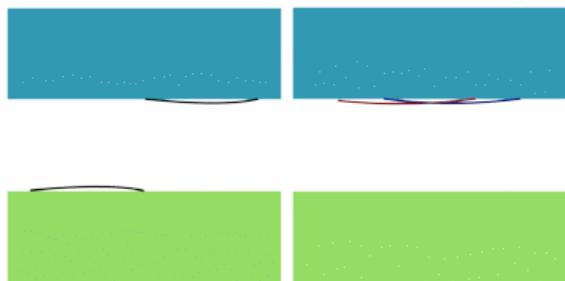


No back-scattering rule  
(by non-magnetic impurities)

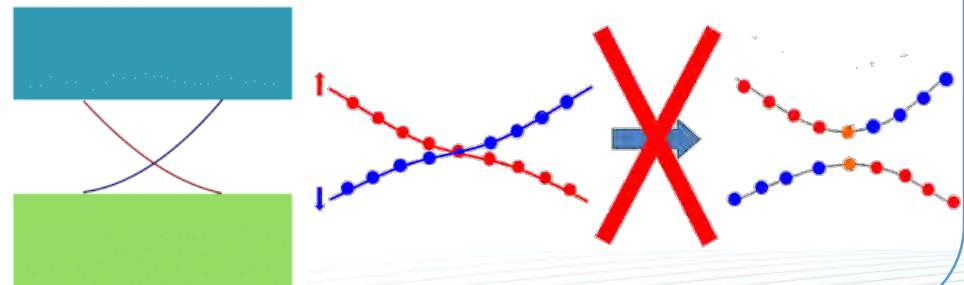


Robustness of the topological surface state

Surface state in regular insulator  
**vulnerable**



Surface state in topological insulator  
**robust**

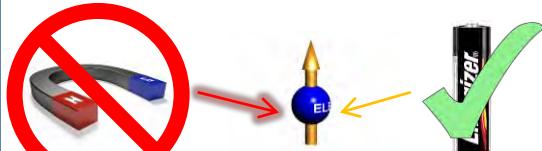


# Application potentials

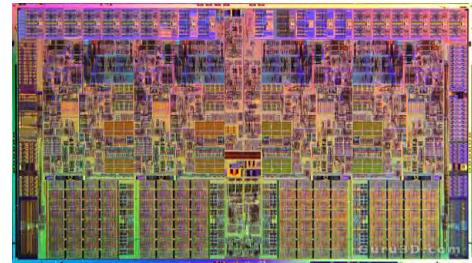
**Electronics more efficient  
(Longer functional time)**



**Spintronics without magnet  
(Faster & less consumption)**



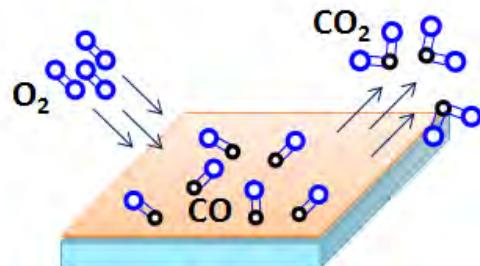
**Higher density integrated circuit**



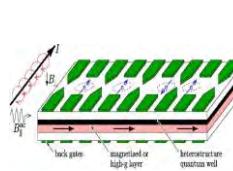
**Thermoelectric  
generators**



**New catalysts**



**Quantum computation**



# How to find TIs

Search for the unique band structure

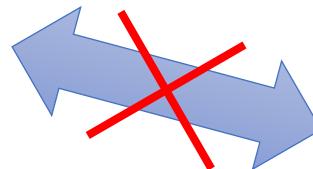
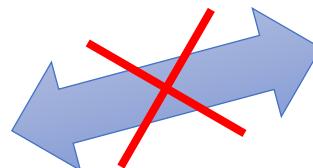
**Topological insulator**



**Regular conductor**



**Regular insulator**

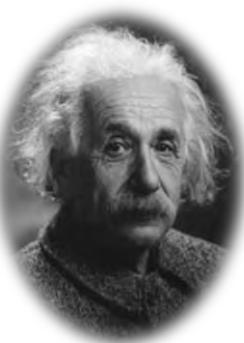


# How to “see” band structures

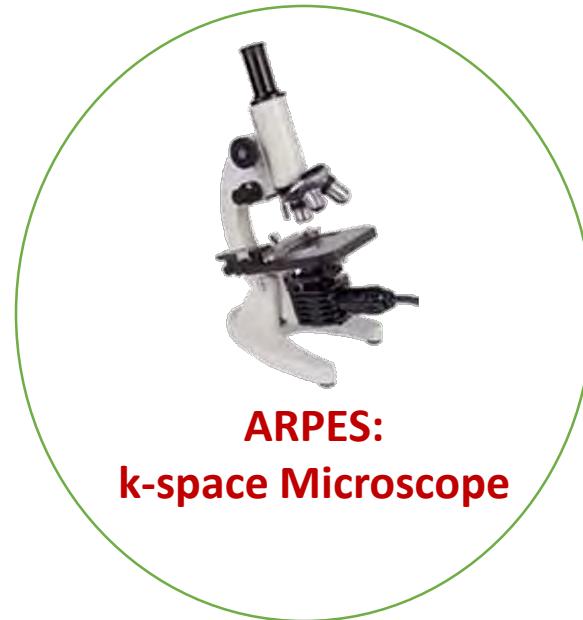
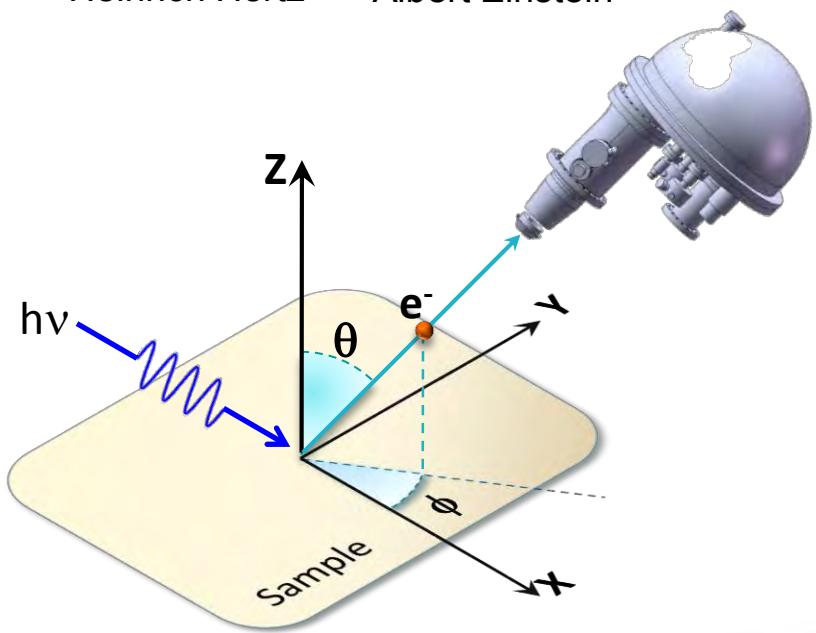
Angle Resolved Photoemission Spectroscopy (ARPES)



Heinrich Hertz



Albert Einstein



Energy Conservation

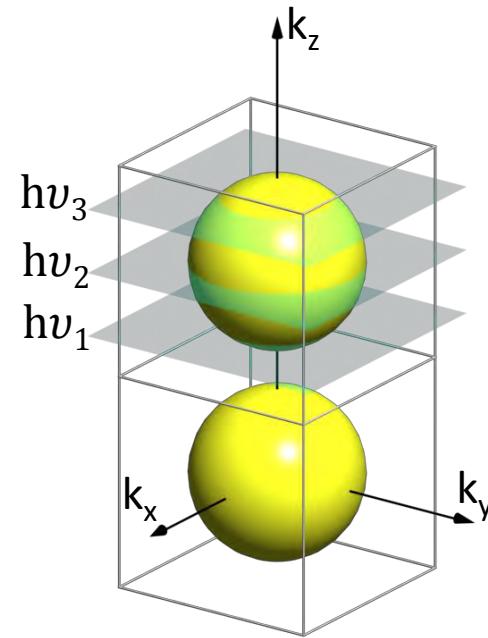
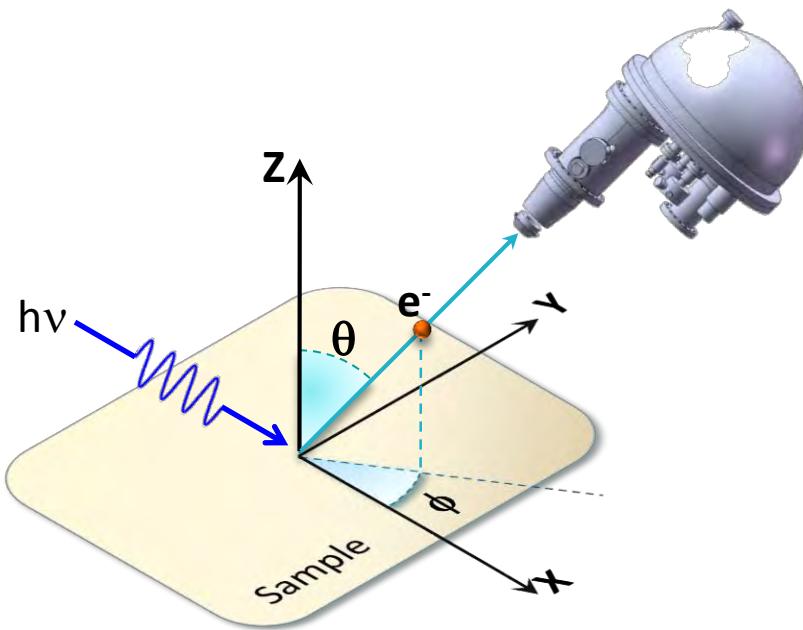
$$E_B = h\nu - E_{\text{kin}} - \Phi$$

Momentum Conservation

$$\mathbf{K}_{\parallel} = \mathbf{k}_{\parallel} + \mathbf{G}_{\parallel}$$

# How to determine $k_z$ ?

## Photon energy dependent ARPES measurement



$$E_k = h\nu - w - E_B$$

In vacuum:

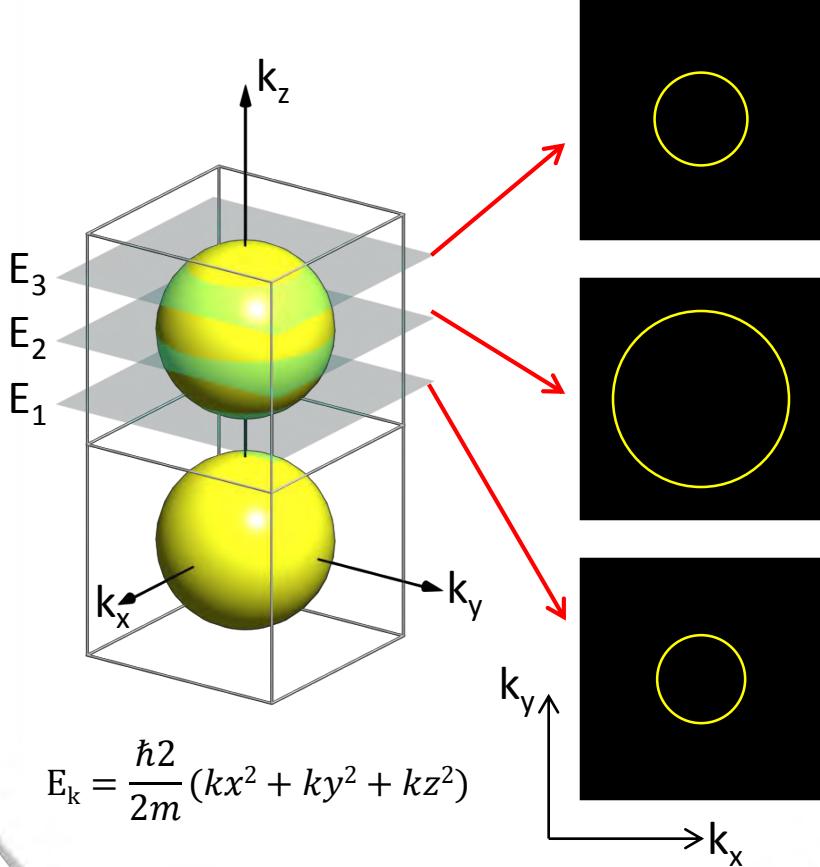
$$k^V_x = \frac{\sqrt{2m_e E_k}}{\hbar} \sin(\theta) \cos(\phi)$$
$$k^V_y = \frac{\sqrt{2m_e E_k}}{\hbar} \sin(\theta) \sin(\phi)$$
$$k^V_z = \frac{\sqrt{2m_e E_k}}{\hbar} \cos(\theta)$$

In crystal:

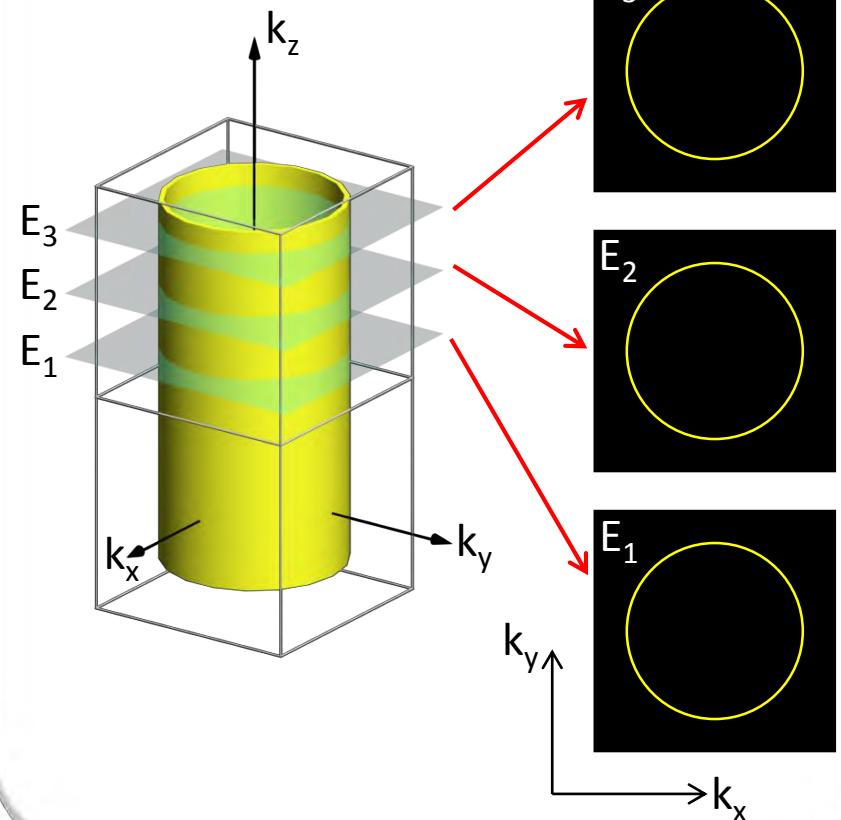
$$k_x = \frac{\sqrt{2m_e E_k}}{\hbar} \sin(\theta) \cos(\phi) = k^V_x$$
$$k_y = \frac{\sqrt{2m_e E_k}}{\hbar} \sin(\theta) \sin(\phi) = k^V_y$$
$$k_z = \sqrt{\frac{2m_e}{\hbar^2} (E_k + V_0) - \frac{2m_e E_k}{\hbar^2} \sin^2 \theta} \neq k^V_z$$

# How to discriminate bulk & surface?

**3D FS**  
(e.g. FS from bulk state)



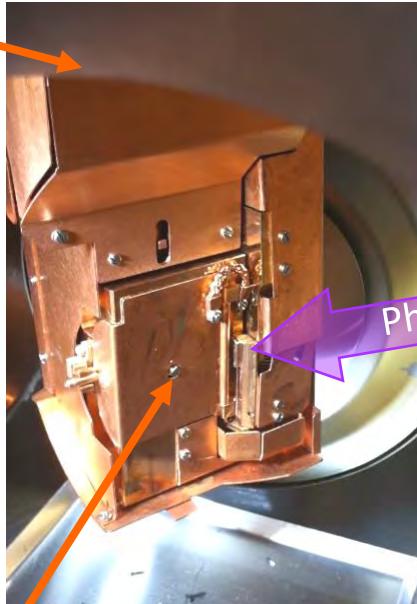
**2D FS**  
(e.g. FS from surface state)



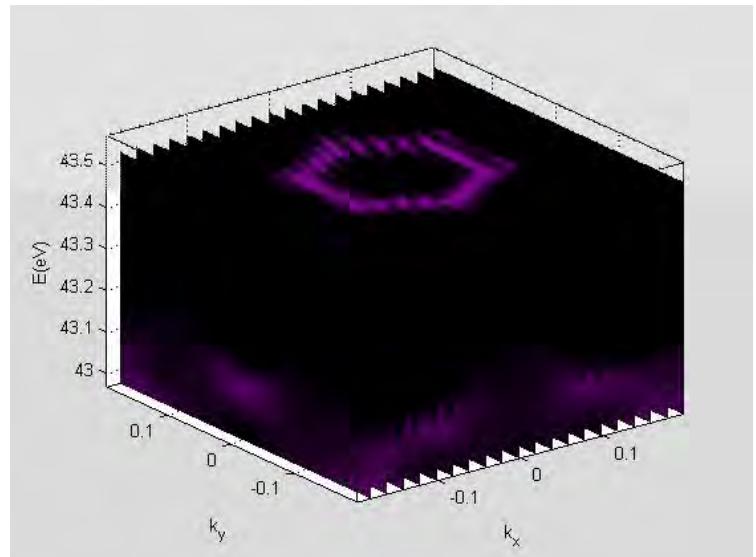
# Modern ARPES

Experimental setup

Experiment  
Chamber



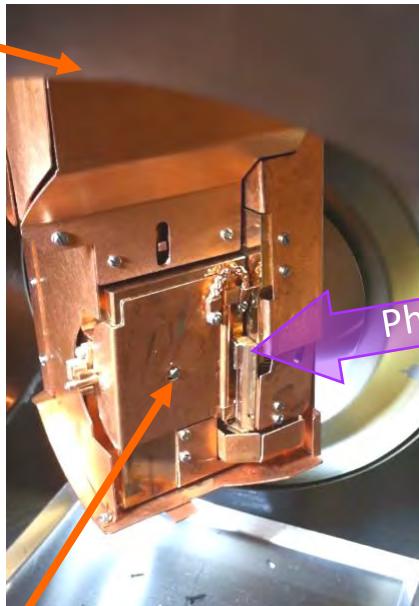
Data acquired



# Modern ARPES

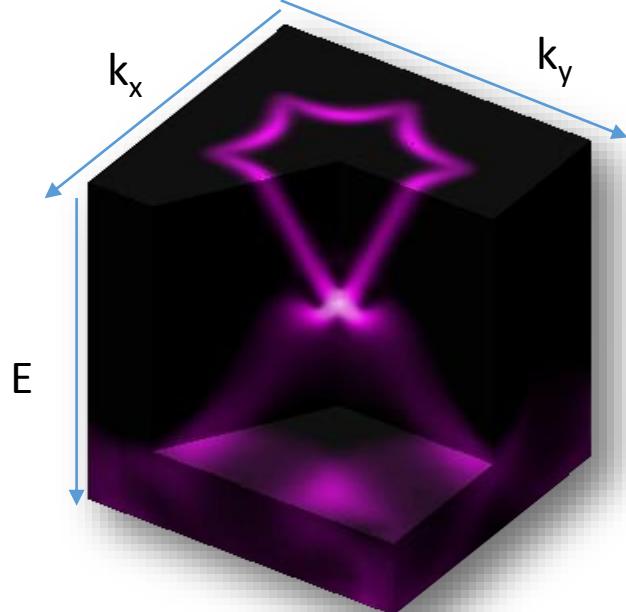
Experimental setup

Experiment  
Chamber



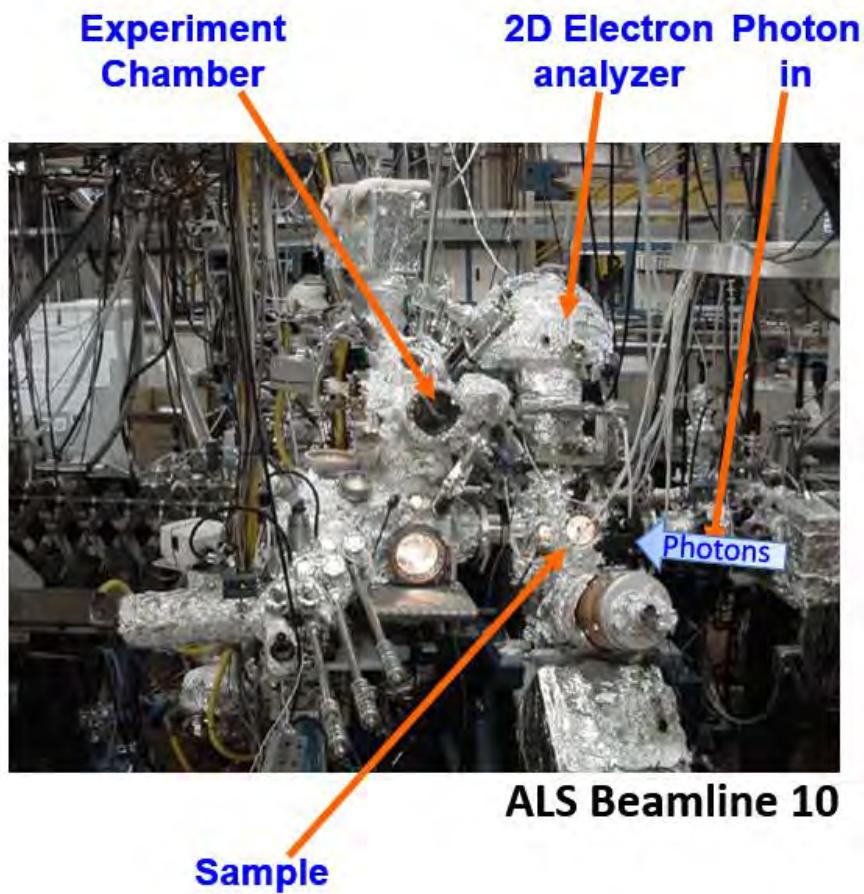
Sample

Data acquired

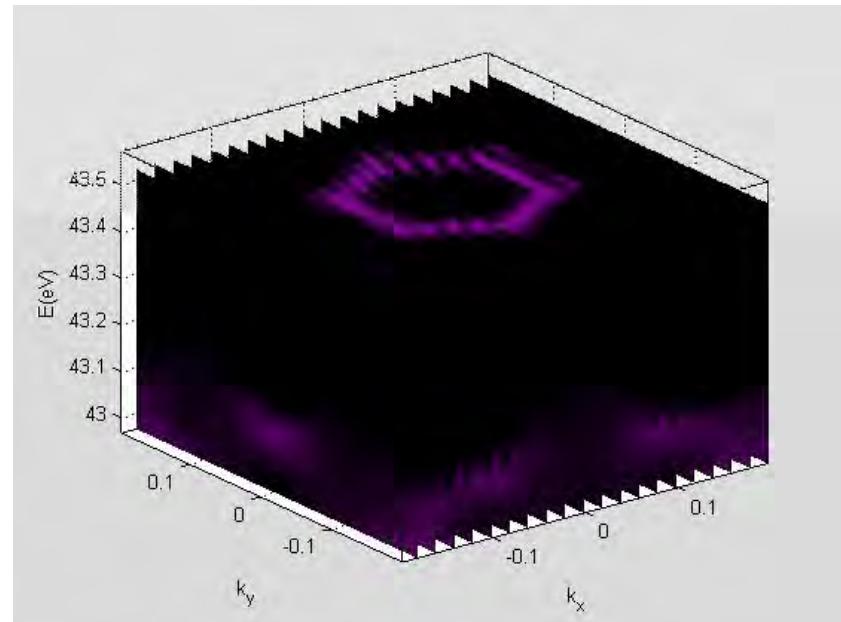


# Or Alternatively...

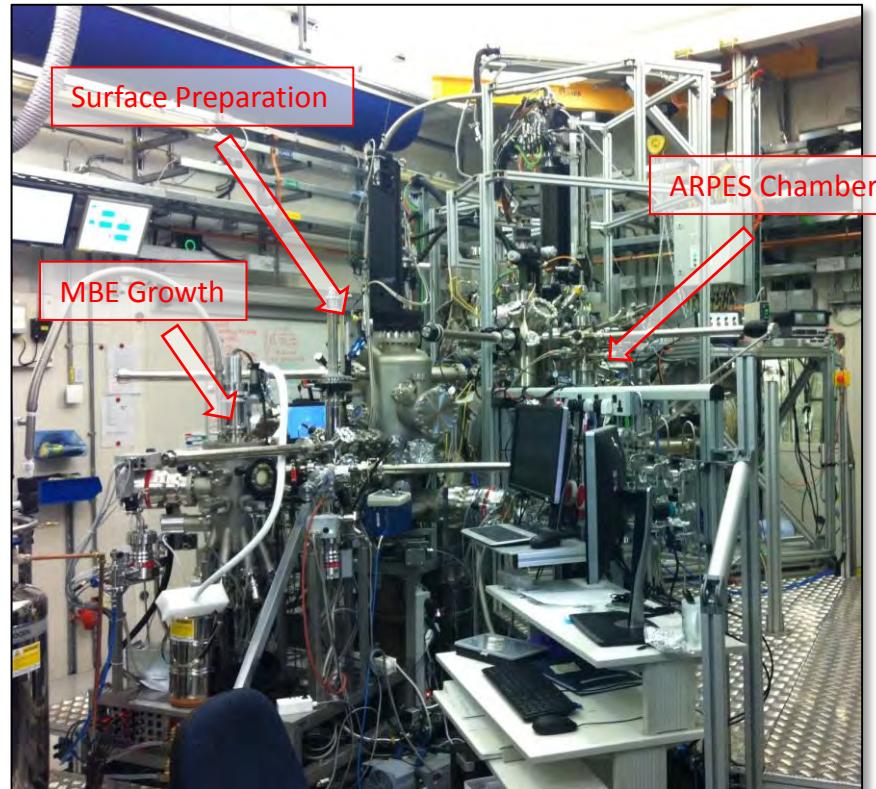
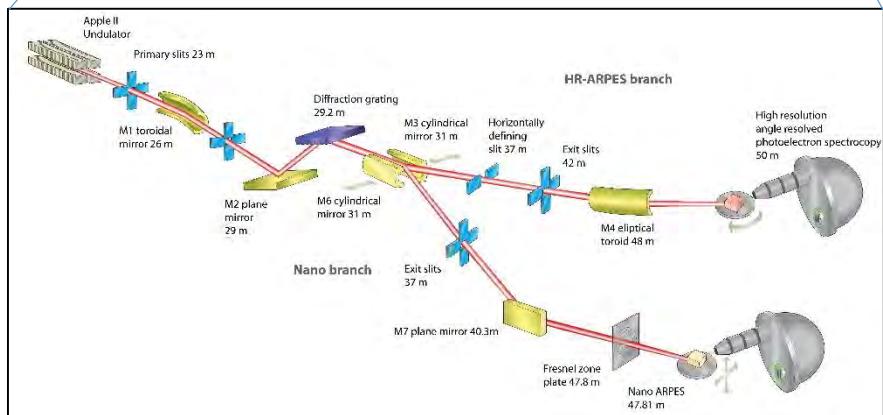
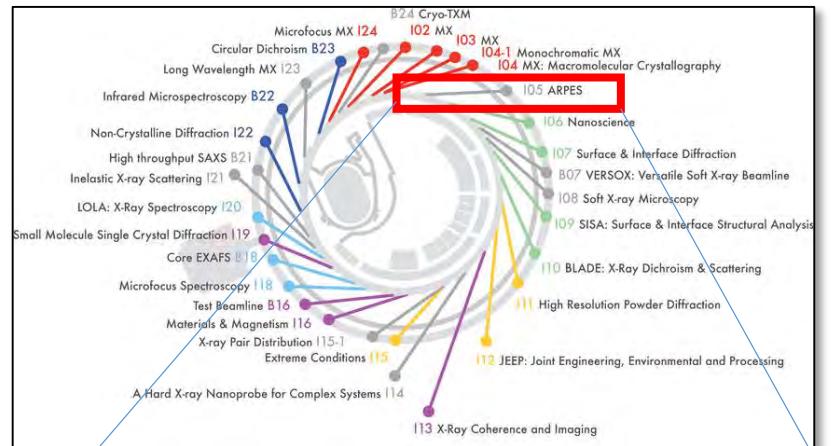
Experimental setup



Data acquired



# Synchrotron based ARPES station



hv range: 18~240eV  
 $\Delta E=2\sim10\text{meV}$  (hv: 18~80eV)

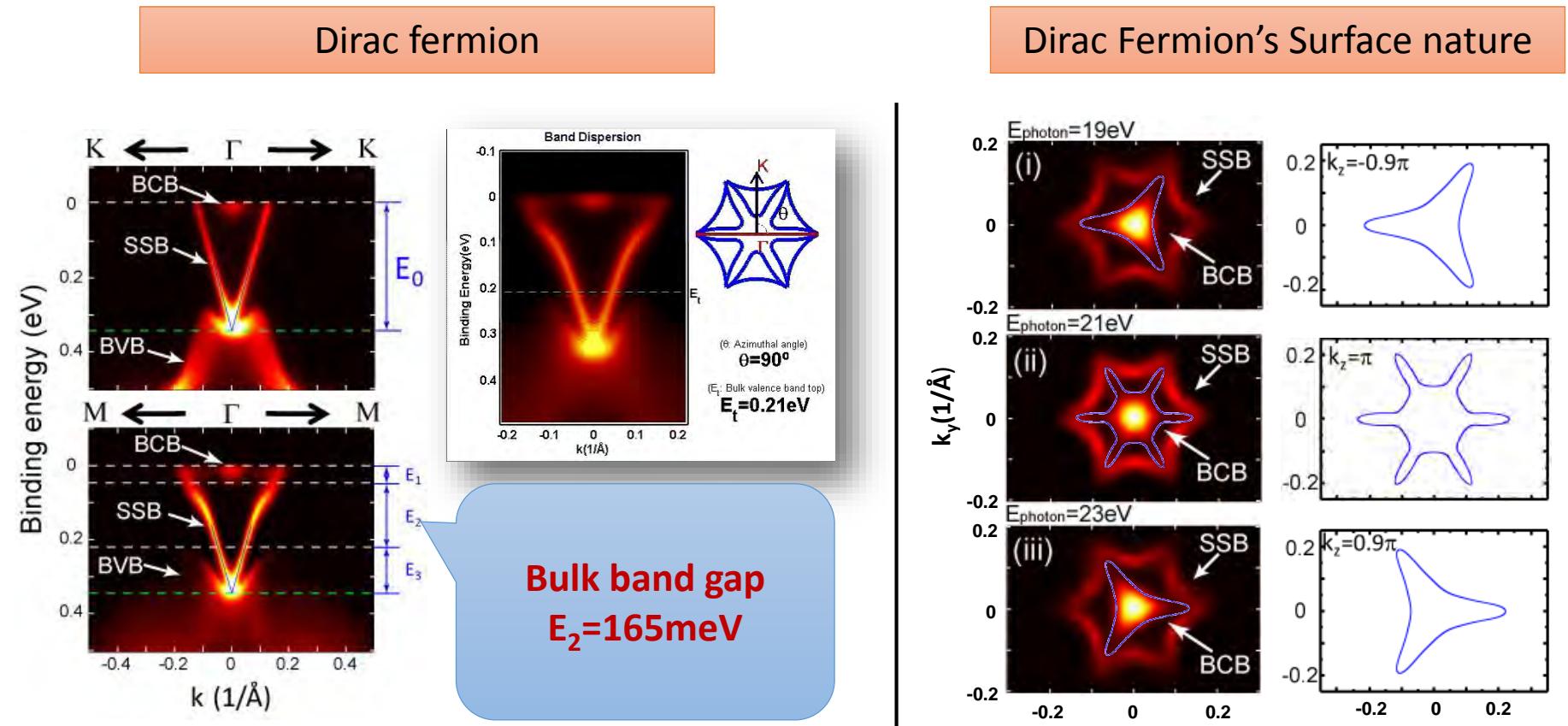
Temperature: 6K~RT

6 axis manipulator

Beamspot 50x50  $\mu\text{m}^2$

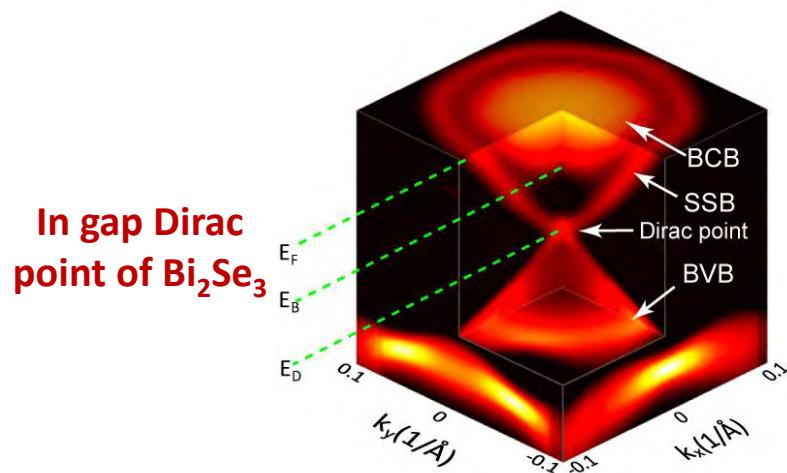
# Realization of TI state in $\text{Bi}_2\text{Te}_3$

Y. L. Chen, et. al., *Science* 325, 178 (2009)

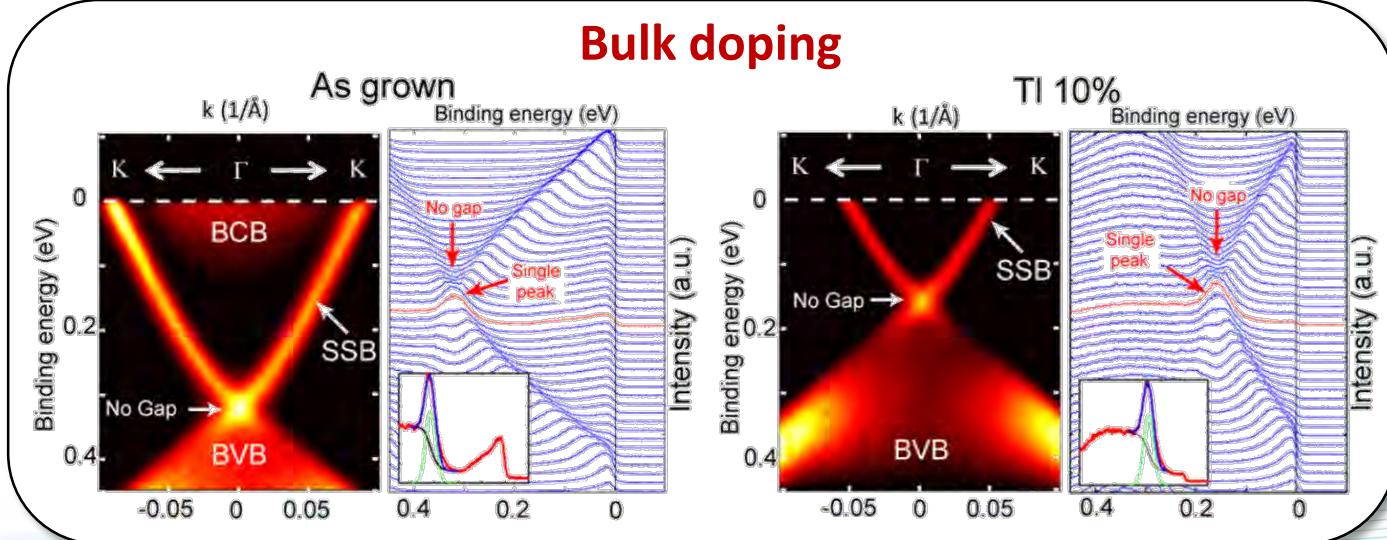
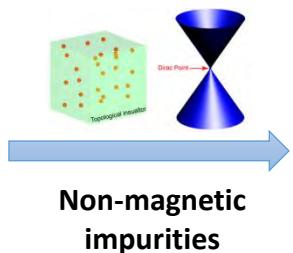
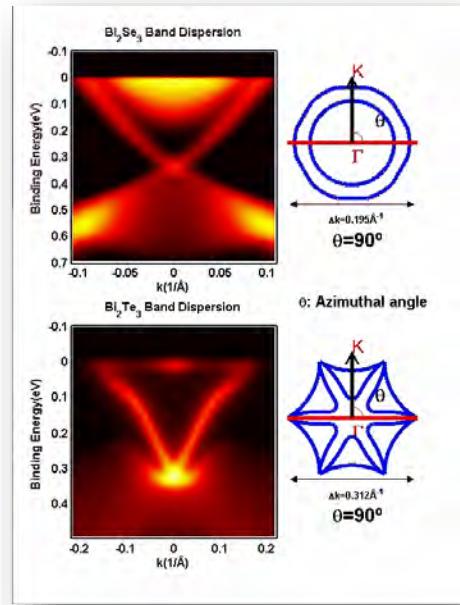


# TRS protection – bulk doping

Y. L. Chen, et. al., Science 329, 659 (2010)

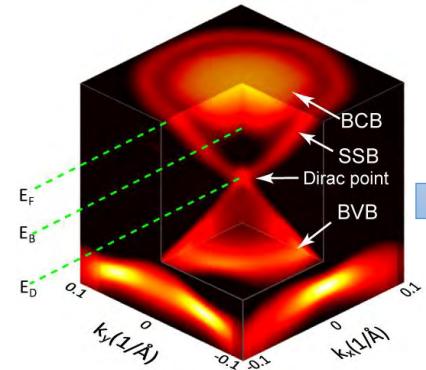


Compare to  $\text{Bi}_2\text{Te}_3$

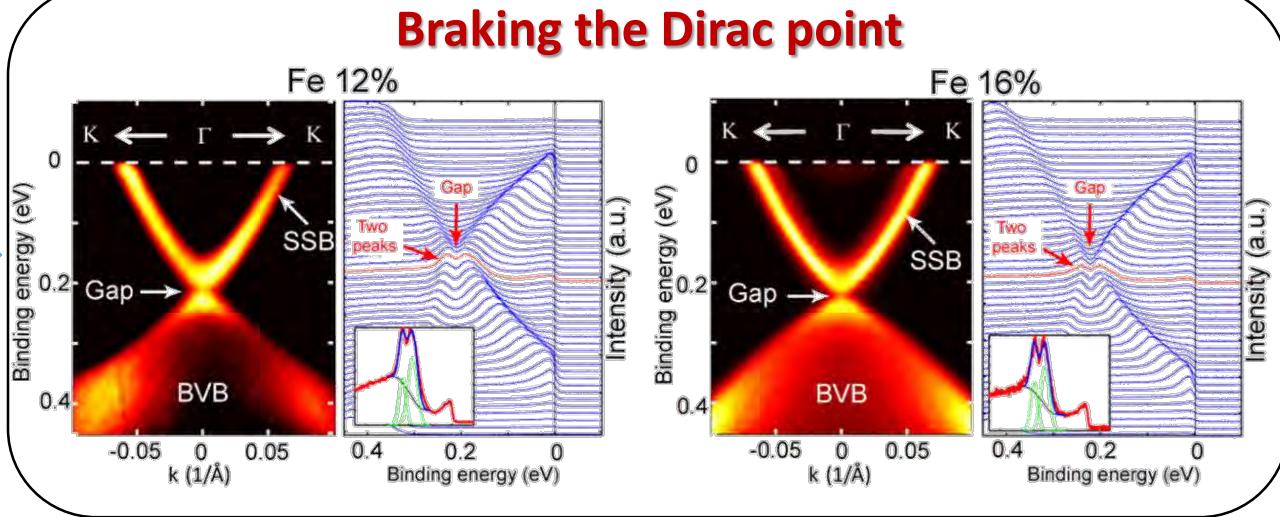


# Dirac fermion becomes massive

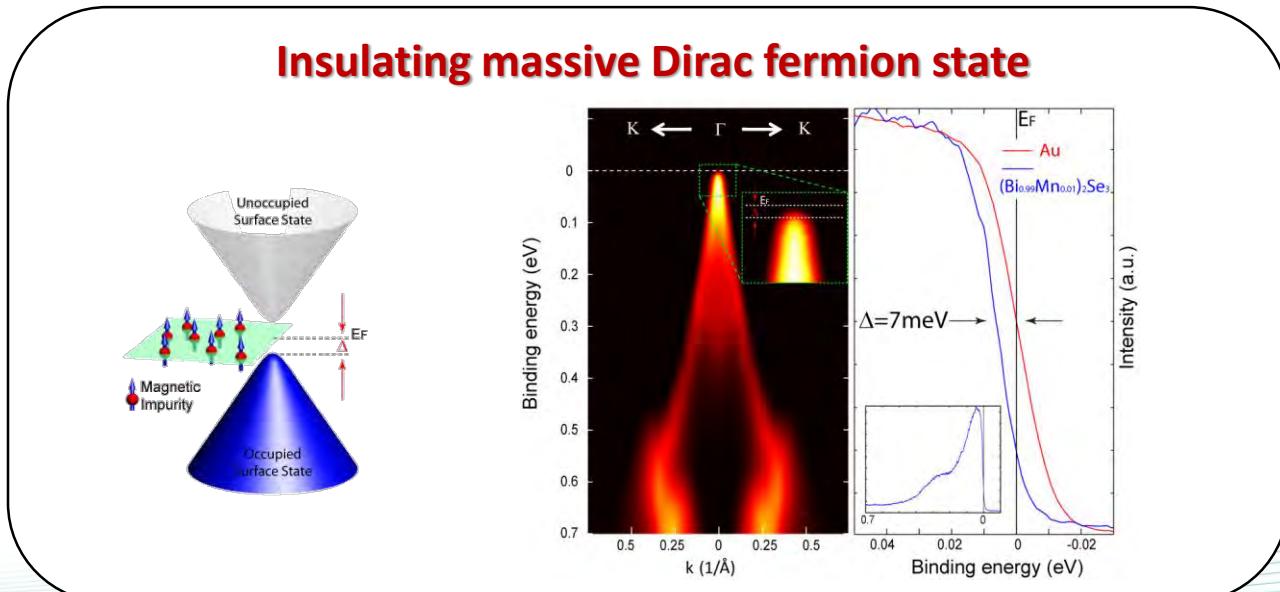
Y. L. Chen, et. al., Science 329, 659 (2010)



Magnetic impurities



Charge tuning:  
Move  $E_F$  into Dirac gap

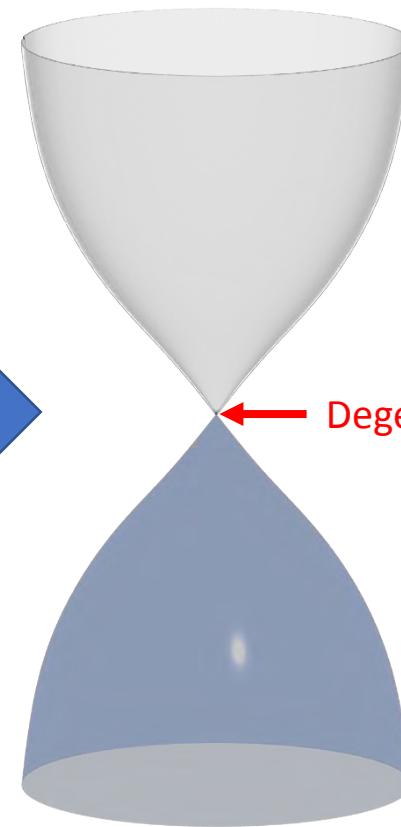


# Topological Dirac Semimetals



Regular insulator

Band gap reduced to zero

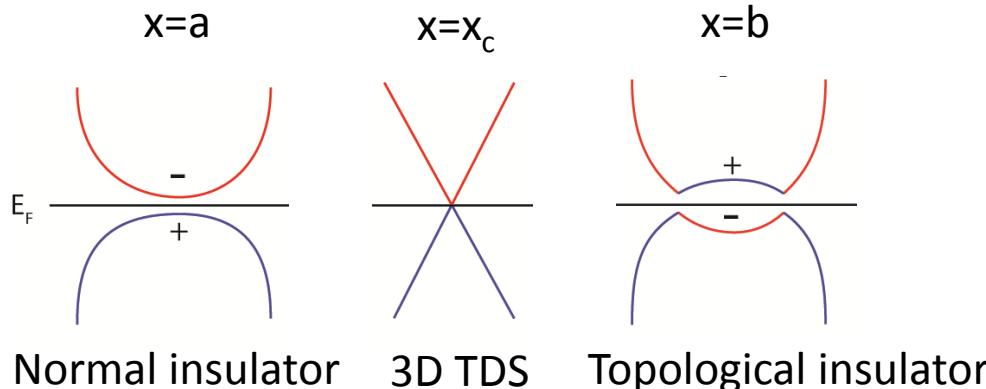


Topological Dirac Semimetal

# Formation of 3D Topological Dirac Semimetal

Extrinsic 3D TDS:

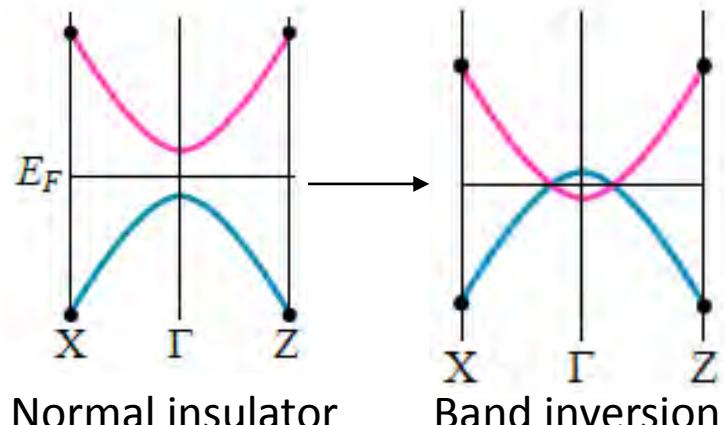
Doping:



Topological critical point between topological and normal insulator:

- Fine tuning of chemical composition required
- Not necessarily protected by crystal symmetry
- Very sensitive to temperature, pressure and composition homogeneity

Intrinsic 3D TDS:



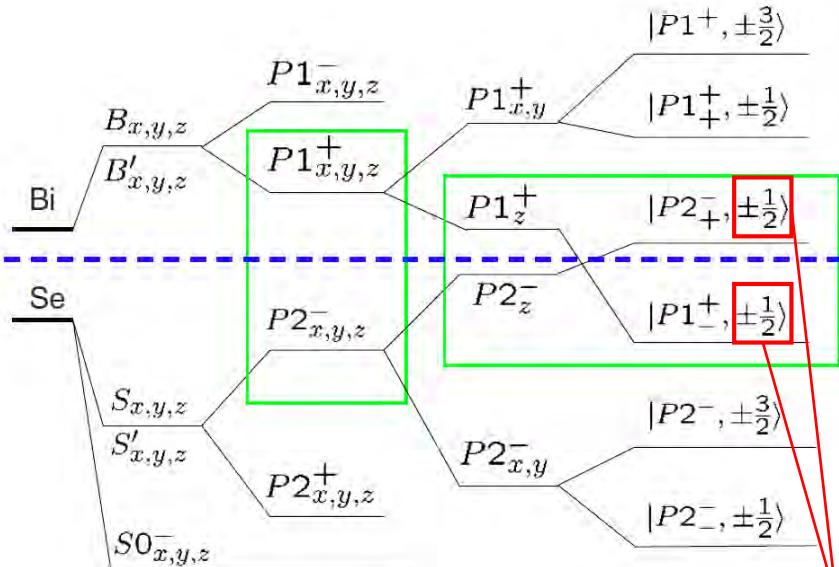
Node preserved: 3D TDS

- The crossing bands are orthogonal so that perturbation would not open a gap
- Crystal symmetry allows such orthogonal bands, even at the presence of SOC

Gap opening: Topological insulator

- SOC helps to increase the band inversion magnitude, at the same time, it would mix-up bands and make them non-orthogonal. So that an inversion gap usually persists

## Bi<sub>2</sub>Se<sub>3</sub>, topological insulator



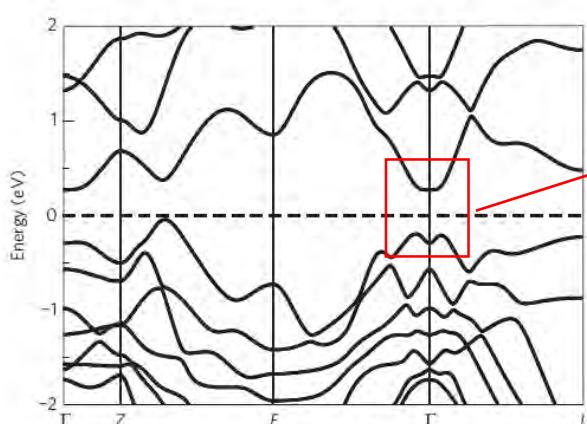
Orbital hybridization

Crystal field Splitting

Same  $|J_z|$ ,  
Not Orthogonal

Chemical  
bounding

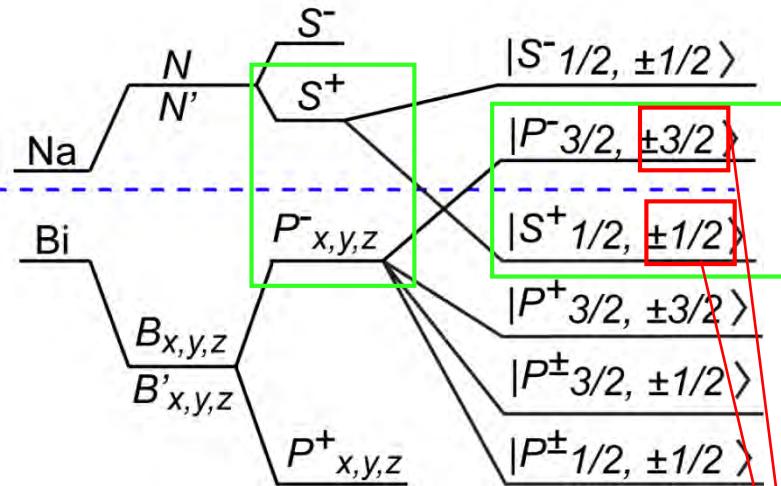
Spin-Orbit  
Coupling



Inverted  
Band gap  
From p-p  
Band inversion

H. J. Zhang *et al.*,  
*Nature Physics* **5**, 438 – 442(2009)  
C. -X. Liu *et al.*,  
*Phys. Rev. B* **82**, 045122(2010)

## Na<sub>3</sub>Bi, 3D topological Dirac semimetal

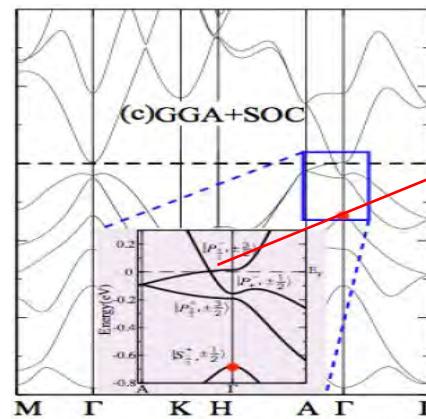


Orbital  
hybridization

Spin-Orbit  
Coupling

Chemical  
bounding

Different  $|J_z|$ ,  
Orthogonal

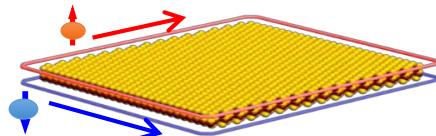


Band touching  
Point  
preserved  
From s-p  
Band  
inversion (at  
some Kz)

Z. J. Wang *et al.*,  
*Phys. Rev. B* **85**, 195320(2012)

# Dirac electron systems

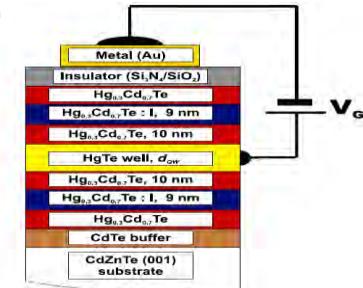
1D Dirac fermions



Quantum spin Hall edge state

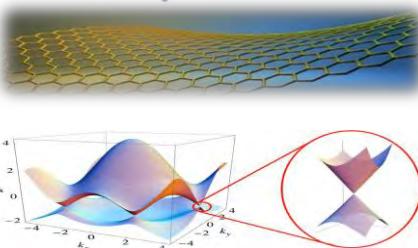
Conduction band

Valence band

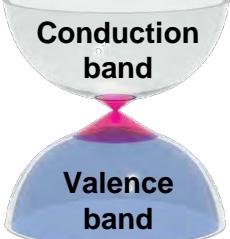
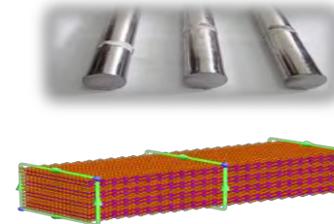


2D Dirac fermions

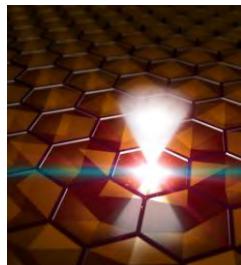
Graphene



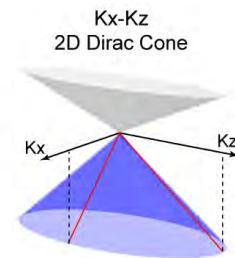
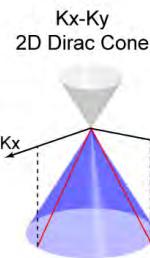
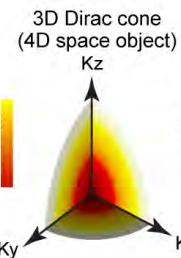
3D TI surface state



3D Dirac fermions



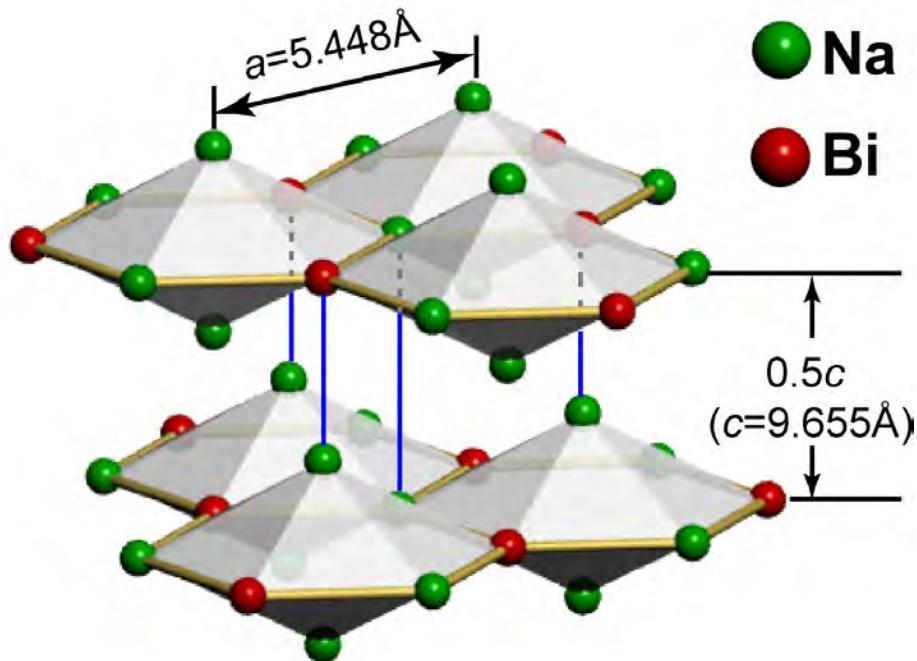
Topological Dirac Semimetal



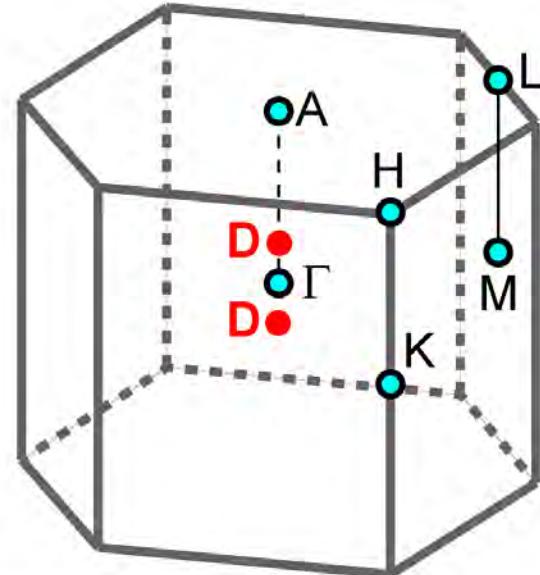
# 3D Topological Dirac Semi-metal (TDS)

Z. K. Liu. et. al., Science, 343, 864 (2014)

## Crystal structure

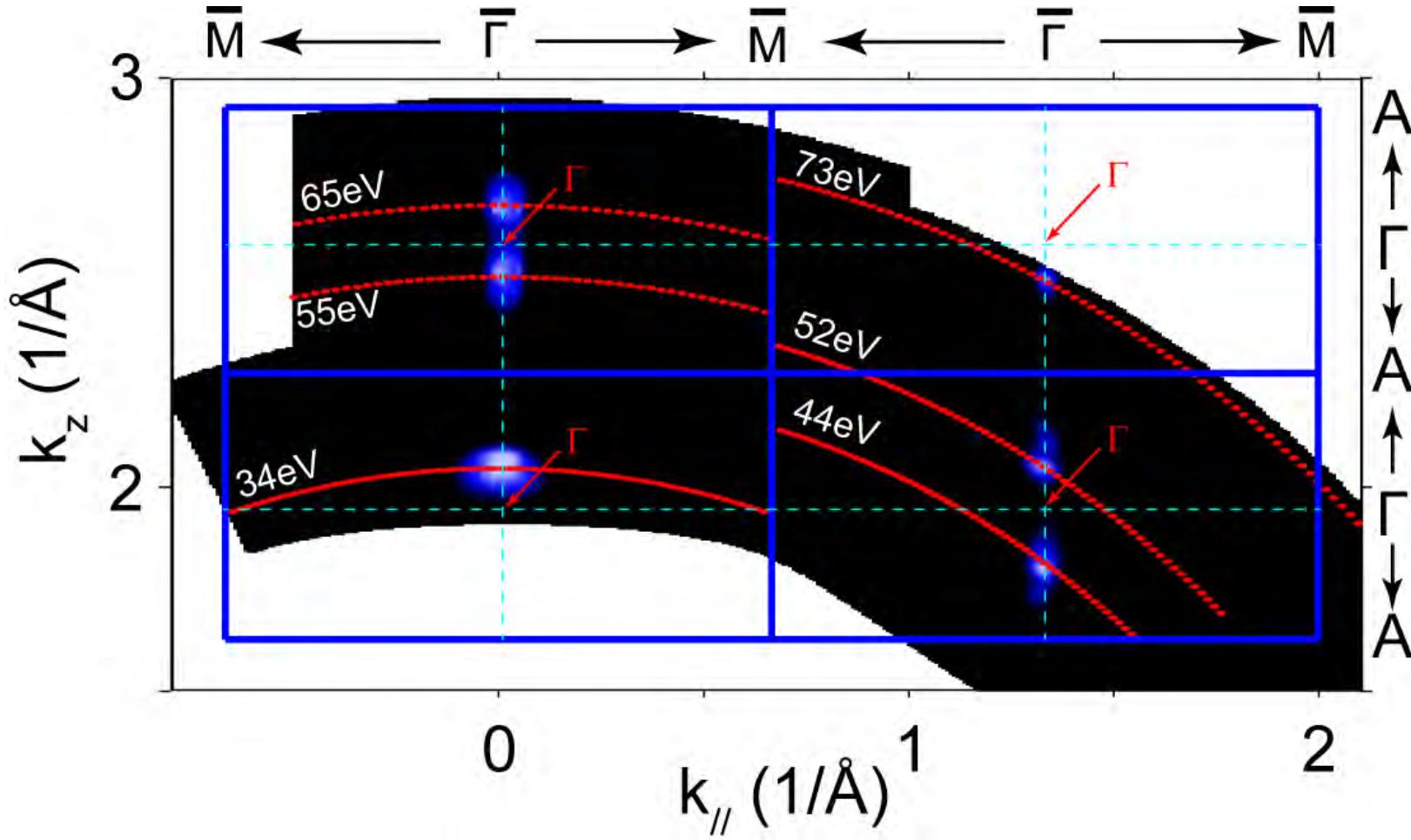


## Brillouin Zone



# Extracting $k_z$ dispersions

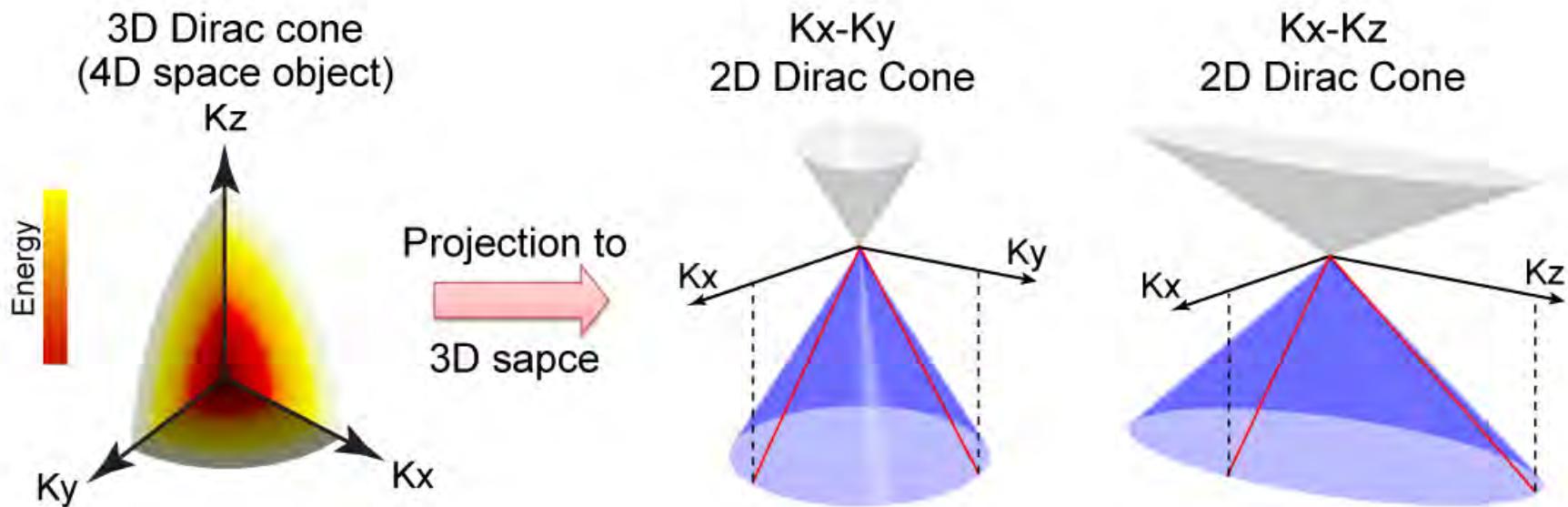
Multiple BZ mapping along  $k_z$



# How to identify a 3D TDS?

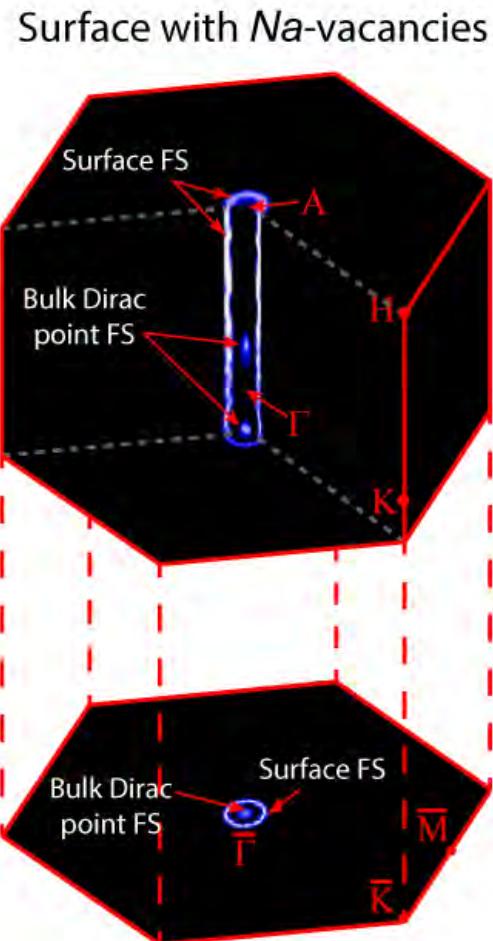
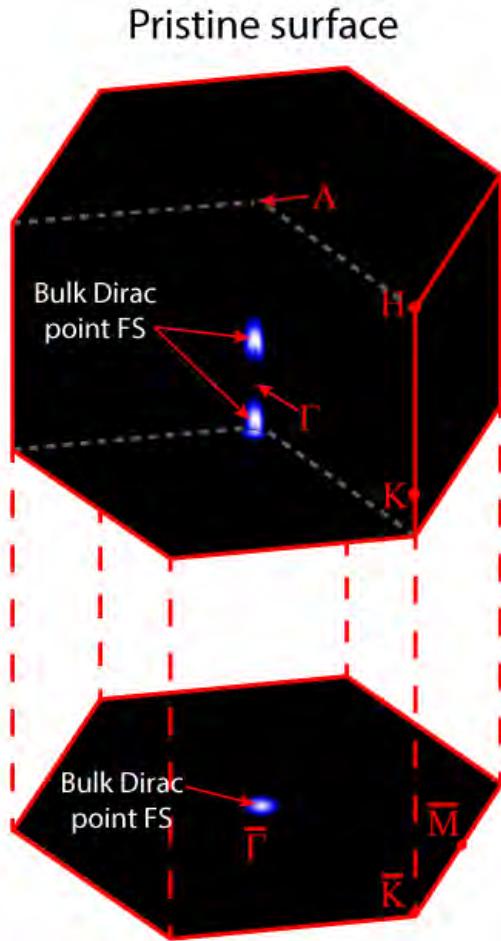
The 3D counterpart of graphene

## Identify the band structure



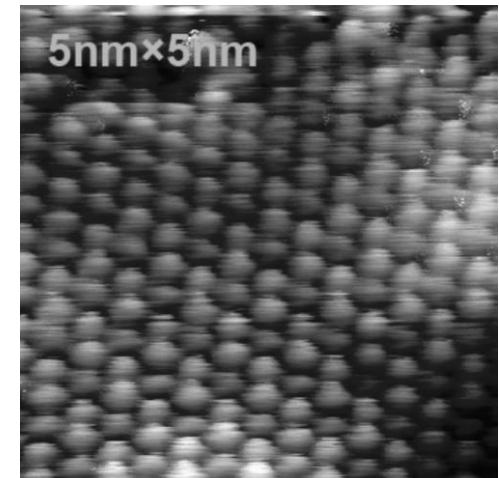
# Fermi surface and Real surface

## Complete 3D Fermi-surface mapping



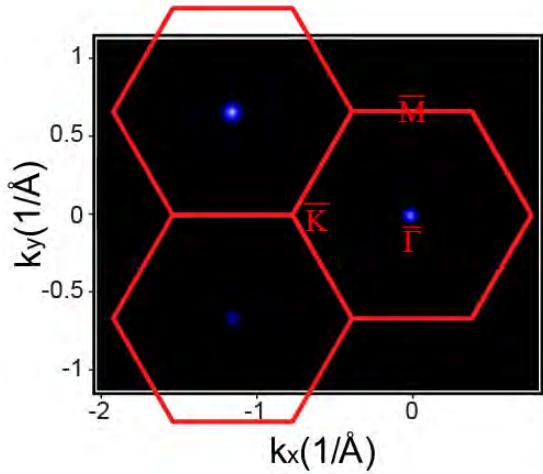
## Real surface

(Courtesy of X. Chen  
Tsinghua Univ., China)



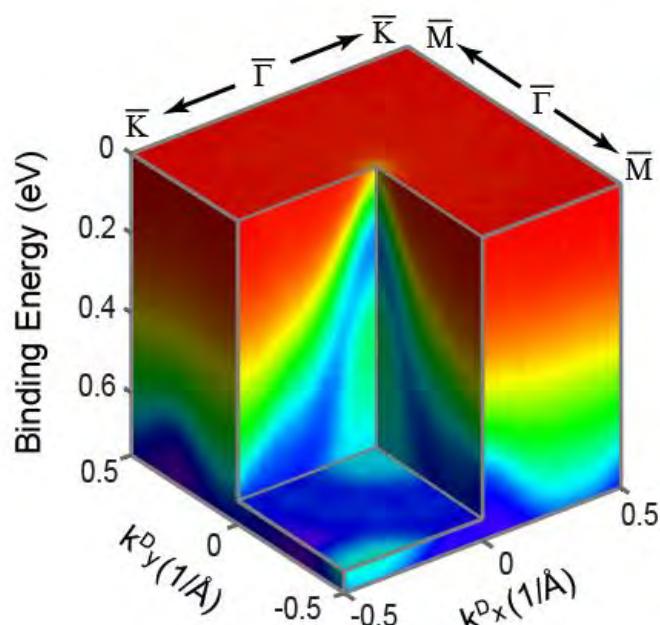
# Projections to $(k_x, k_y, E)$ space

Fermi-surface



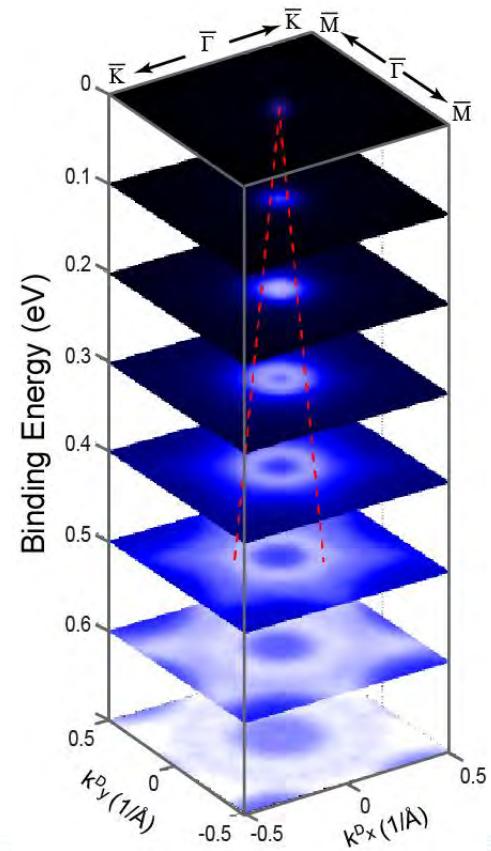
$$V_x = 2.75 \text{ eV}\cdot\text{\AA} \quad \text{or} \quad V_y = 2.39 \text{ eV}\cdot\text{\AA}$$

Band dispersion



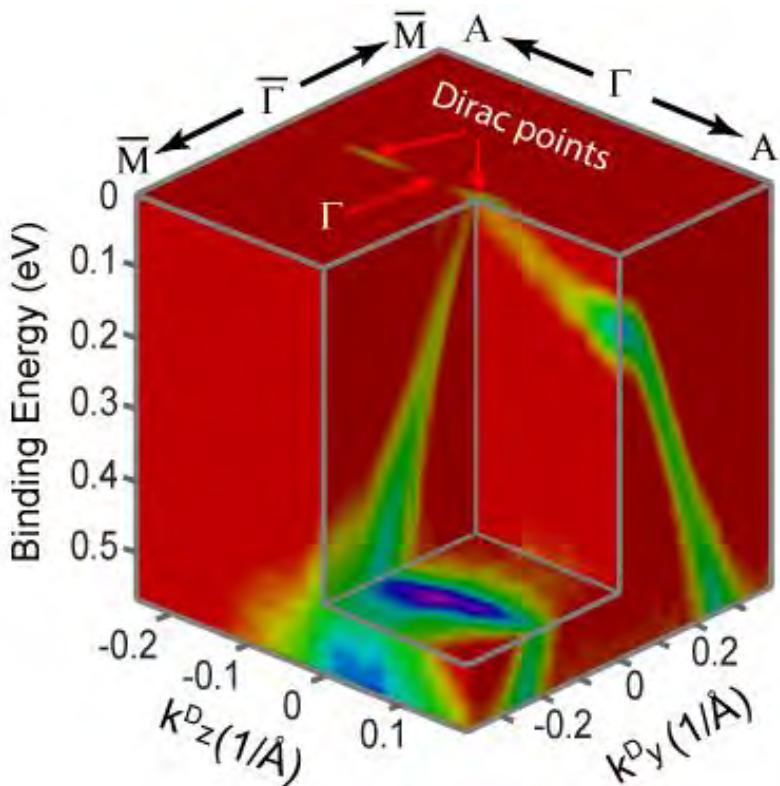
$$4.17 \times 10^5 \text{ m/s} \quad \text{or} \quad 3.63 \times 10^5 \text{ m/s}$$

Constant energy contours

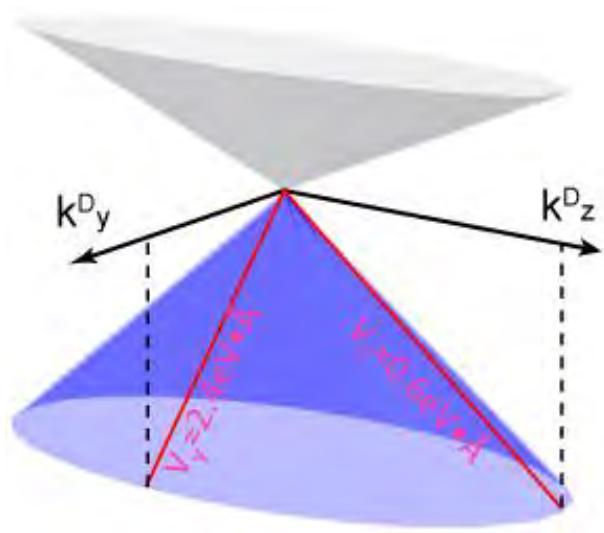


# Projection to (ky, kz, E) space

## Band dispersions



## Strong anisotropy



$$Vx = 2.75 \text{ eV} \cdot \text{Å} \quad \text{or}$$

$$Vy = 2.39 \text{ eV} \cdot \text{Å} \quad \text{or}$$

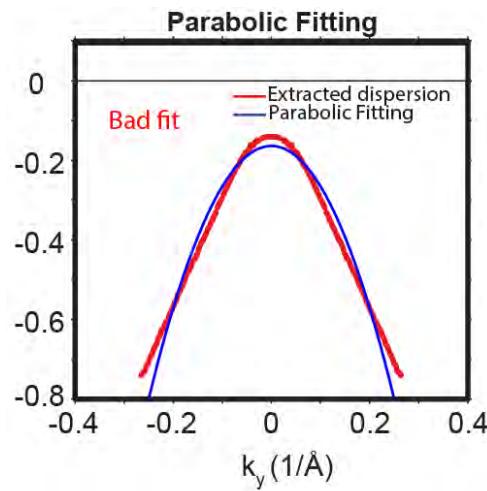
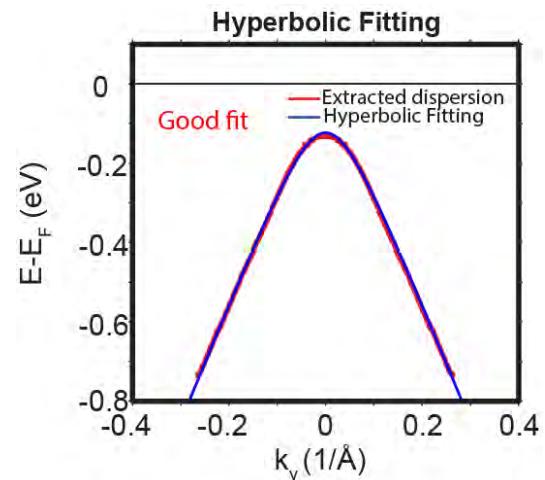
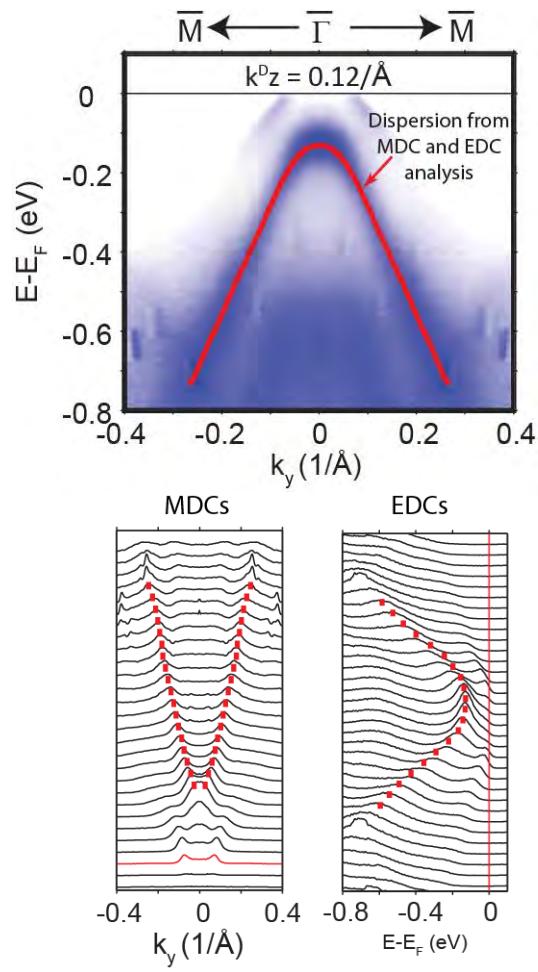
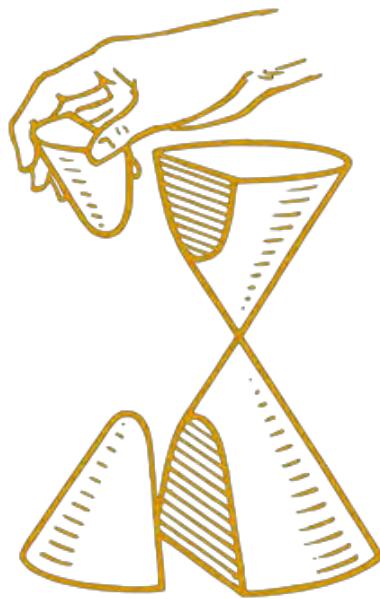
$$Vz = 0.6 \text{ eV} \cdot \text{Å} \quad \text{or}$$

$$4.17 \times 10^5 \text{ m/s}$$

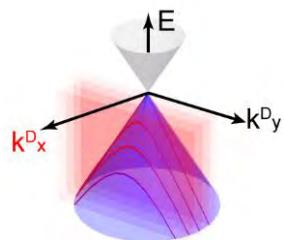
$$3.63 \times 10^5 \text{ m/s}$$

$$0.95 \times 10^5 \text{ m/s}$$

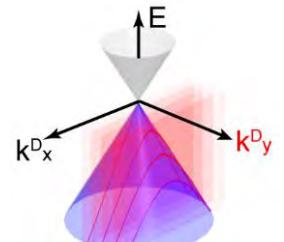
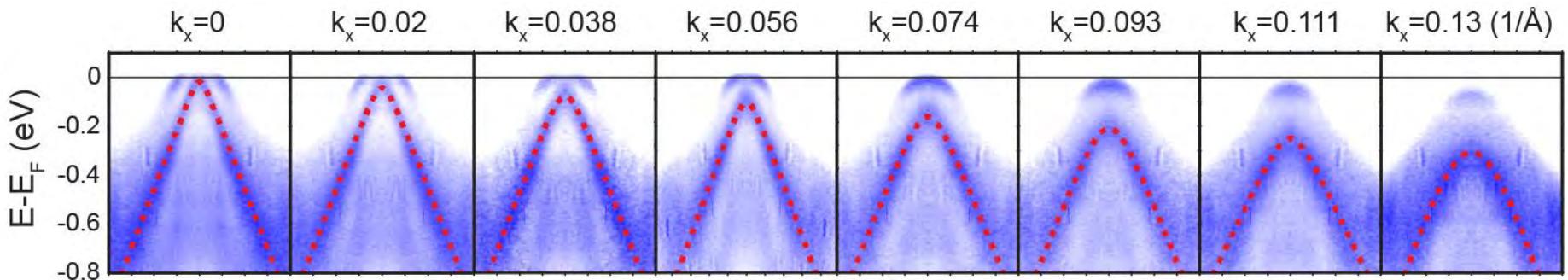
# Unusual hyperbolic dispersion



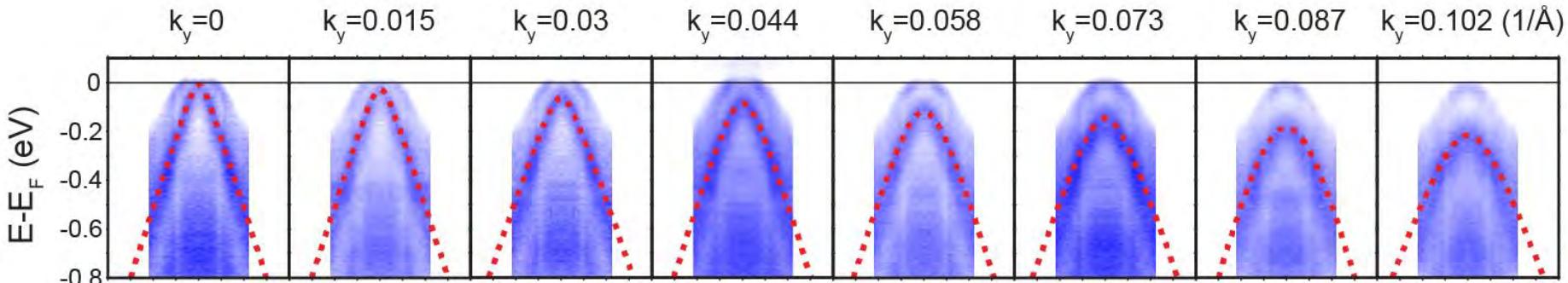
# Dispersions at different $k_x$ , $k_y$ values



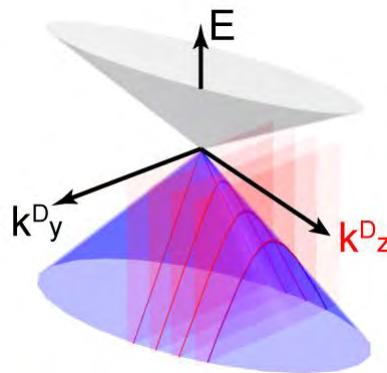
$$k_x = 2.75 \text{ eV}\cdot\text{Å} \text{ or } 4.17 \times 10^5 \text{ m/s}$$



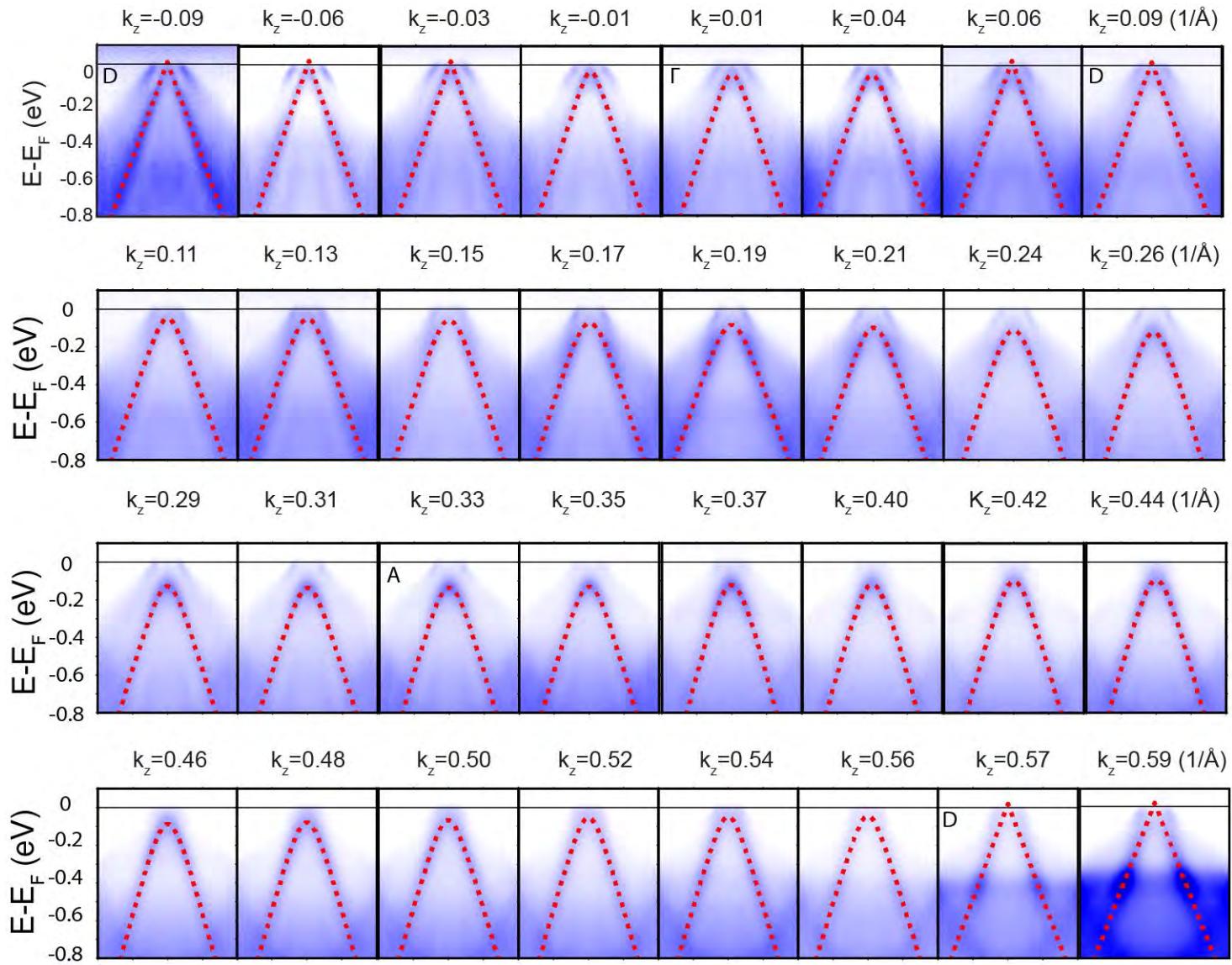
$$k_y = 2.39 \text{ eV}\cdot\text{Å} \text{ or } 3.63 \times 10^5 \text{ m/s}$$



# Dispersions at different $k_z$ values

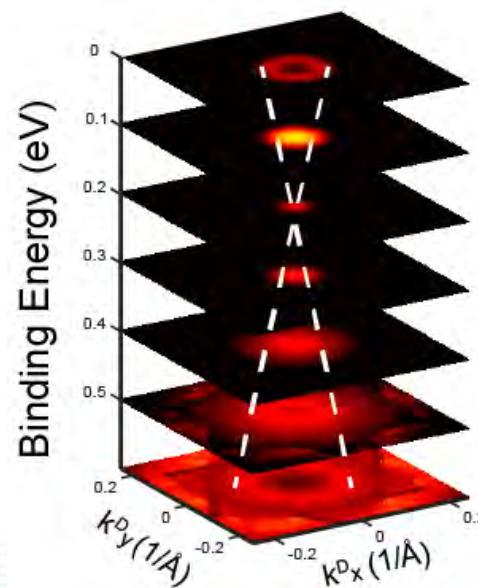
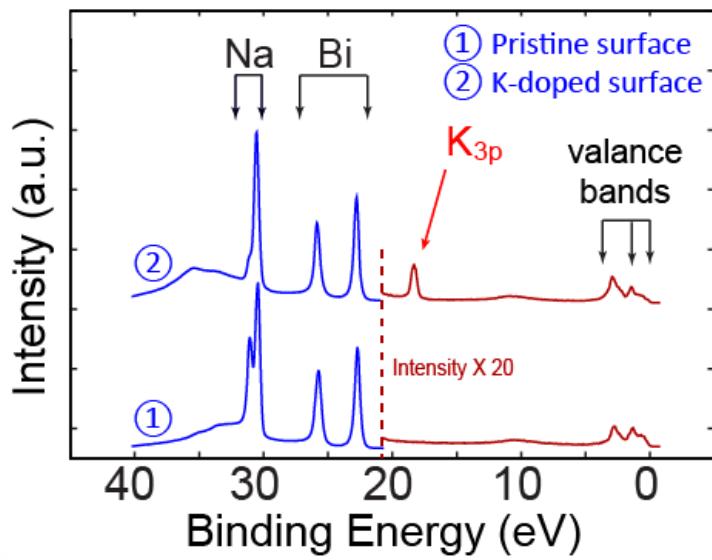
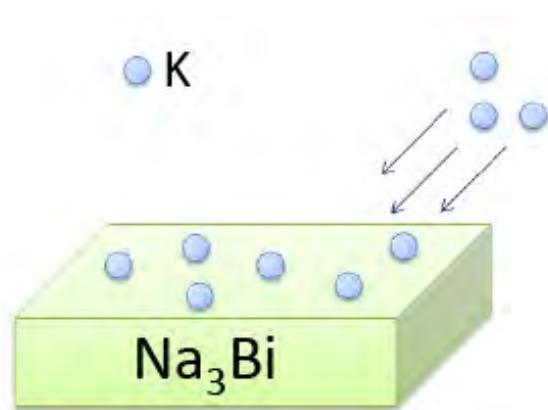


$k_z = 0.6 \text{ eV}\cdot\text{\AA}$   
or  $0.95 \times 10^5 \text{ m/s}$



# Observing the Dirac point and upper cone

*In-situ K-doping*

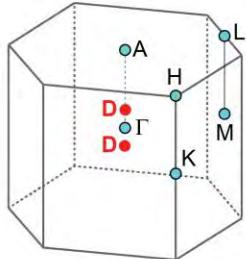


# Protection of the crystalline symmetry

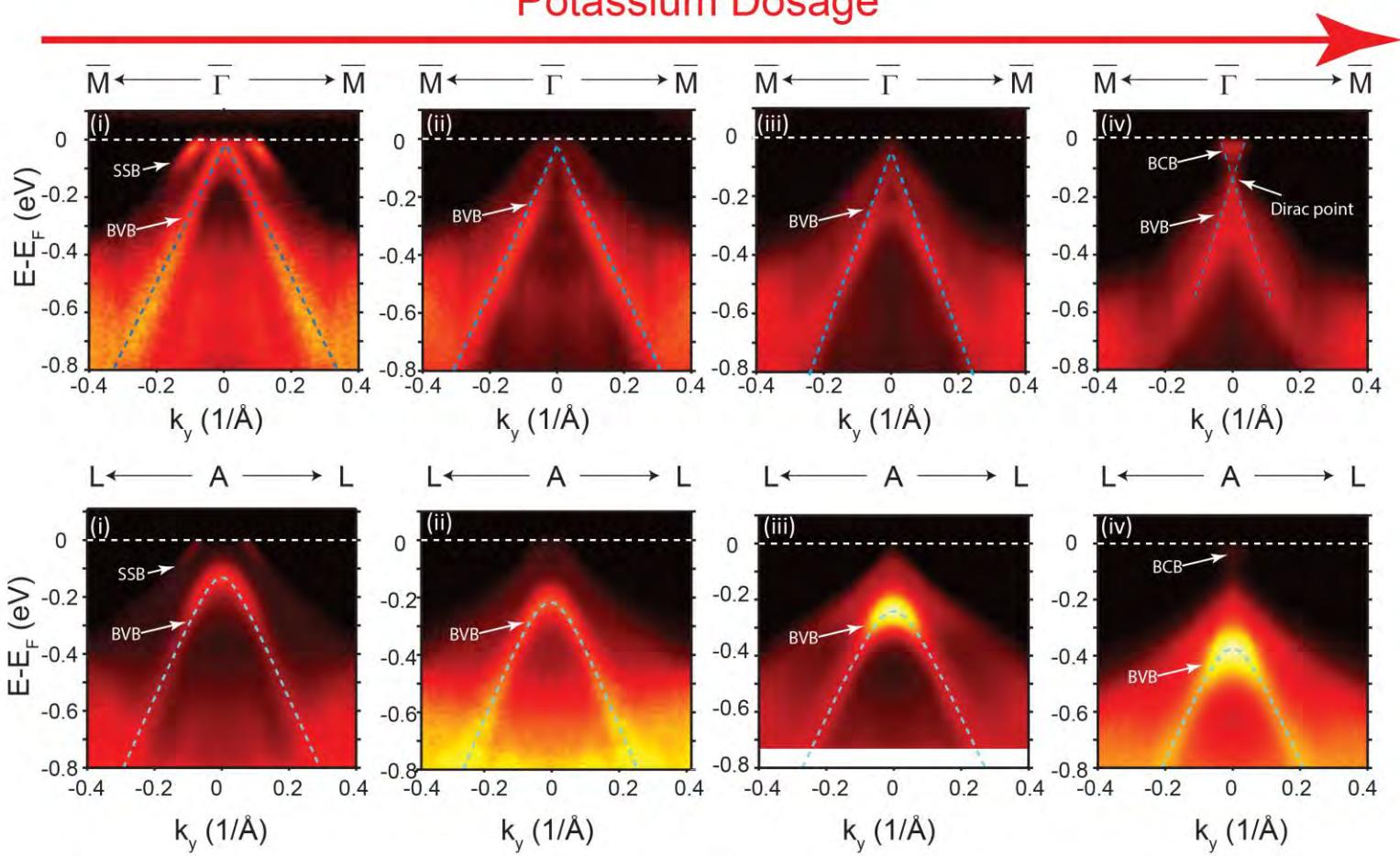
Disrupted surface state but intact bulk

Potassium Dosage

$k_z = -0.09/\text{\AA}$   
(Cut across the  
bulk Dirac point)

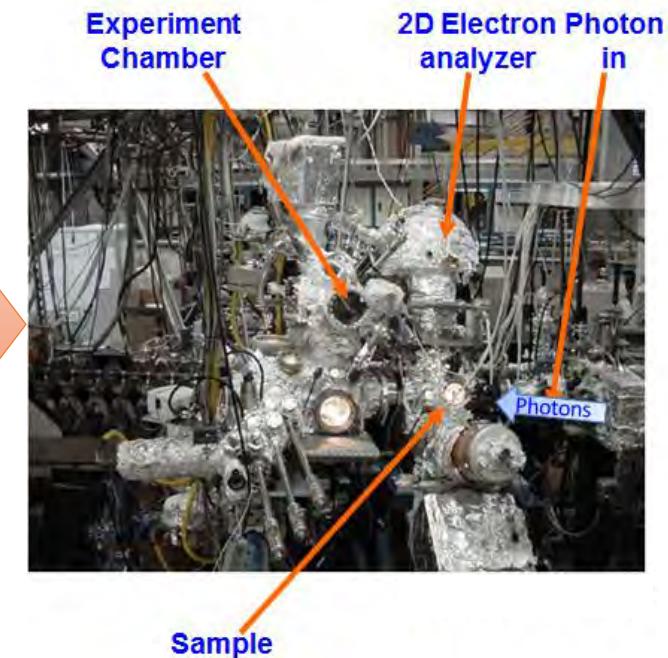


$k_z = 0.327/\text{\AA}$   
(Cut across the "A"  
point at the top  
of the BZ)



# The problem of Na<sub>3</sub>Bi

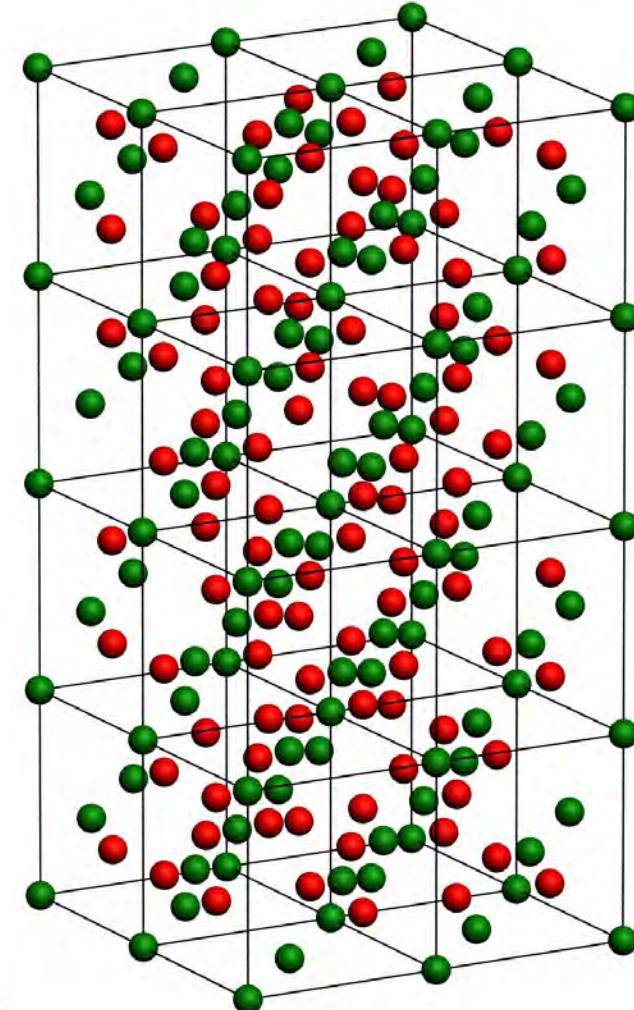
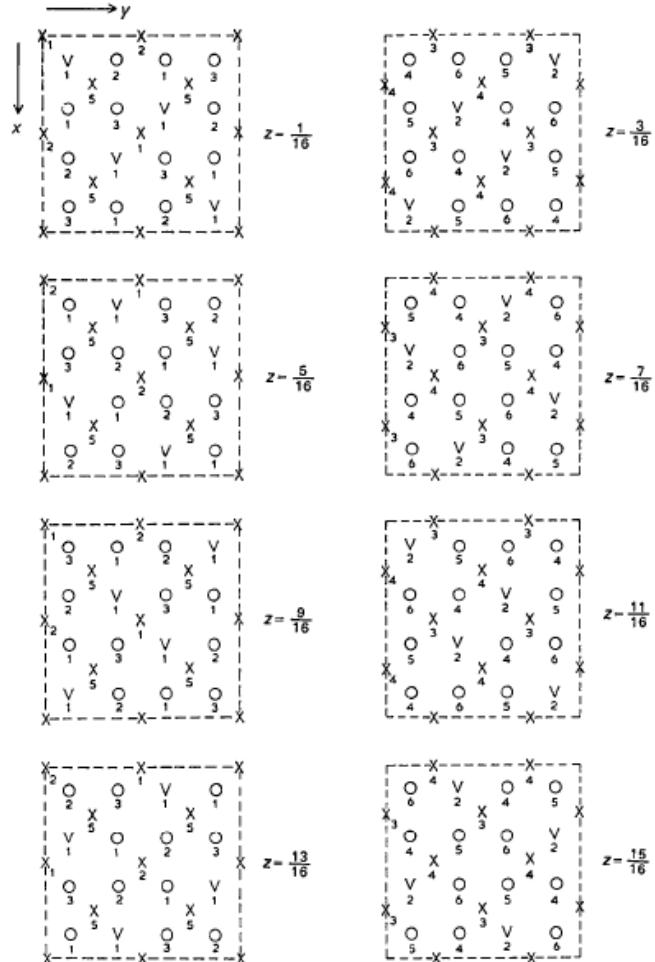
**Too reactive in ambient environment ...**



**Hard to handle and used in functional devices**

# A stable 3D TDS, $\text{Cd}_3\text{As}_2$

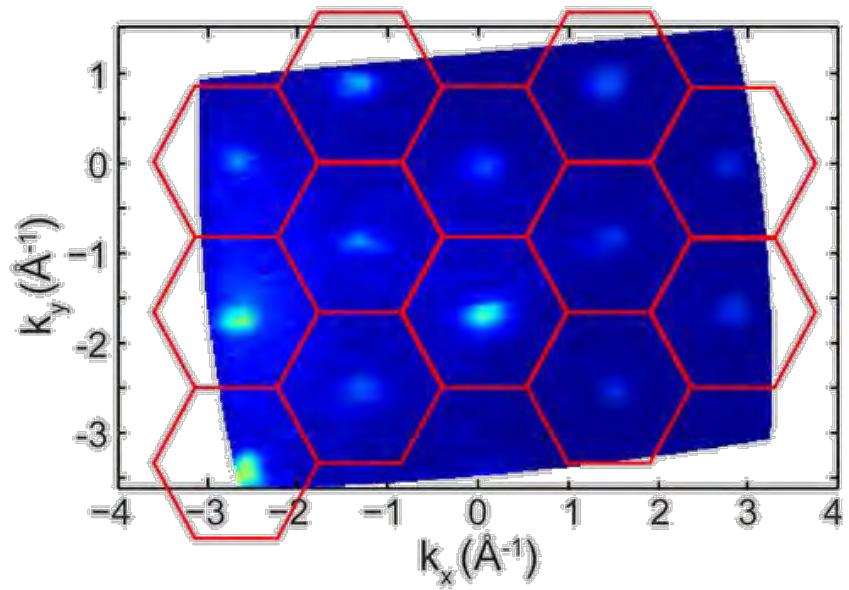
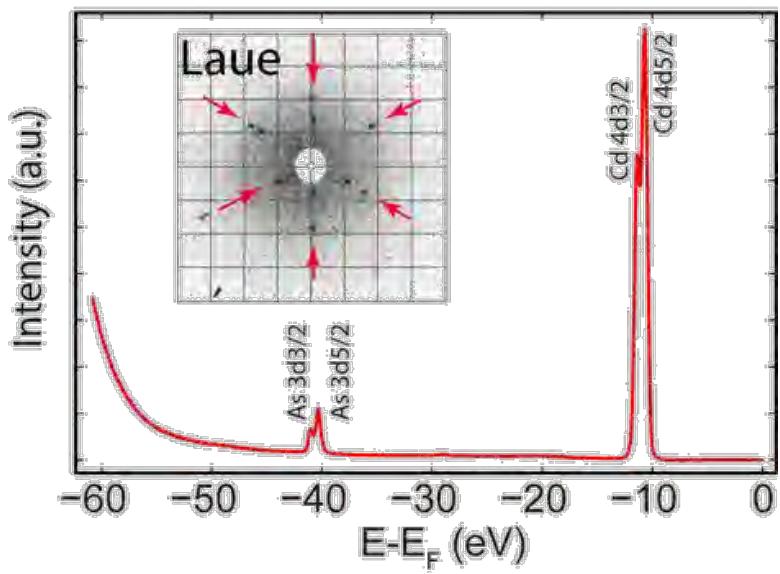
## Dizzying crystal structure...



# A stable 3D TDS, Cd<sub>3</sub>As<sub>2</sub>

Z. K. Liu. et. al., Nature Materials, 13, 677 (2014)

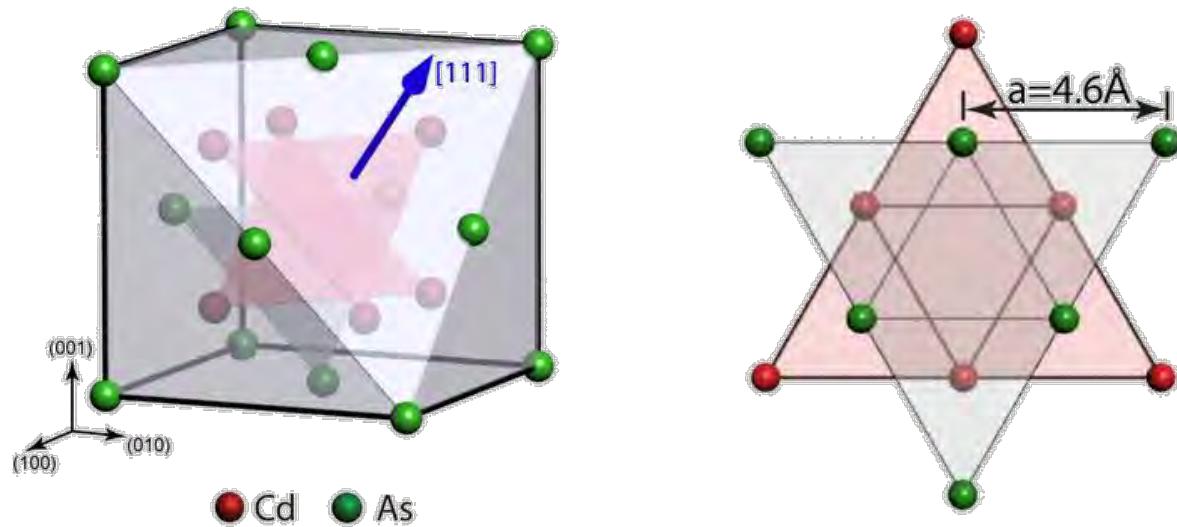
## Laue, corelevel and broad FS mapping



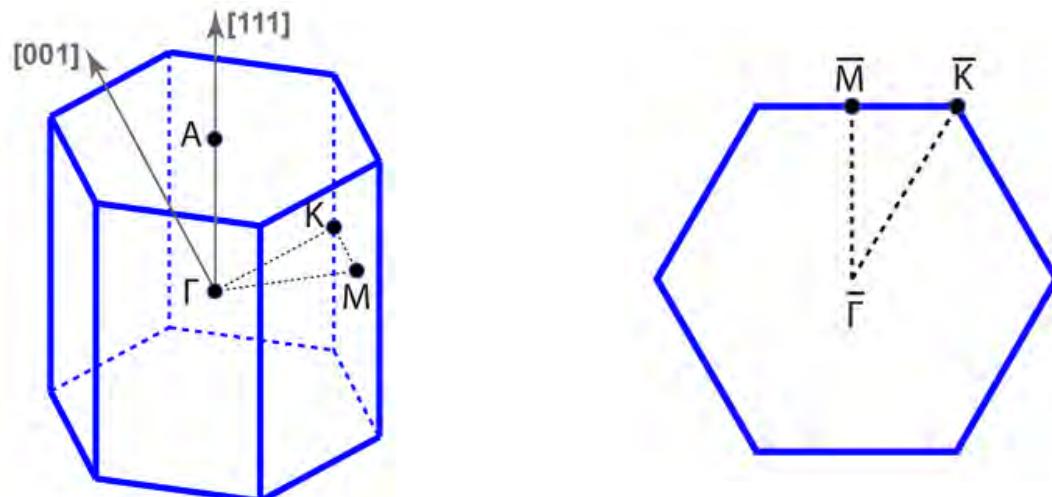
# A stable 3D TDS, $\text{Cd}_3\text{As}_2$

Z. K. Liu. et. al., Nature Materials, 13, 677 (2014)

## Crystal structure



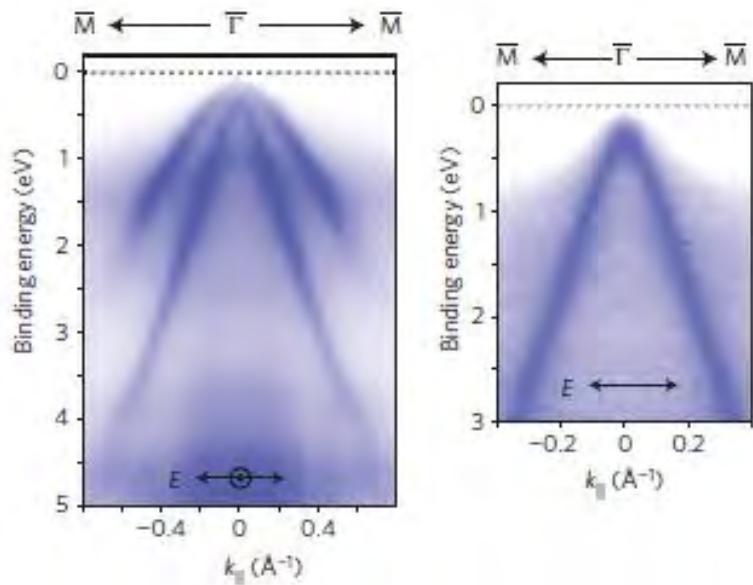
## Brillouin Zone



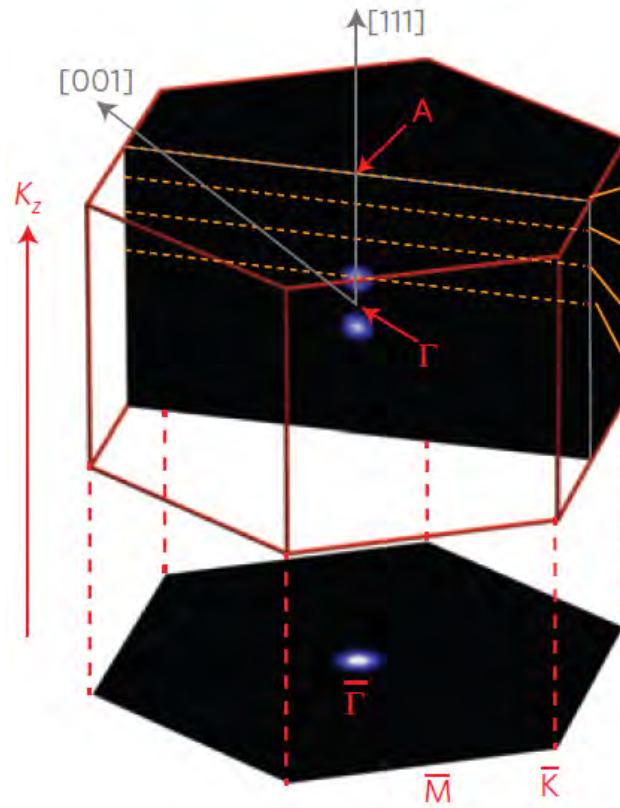
# A stable 3D TDS, $\text{Cd}_3\text{As}_2$

Z. K. Liu. et. al., Nature Materials, 13, 677 (2014)

## Bands at different geometry

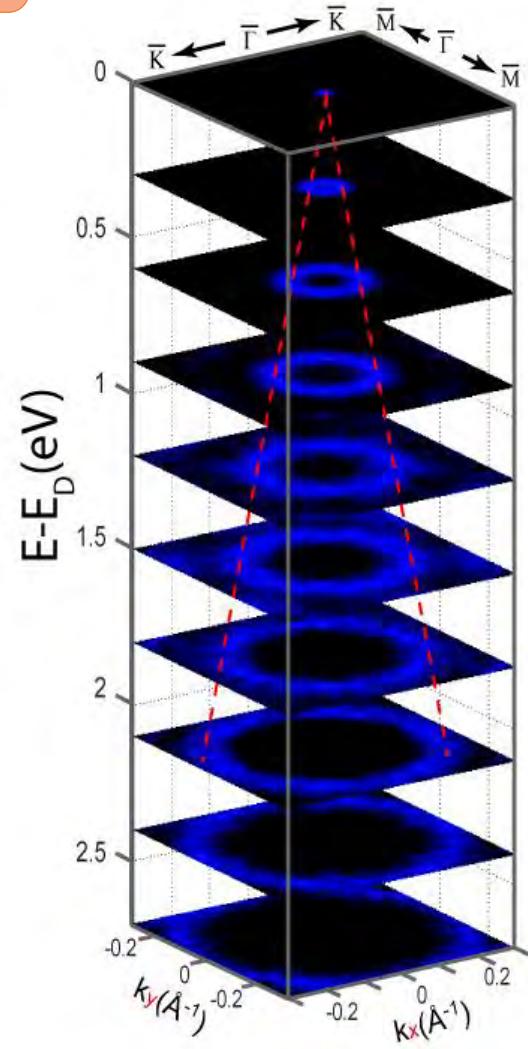
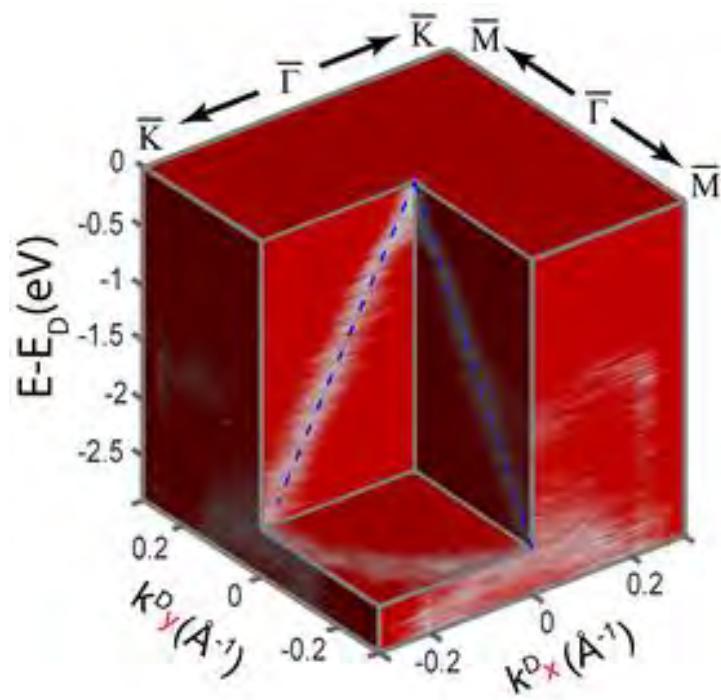
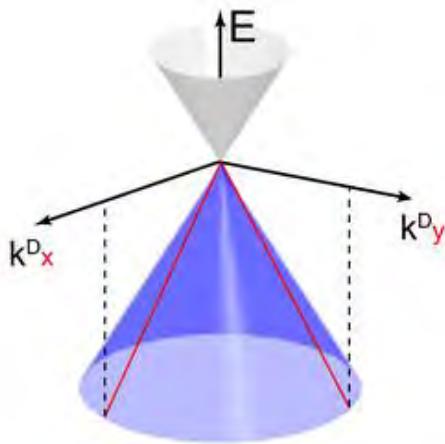


## 3D Fermi-Surface



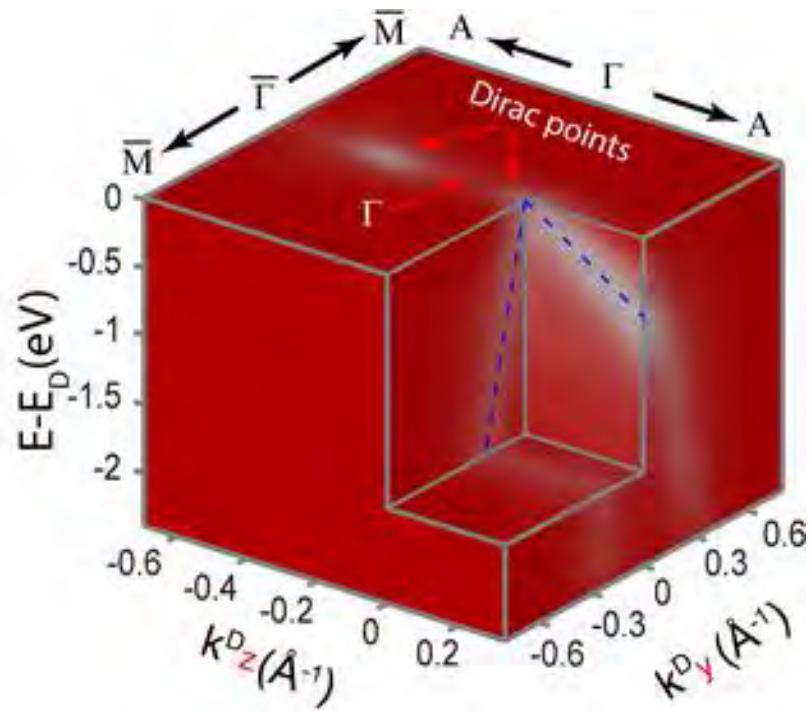
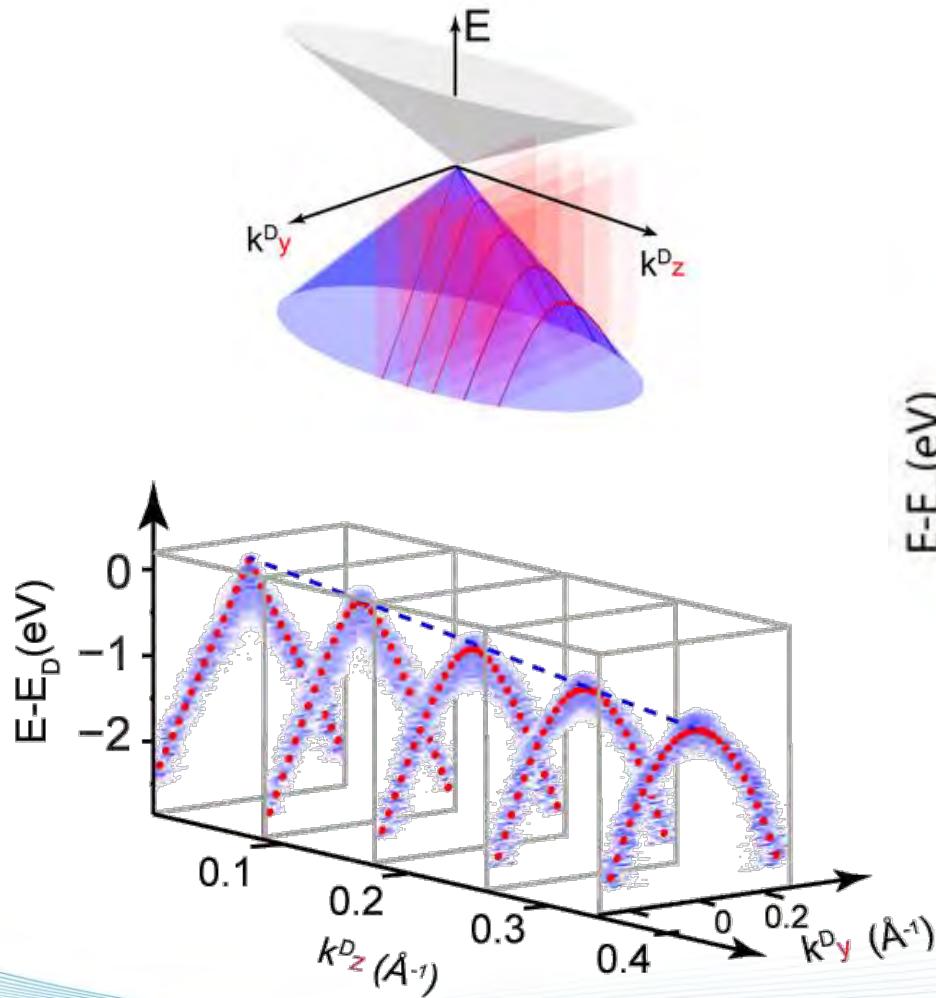
# A stable 3D TDS, Cd<sub>3</sub>As<sub>2</sub>

Projection to (K<sub>x</sub>, k<sub>y</sub>, E)



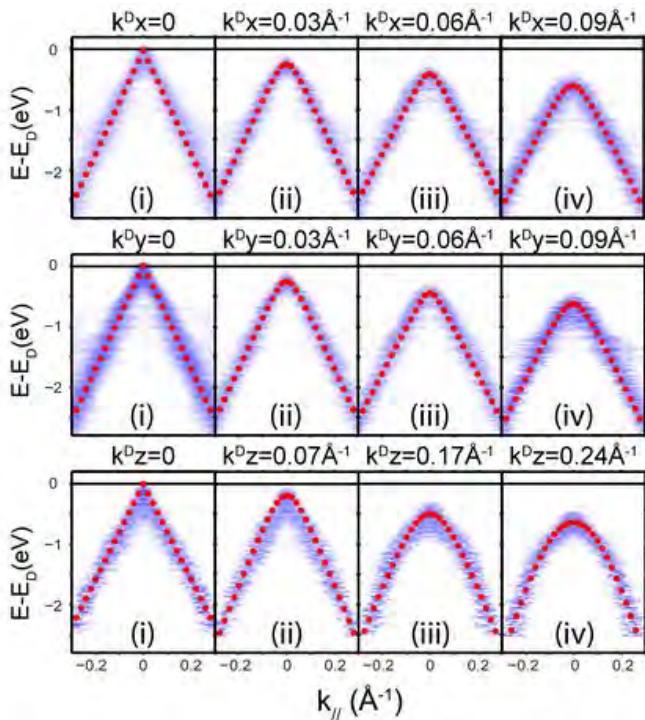
# A stable 3D TDS, Cd<sub>3</sub>As<sub>2</sub>

Projection to (k<sub>y</sub>, k<sub>z</sub>, E)

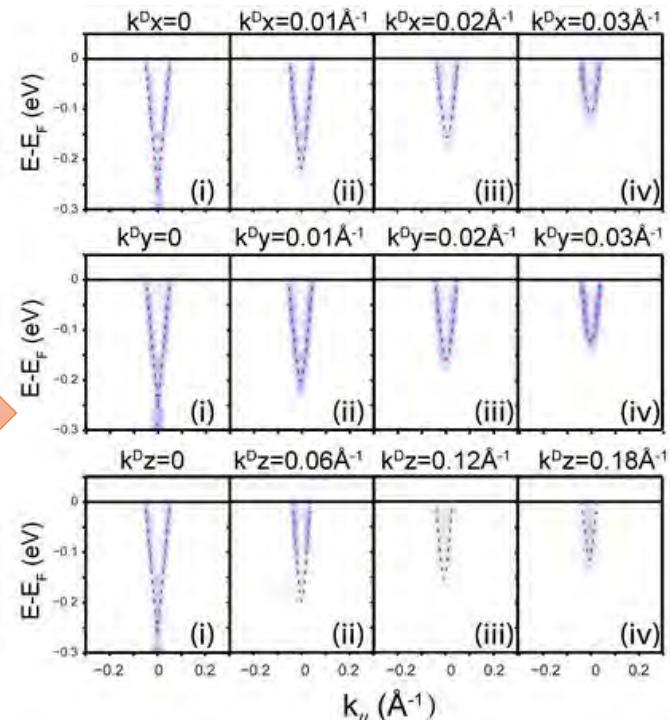


# A stable 3D TDS, Cd<sub>3</sub>As<sub>2</sub>

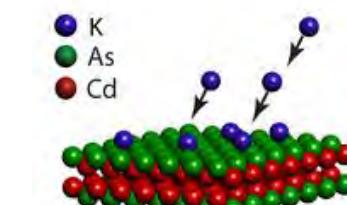
## Valence band



## Conduction band



## In-situ K-doping



$$V_x = 8.47 \text{ eV}\cdot\text{\AA} \text{ or } 1.28 \times 10^6 \text{ m/s}$$

$$V_y = 8.56 \text{ eV}\cdot\text{\AA} \text{ or } 1.3 \times 10^6 \text{ m/s}$$

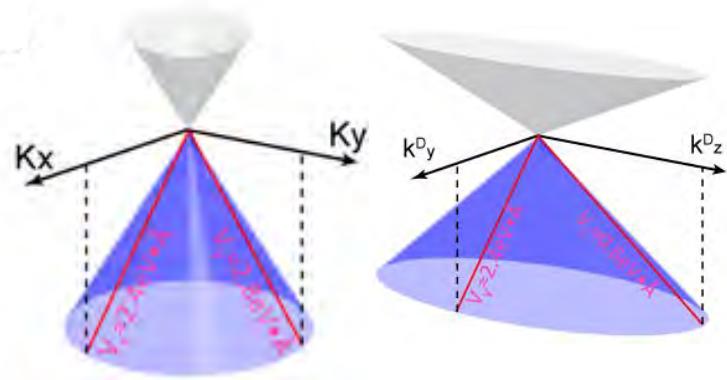
$$V_z = 2.16 \text{ eV}\cdot\text{\AA} \text{ or } 3.27 \times 10^5 \text{ m/s}$$

$$V_x = 5 \text{ eV}\cdot\text{\AA} \text{ or } 7.55 \times 10^5 \text{ m/s}$$

$$V_y = 5.1 \text{ eV}\cdot\text{\AA} \text{ or } 7.7 \times 10^5 \text{ m/s}$$

$$V_z = 1.5 \text{ eV}\cdot\text{\AA} \text{ or } 2.27 \times 10^5 \text{ m/s}$$

# Parameter Extraction



- Discovery of a three-dimensional Dirac Fermion in Three-dimensional Dirac semimetal Na<sub>3</sub>Bi and Cd<sub>3</sub>As<sub>2</sub>
- Stable objects, protected by topology

## Fermi Velocity Comparison:

Na<sub>3</sub>Bi:  $V_x=4.17\times10^5\text{m/s}$ ,  $V_y=3.63\times10^5\text{m/s}$ , and  $V_z=0.95\times10^5\text{m/s}$ ;

Cd<sub>3</sub>As<sub>2</sub>:  $V_x=1.28\times10^6\text{m/s}$ ,  $V_y=1.3\times10^6\text{m/s}$ , and  $V_z=3.27\times10^5\text{m/s}$ ;

**Mobility  $>4\times10^4 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$**  (T. Liang et al., Nat Mater 2014)

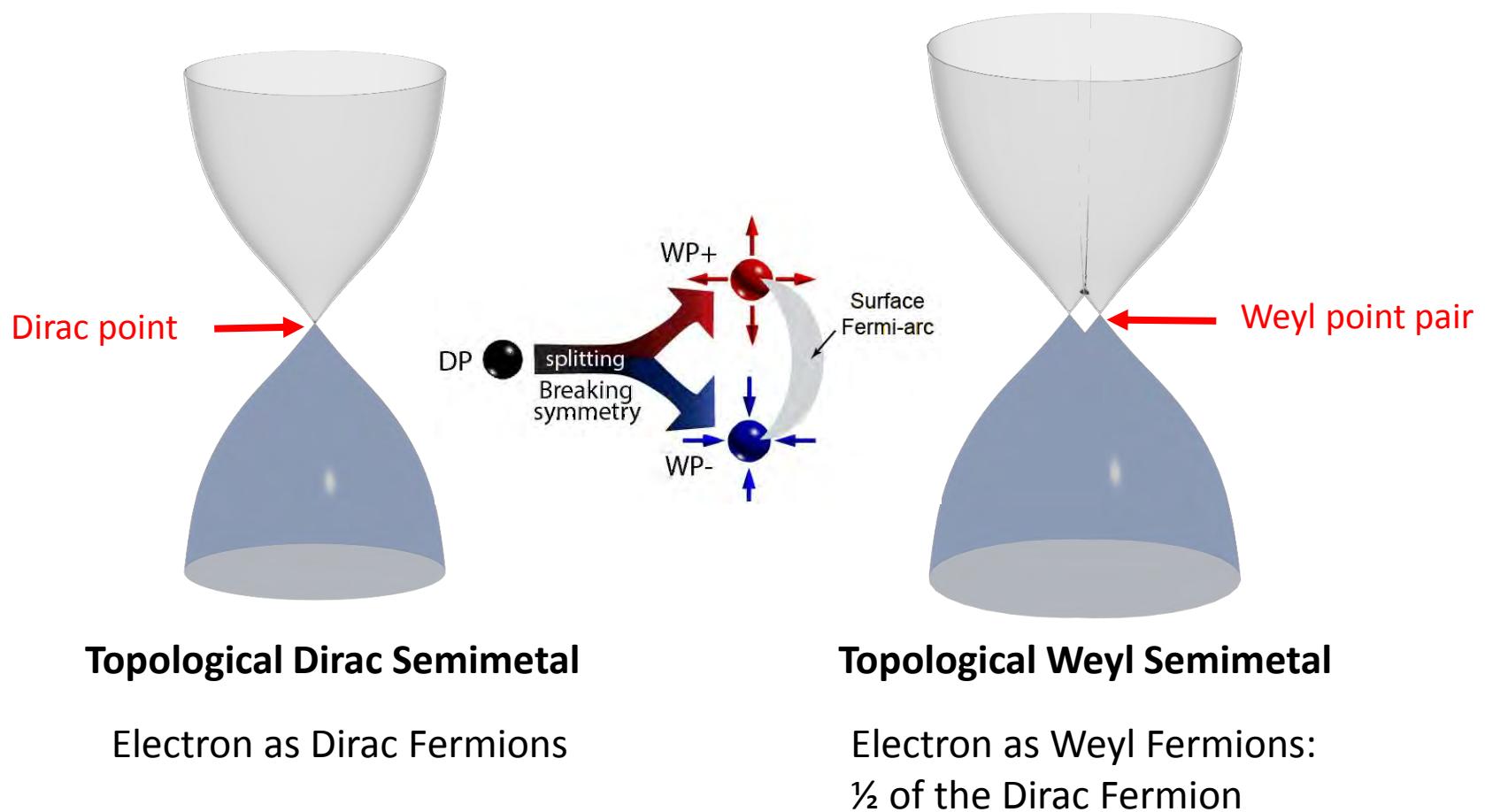
Bi<sub>2</sub>Te<sub>3</sub>:  $V_{\text{surface}}=4\times10^5\text{m/s}$ ;

Graphene:  $V_{\text{Dirac}}=1.1\times10^6\text{m/s}$ ;

**Mobility  $>1.5\times10^4 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$**  (Geim, A. K. & Novoselov, K. S. Nat Mater 2007)

High mobility & large amount of bulk electrons make TDS a promising material for electronic applications.

# From Dirac to Weyl Semimetal

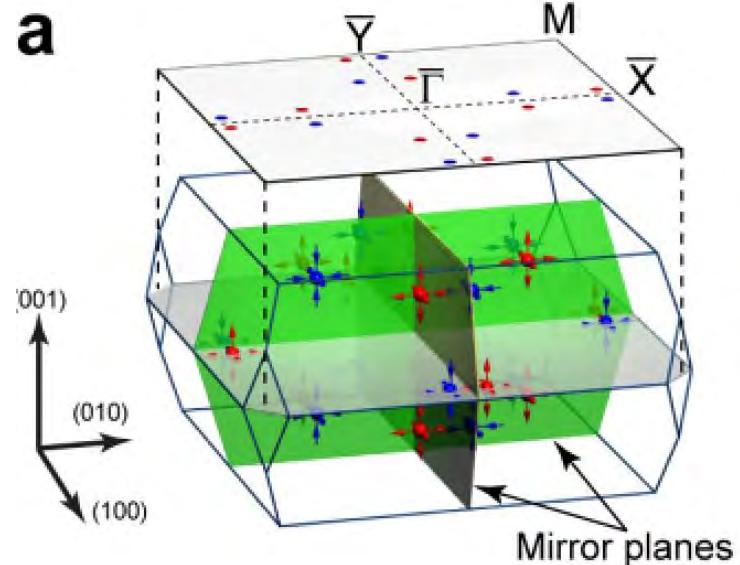
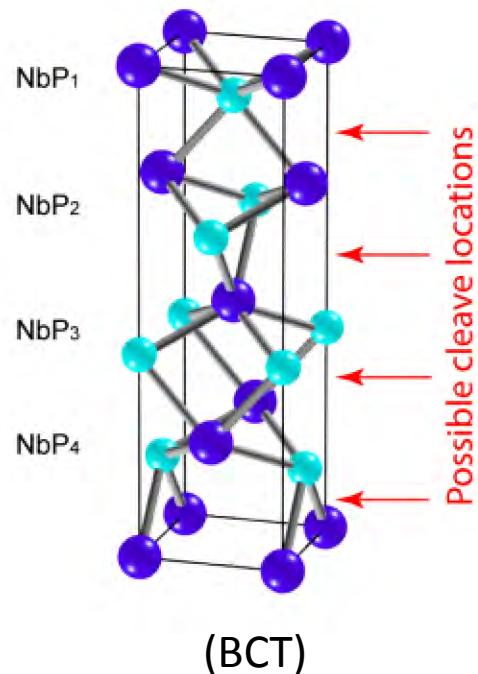
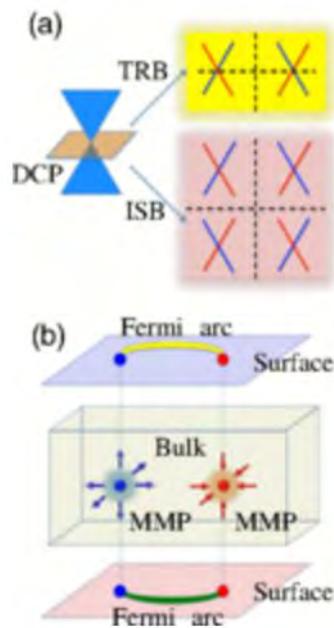


Model Materials:

Time reversal symmetry breaking:  $\text{HgCr}_2\text{Se}_4$ ,  $\text{Y}_2\text{Ir}_2\text{O}_7$ ,  $\text{XCO}_2\text{Z}$ ,  $\text{VCo}_2\text{Ga}_3$ ...

Inversion symmetry breaking:  $\text{Ta}(\text{Nb})\text{As}(\text{P})$ ,  $\text{SrSi}_2$ ...

# TWS in Inversion symmetry breaking transition metal monophosphide family

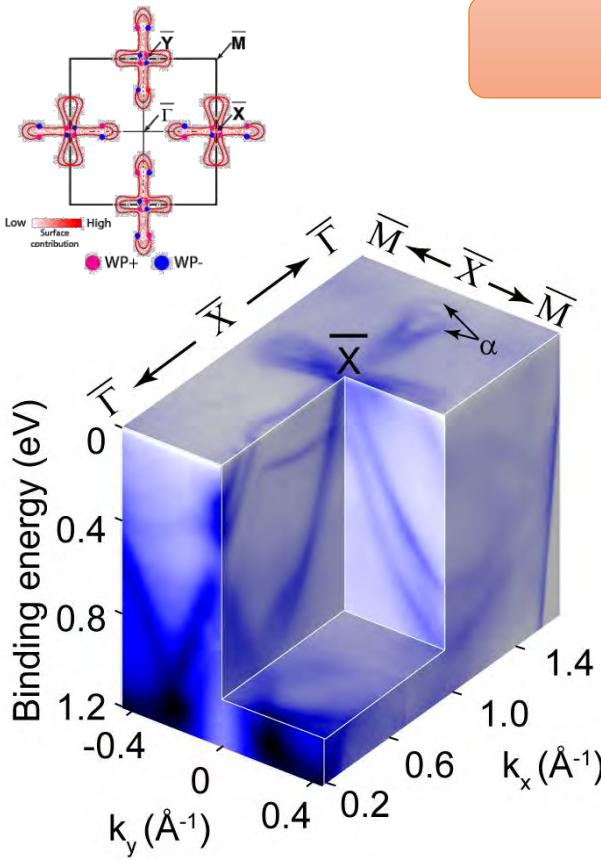


ARPES:

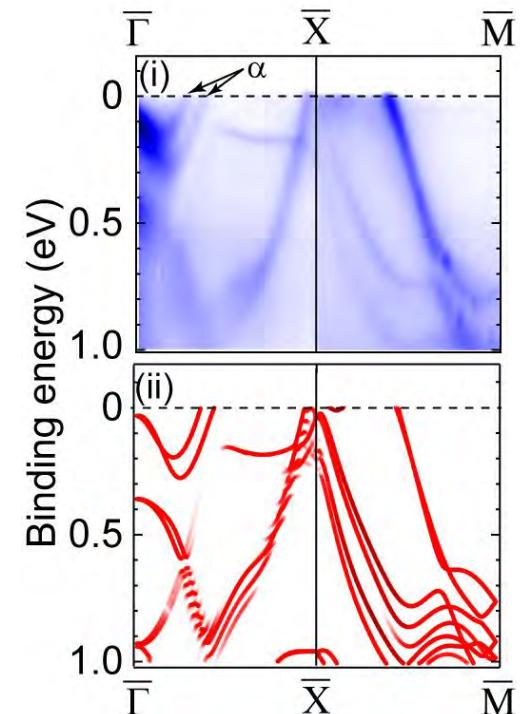
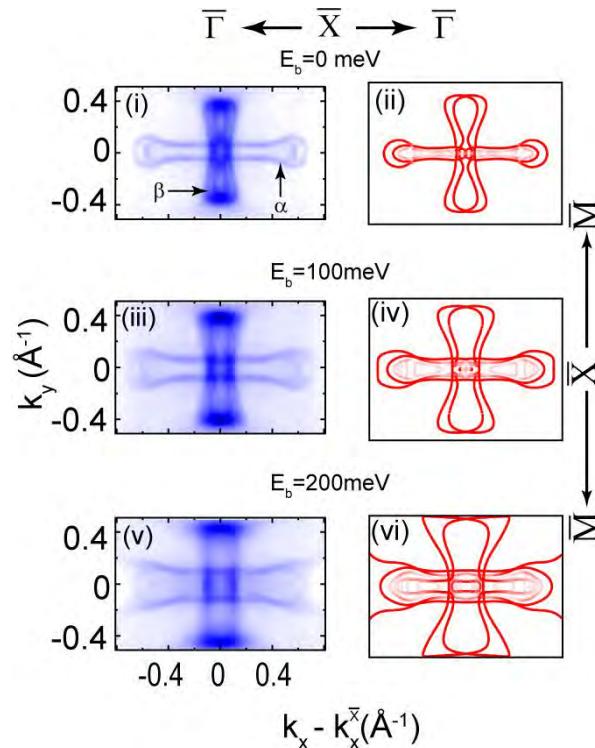
- B. Q. Lv, et al., Phys. Rev. X 5, 031013 (2015)
- B. Q. Lv, et al., Nature Physics 11, 724–727 (2015)
- B. Q. Lv, et al., Phys. Rev. Lett. 115, 217601 (2015)
- S.-Y. Xu, et al., Science 349, 613 (2015).
- S.-M. Huang, et al., Nature Commun. 6:7373 (2015).
- S.-Y. Xu, et al., Nature Physics 11, 748 (2015).
- S.-Y. Xu, et al., Phys. Rev. Lett. 116, 096801 (2016)

# 3D Topological Weyl Semimetal TaAs

L. X. Yang, et. al., *Nature Physics*, 11, 728 (2015)



## Fermi-surface & band structures

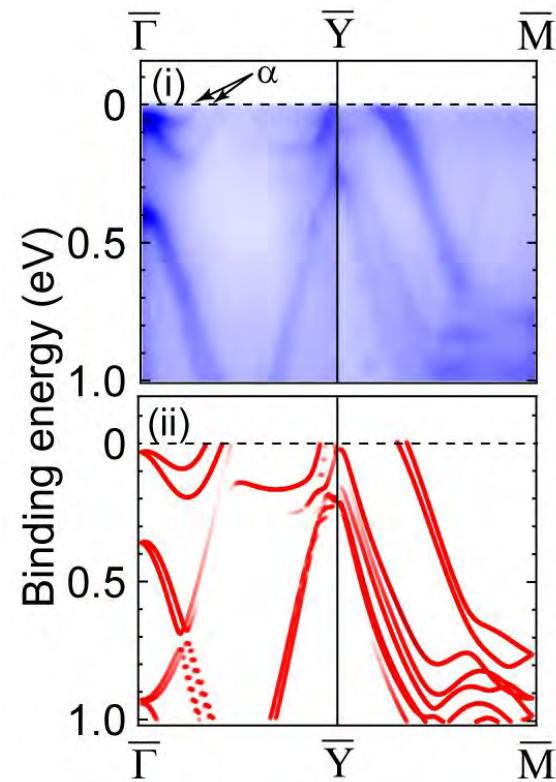
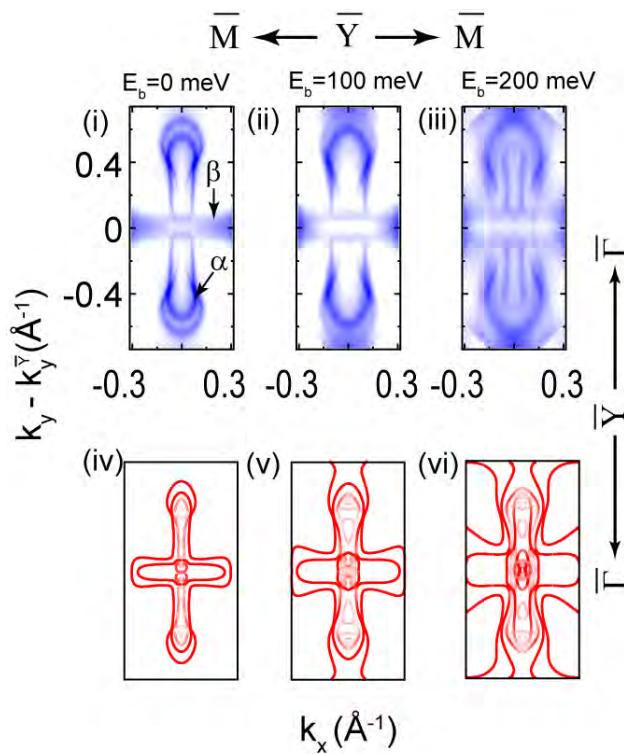
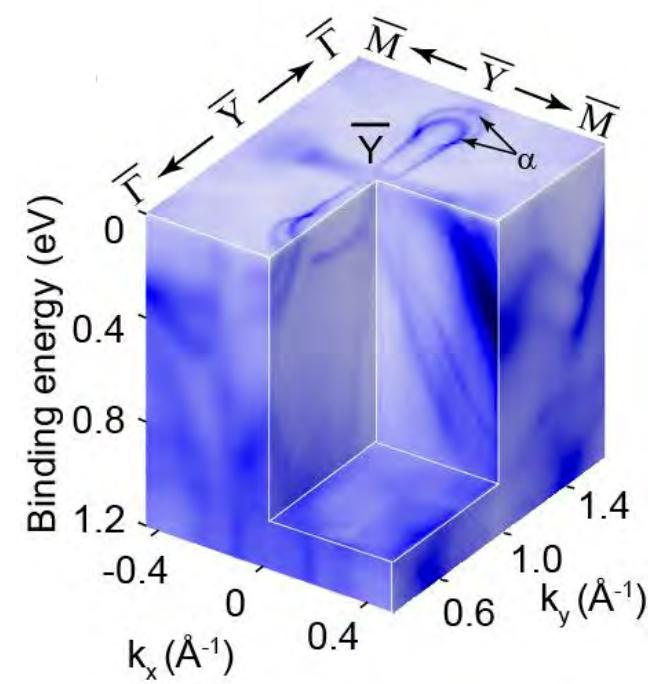


Low Intensity (a.u.) Low Surface contribution High

# 3D Topological Weyl Semimetal TaAs

L. X. Yang, et. al., *Nature Physics*, 11, 728 (2015)

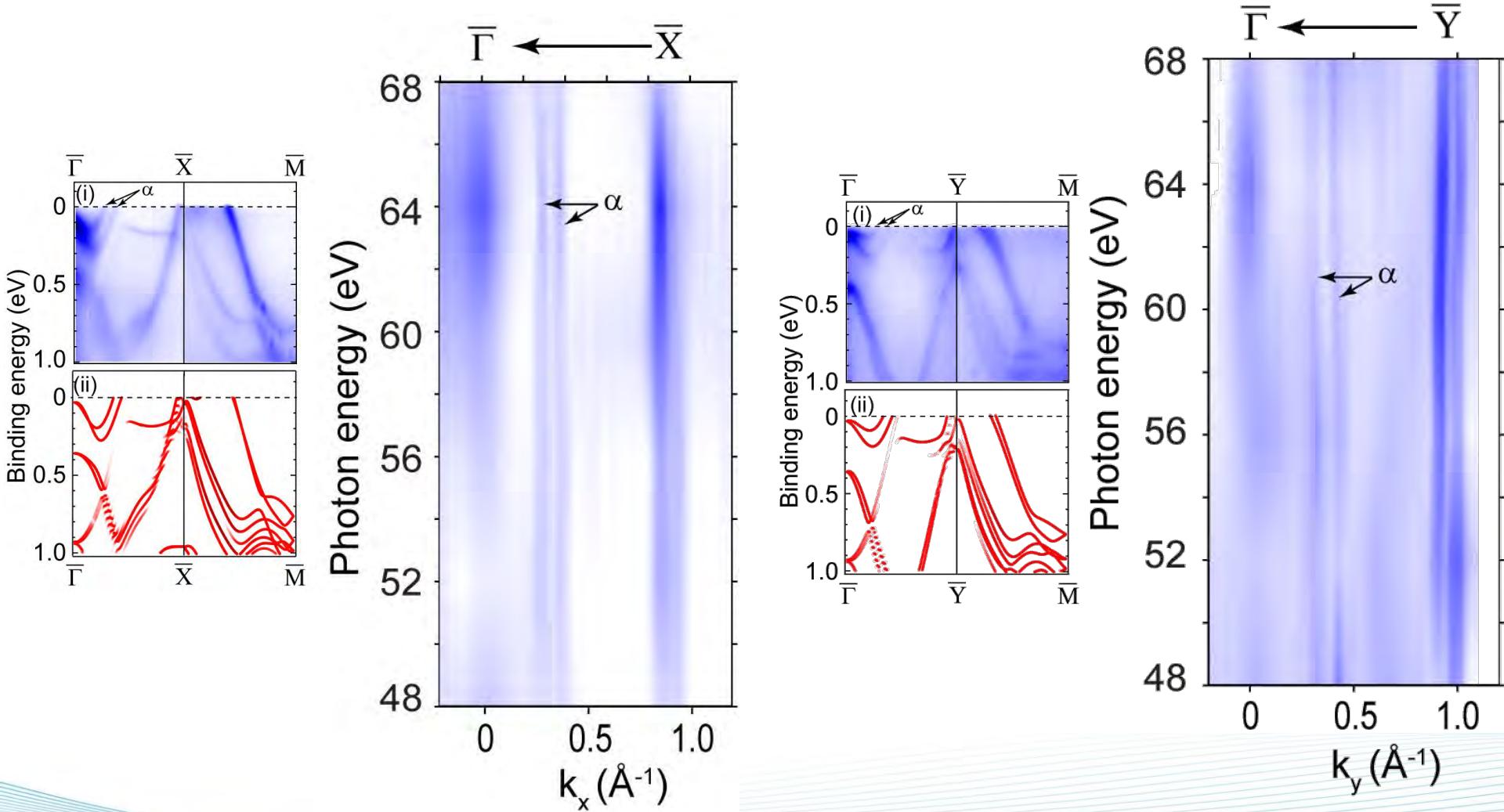
## Rich texture of the band structure



Low Intensity (a.u.) High Low Surface contribution High

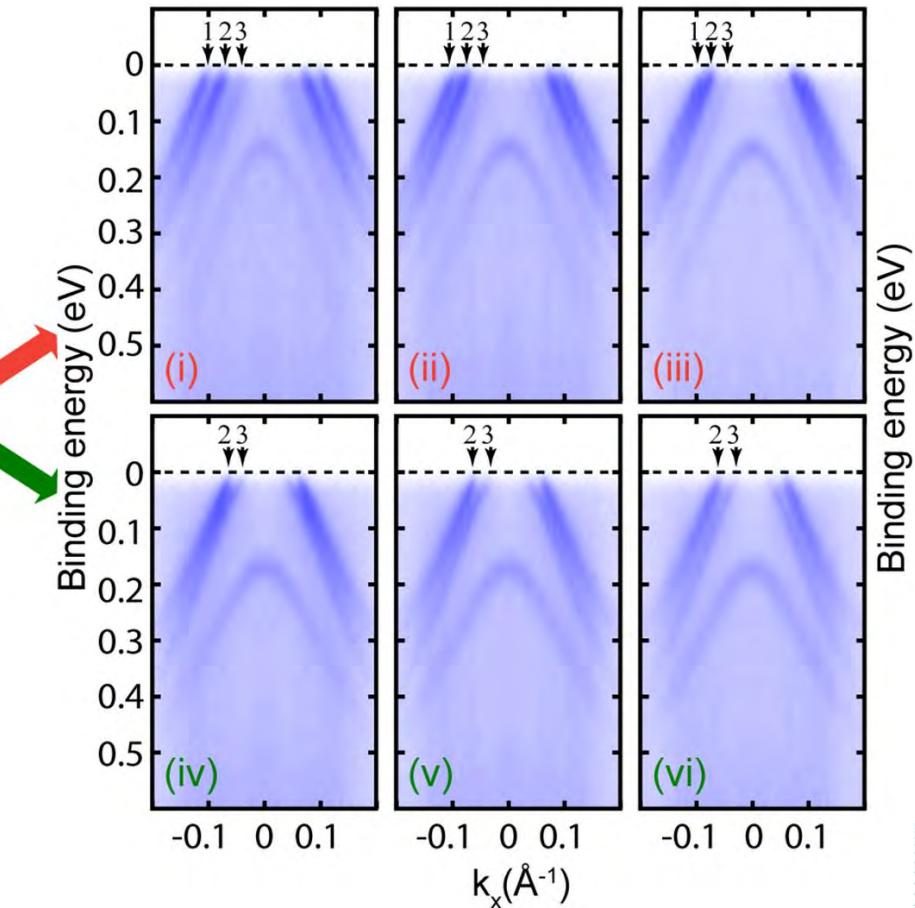
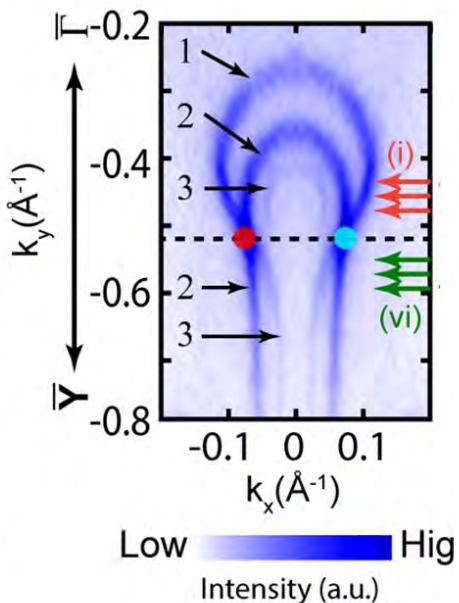
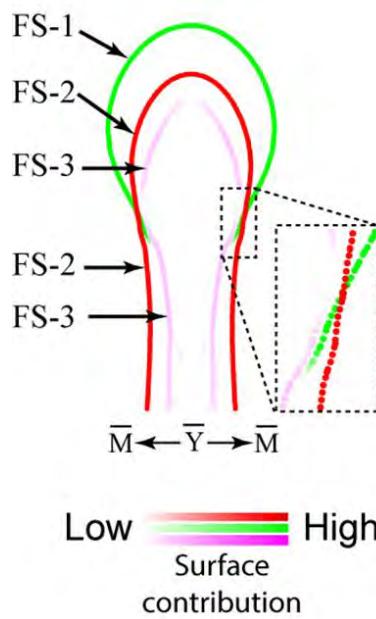
# 3D Topological Weyl Semimetal TaAs

Surface or bulk state?



# 3D Topological Weyl Semimetal TaAs

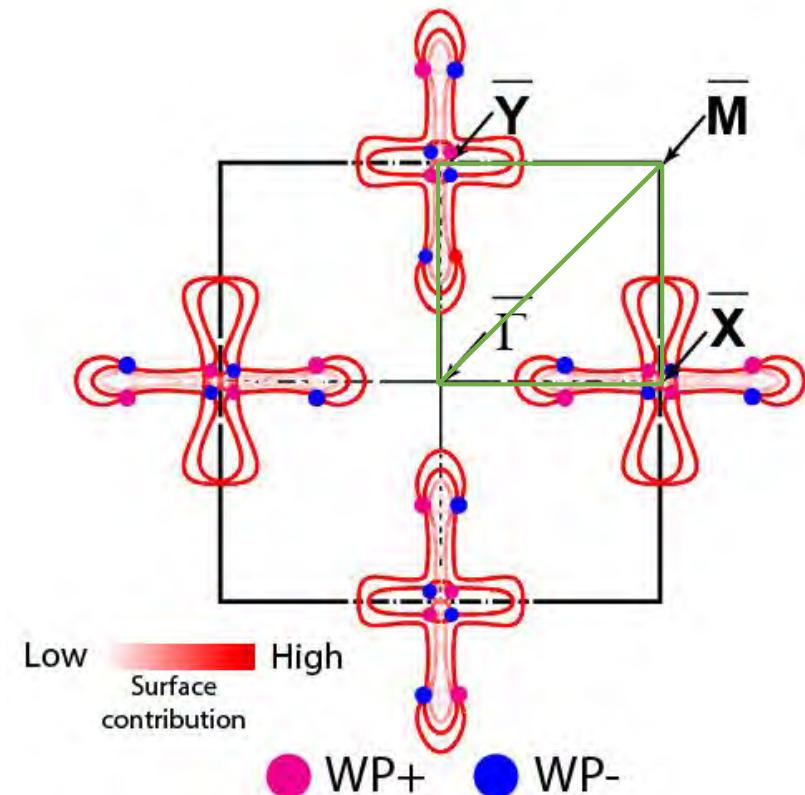
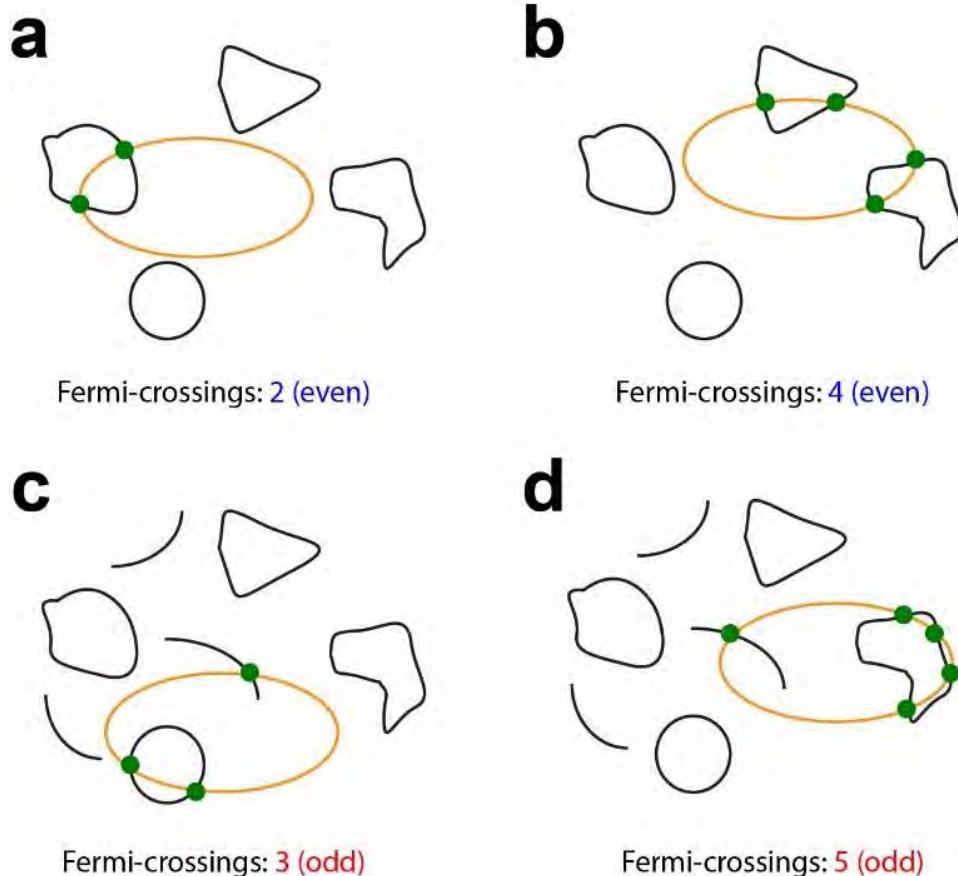
Identify the Fermi-arcs



# 3D Topological Weyl Semimetal TaAs

L. X. Yang, et. al., *Nature Physics*, 11, 728 (2015)

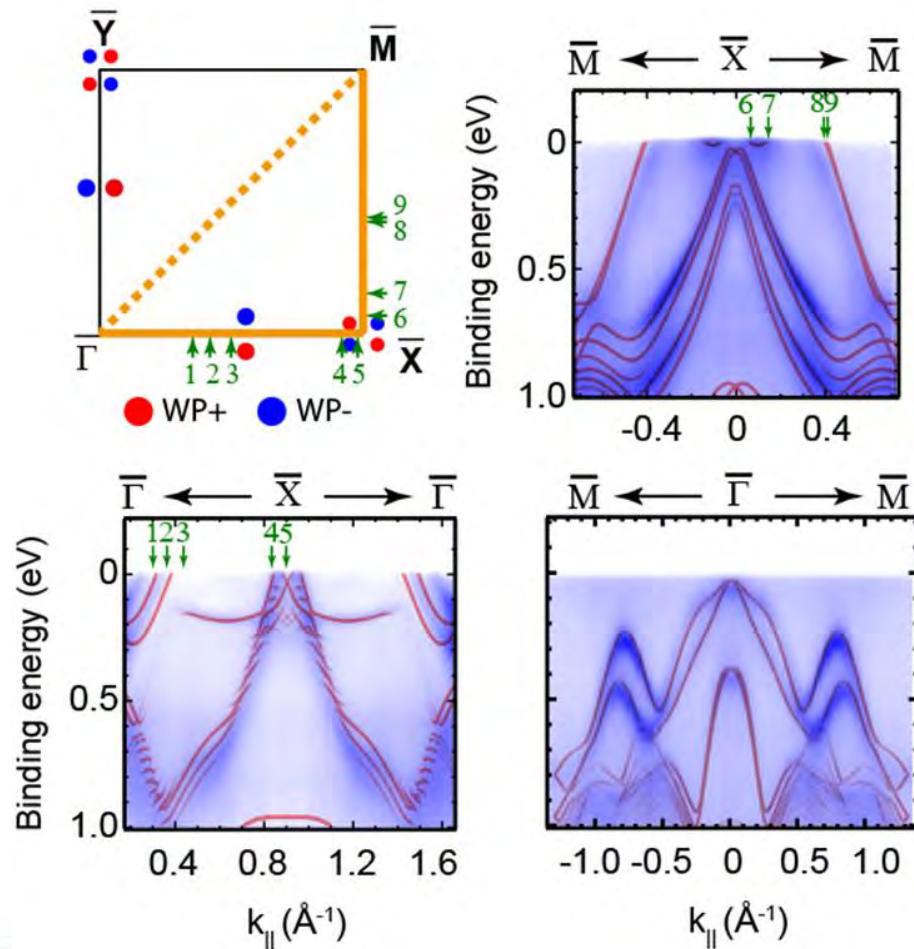
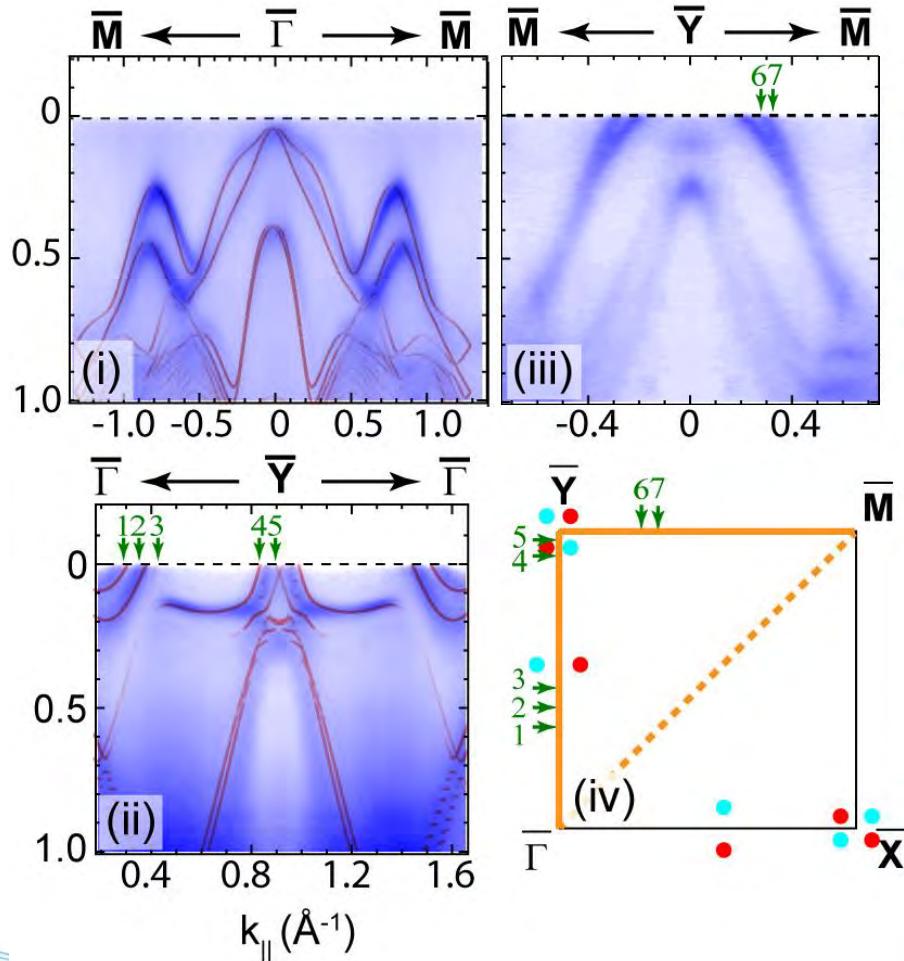
## Other Method to identify Fermi-arcs?



# 3D Topological Weyl Semimetal TaAs

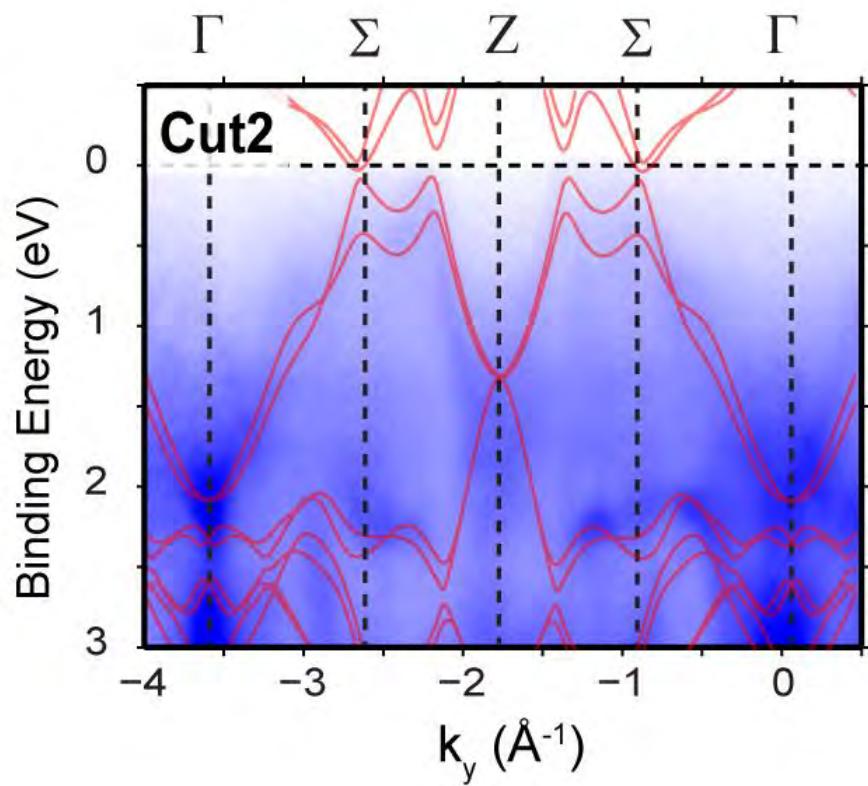
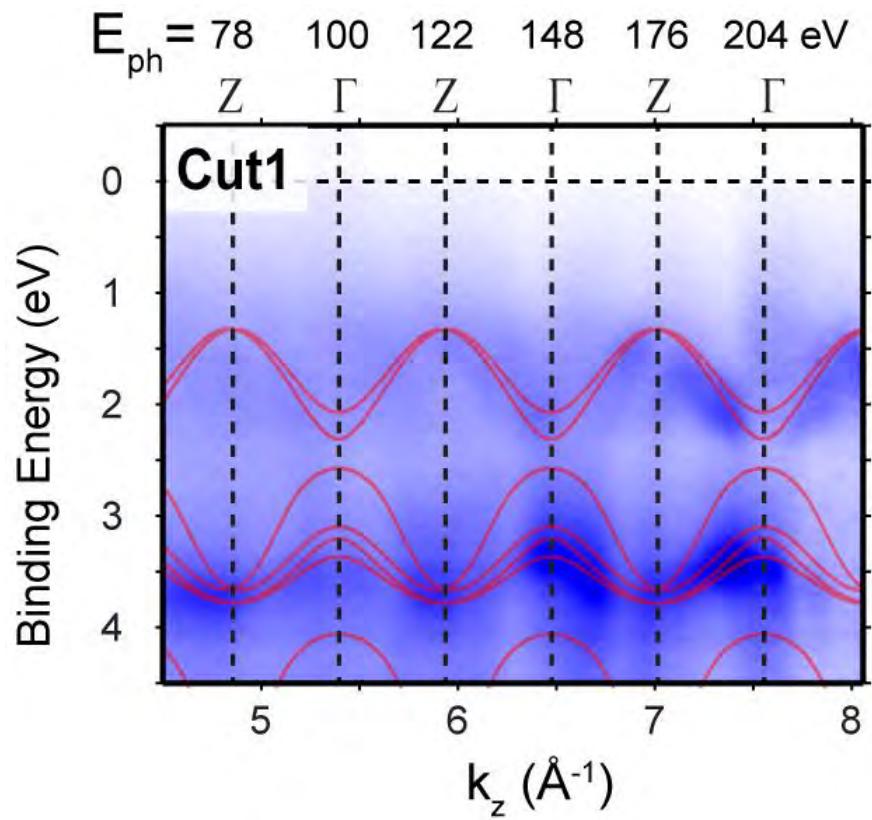
L. X. Yang, et. al., *Nature Physics*, 11, 728 (2015)

Fermi-crossings from two closed loops



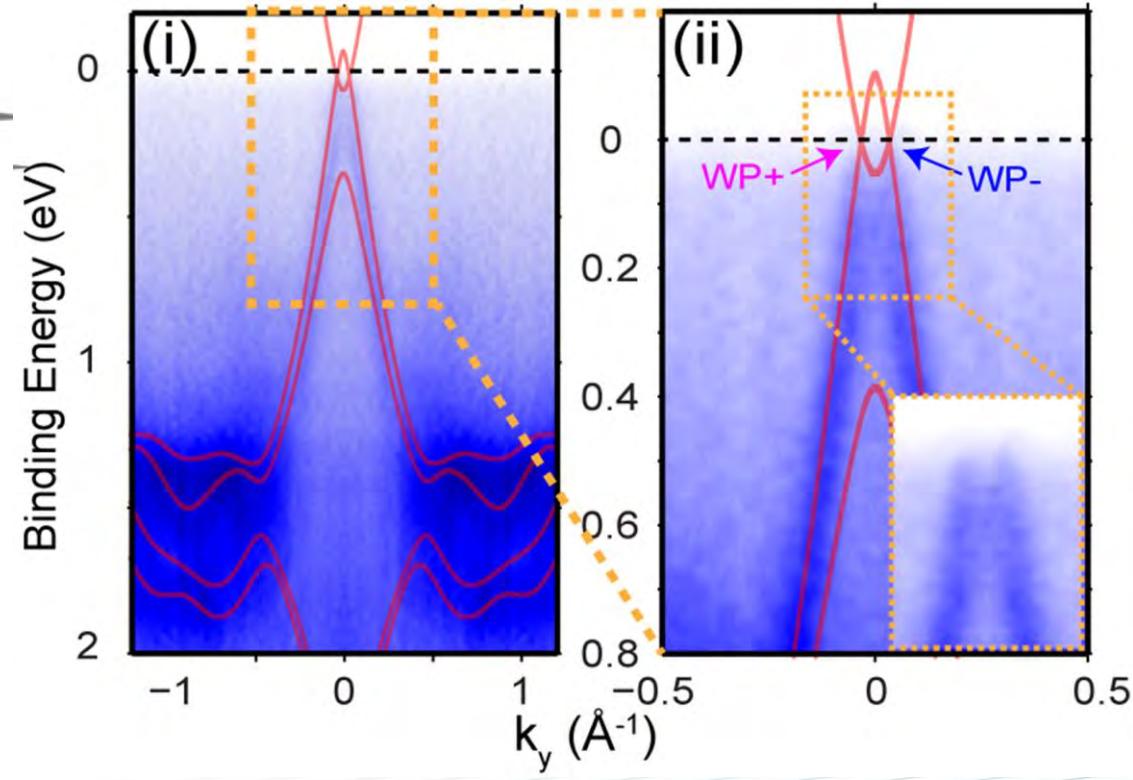
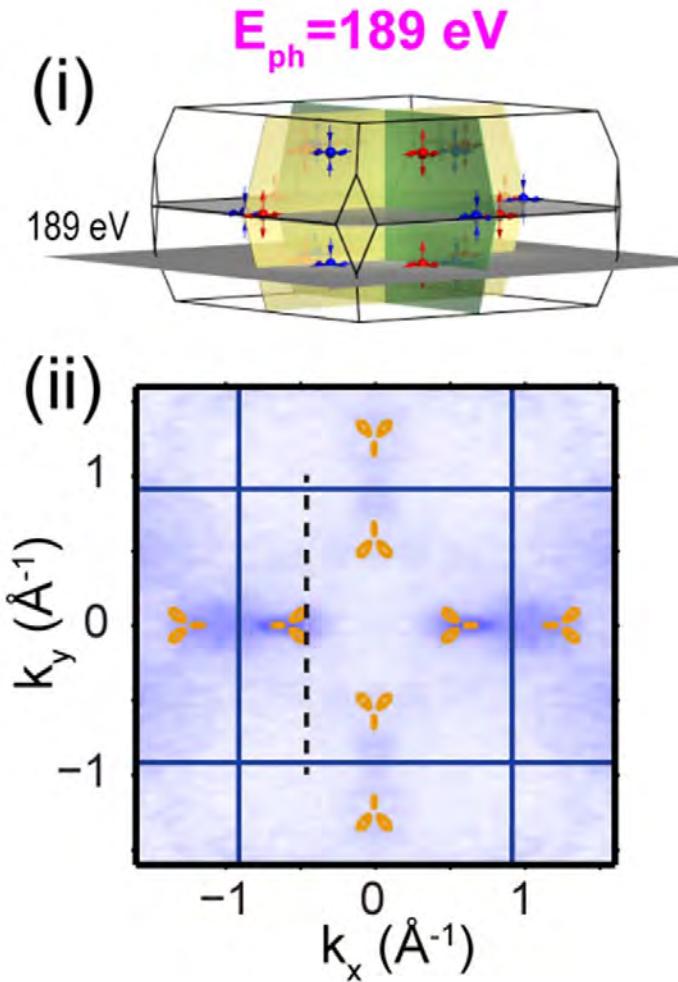
# 3D Topological Weyl Semimetal TaAs

Dispersions along  $k_z$  direction



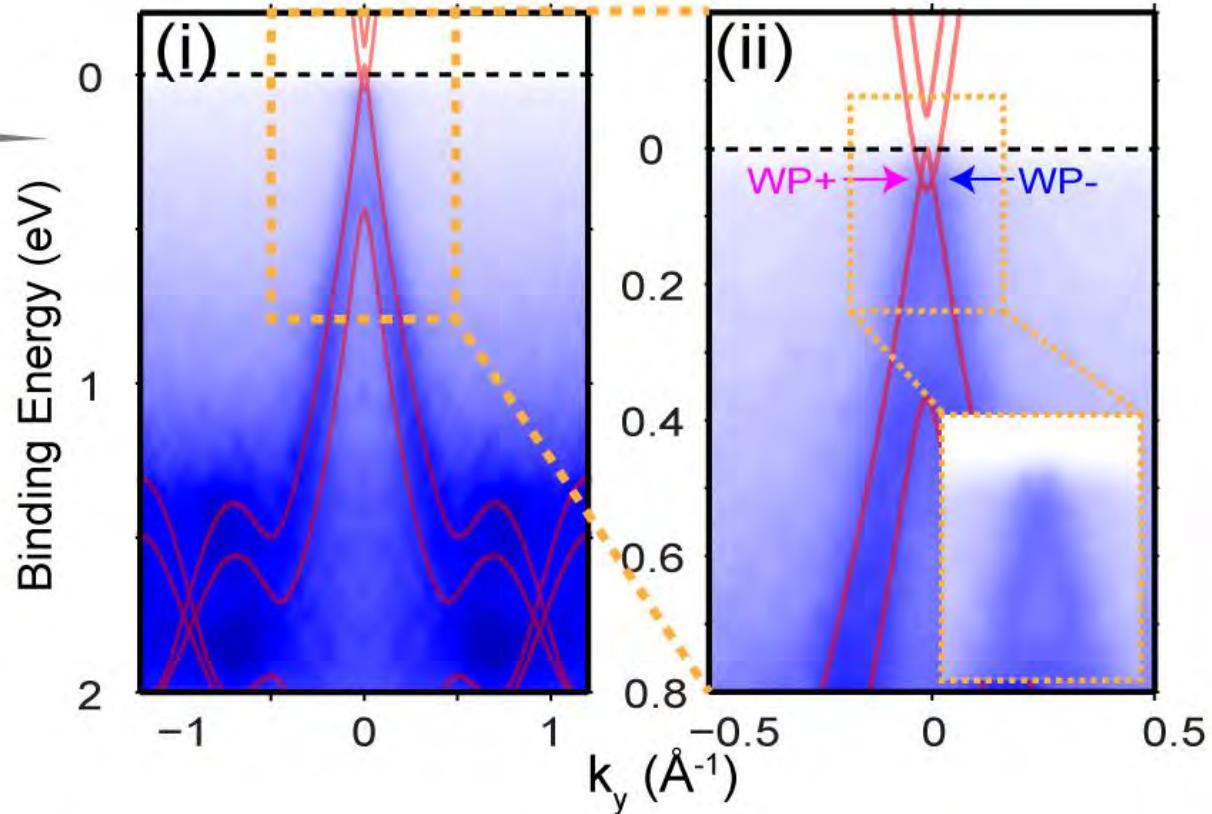
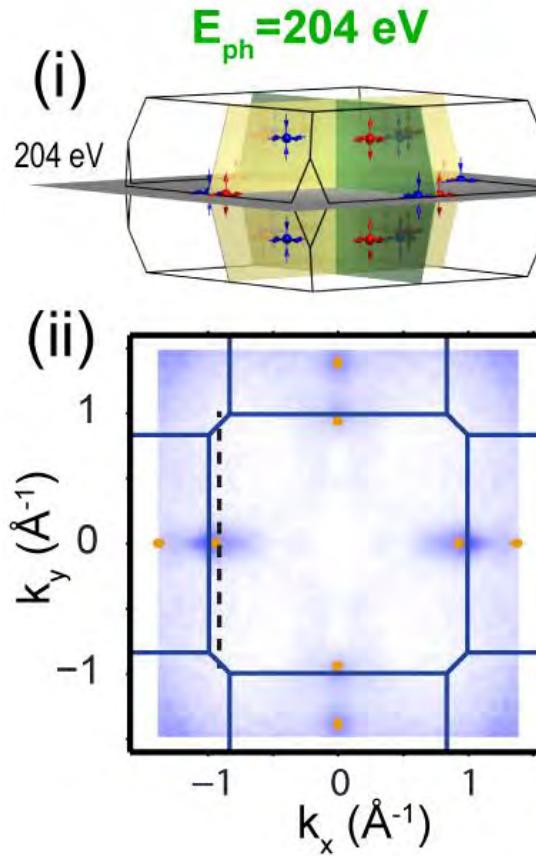
# 3D Topological Weyl Semimetal TaAs

Bulk dispersions near the Weyl points



# 3D Topological Weyl Semimetal TaAs

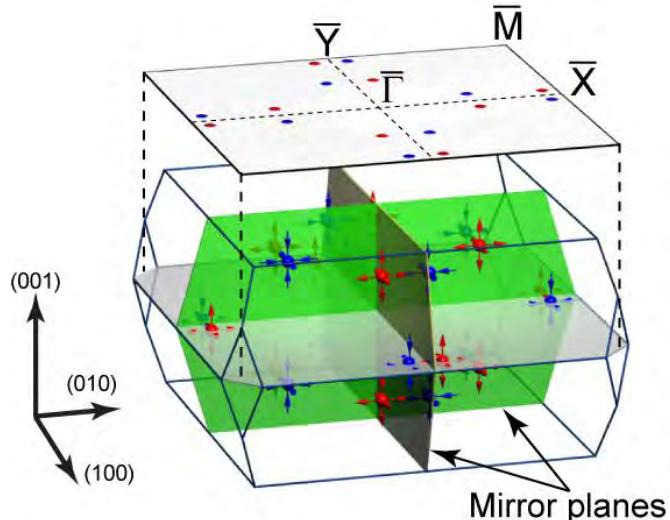
Bulk dispersions near the Weyl points



# Fermiology Evolution of Weyl Semimetals

Z. K. Liu, et. al., *Nature Materials*, 15, 27 (2016)

## Evolution of band structure of different compounds



**NbP**

WP+  
WP+

**TaP**

WP+

**TaAs**

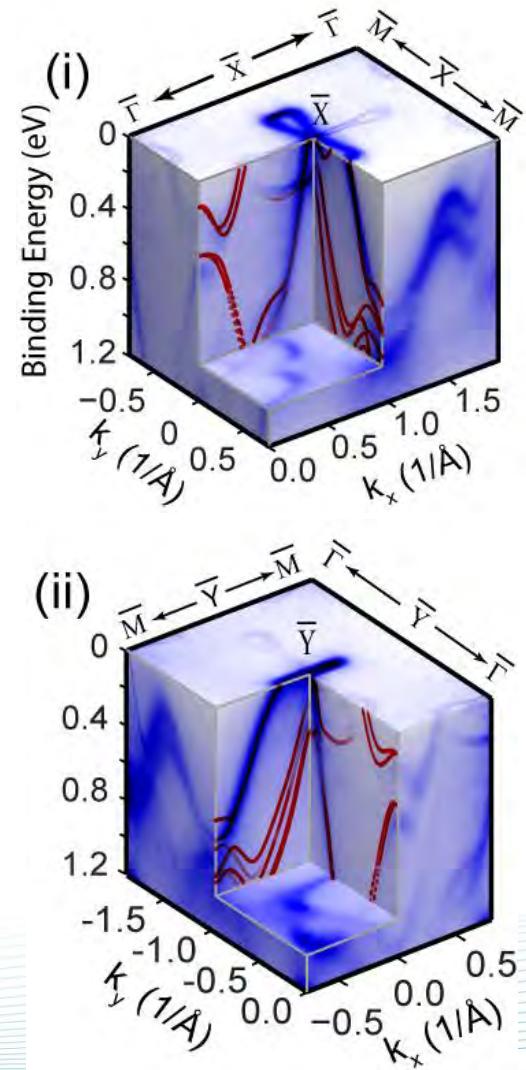
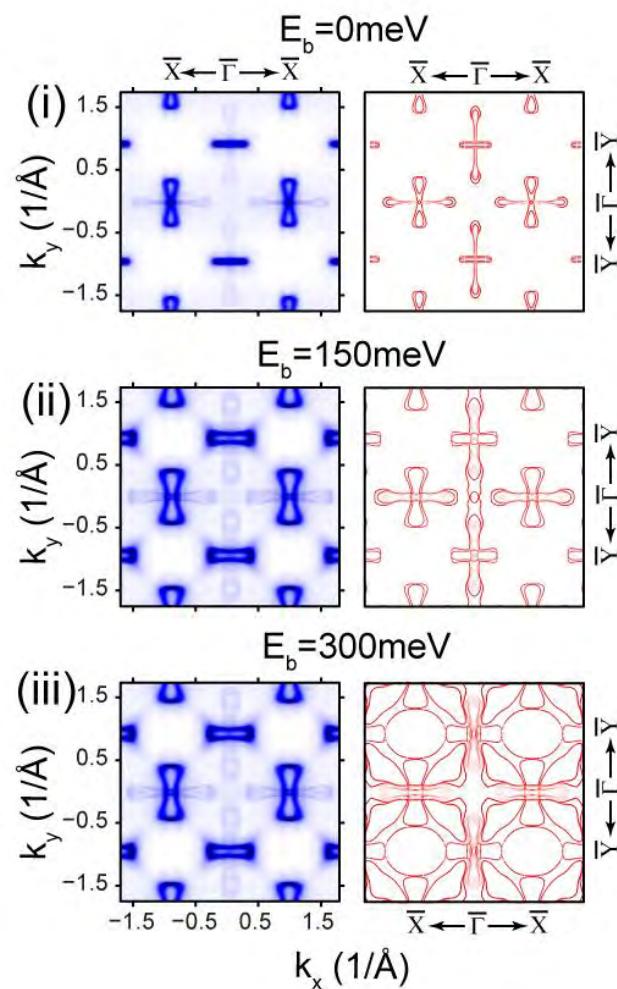
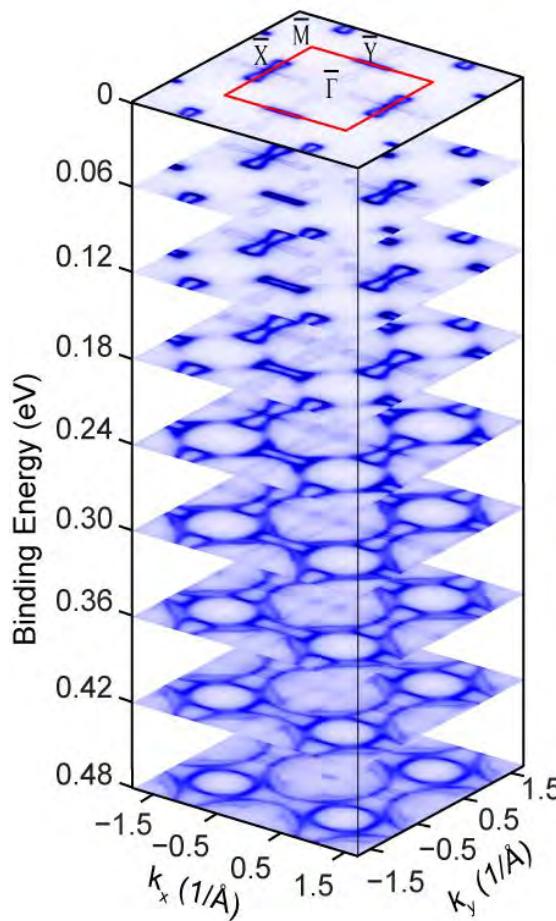
WP+

Increasing SOC

# Fermiology Evolution of Weyl Semimetals

Z. K. Liu, et. al., *Nature Materials*, 15, 27 (2016)

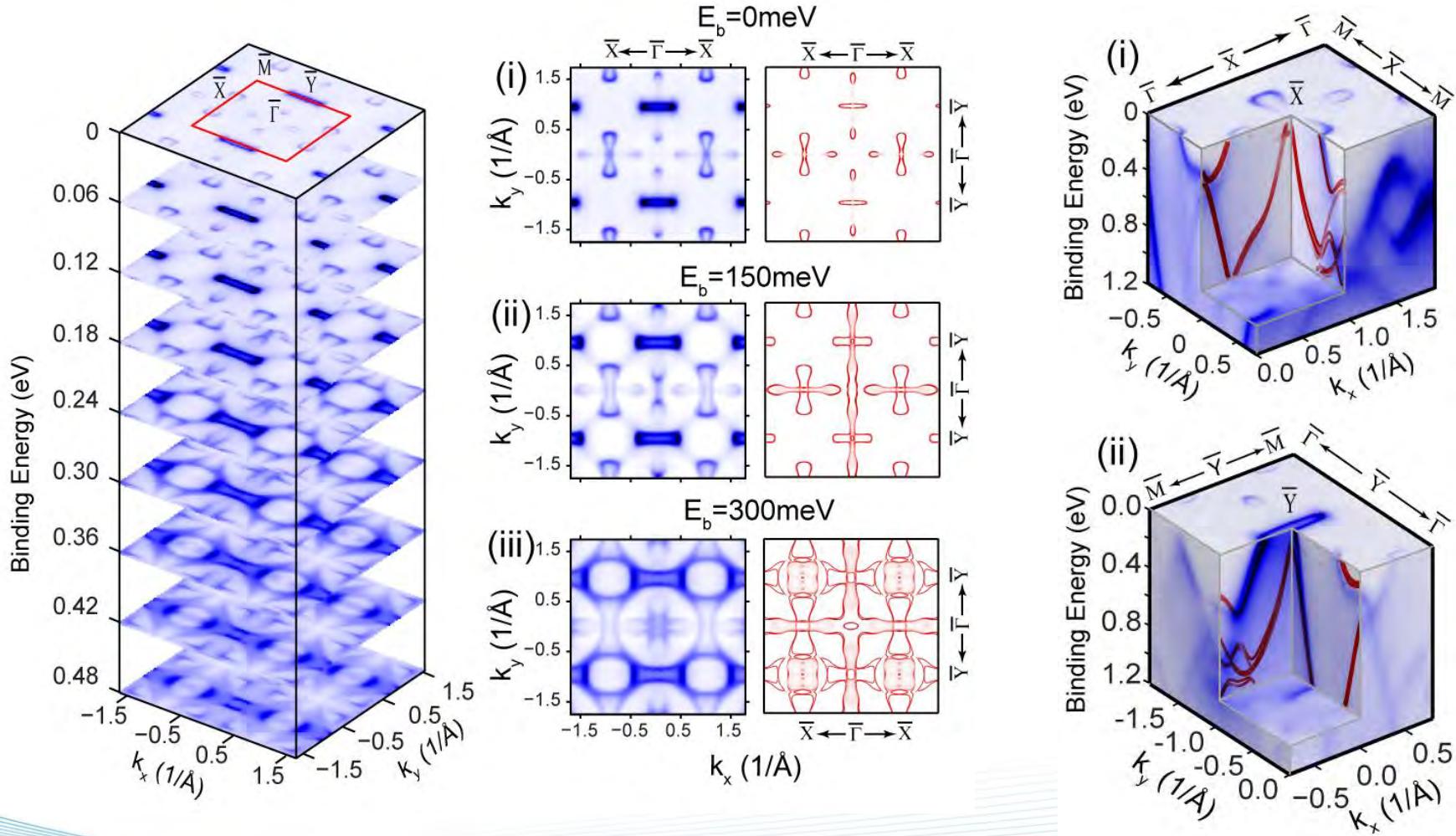
## Rich texture of the band structure of TaP



# Fermiology Evolution of Weyl Semimetals

Z. K. Liu, et. al., *Nature Materials*, 15, 27 (2016)

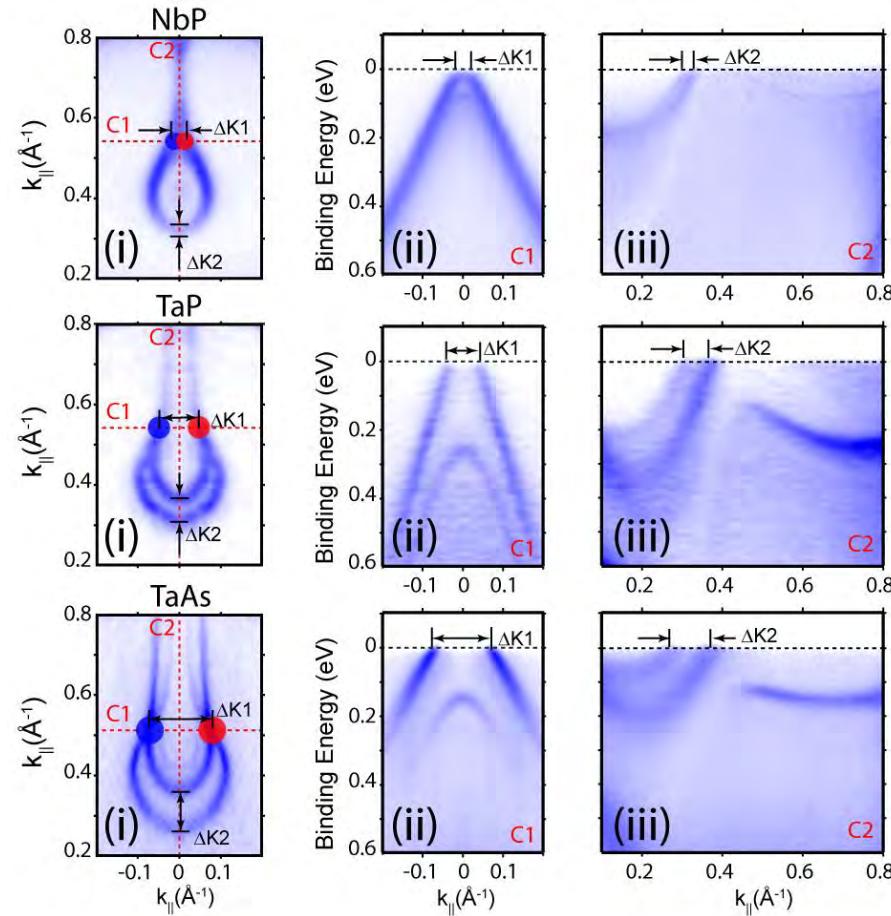
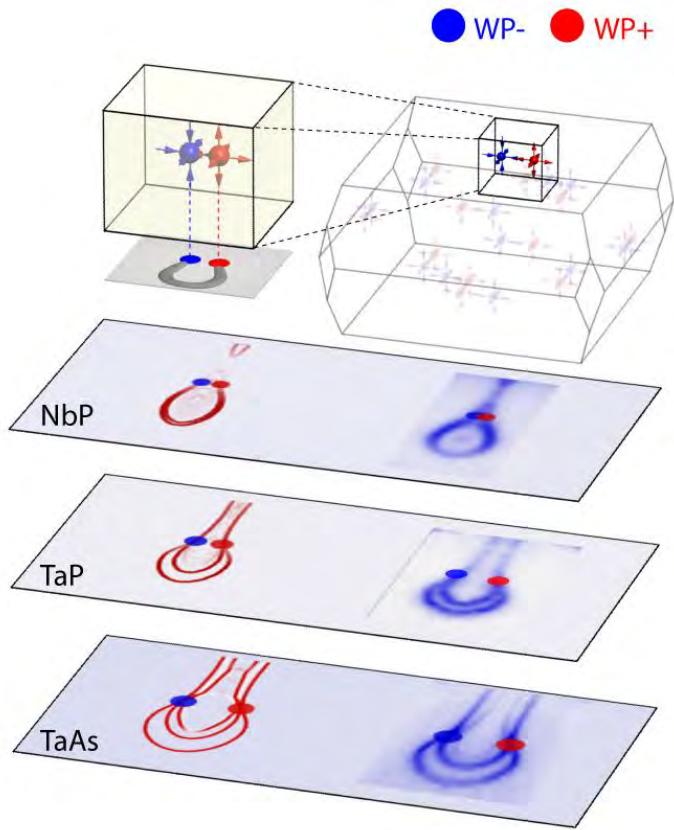
## Rich texture of the band structure of NbP



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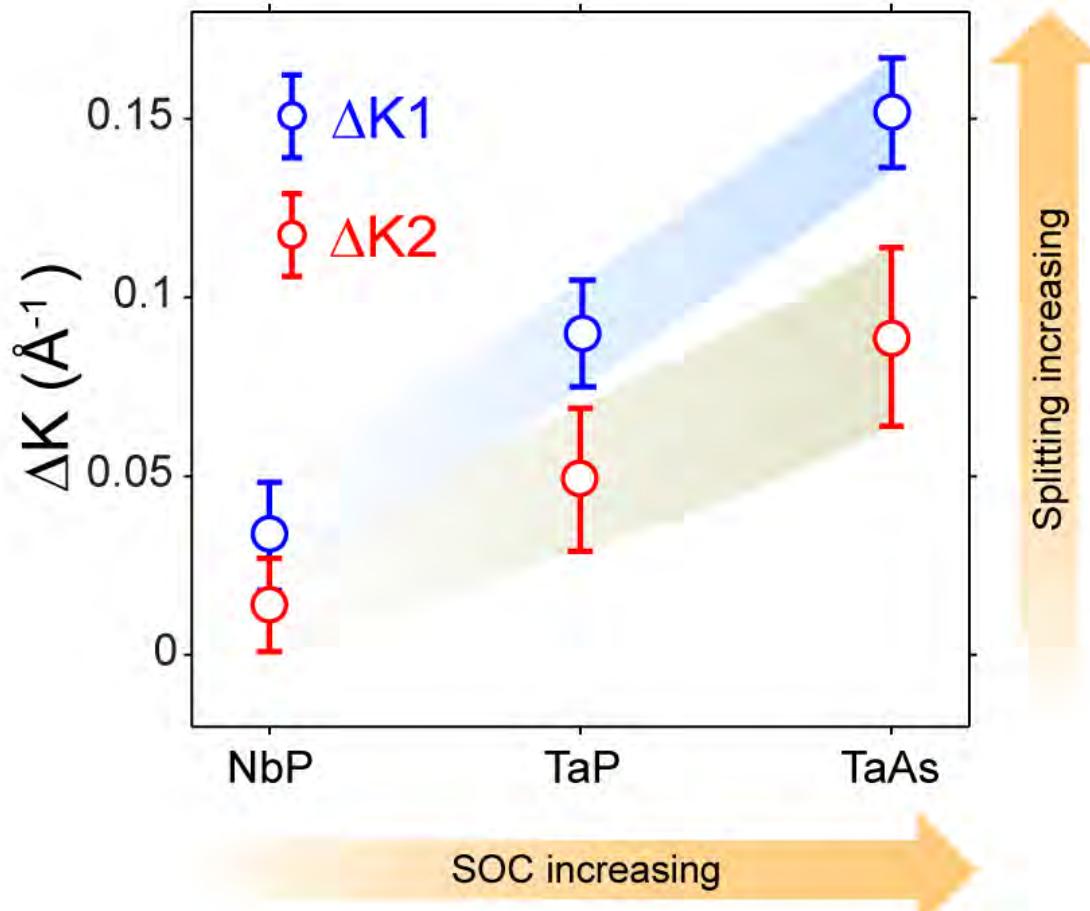
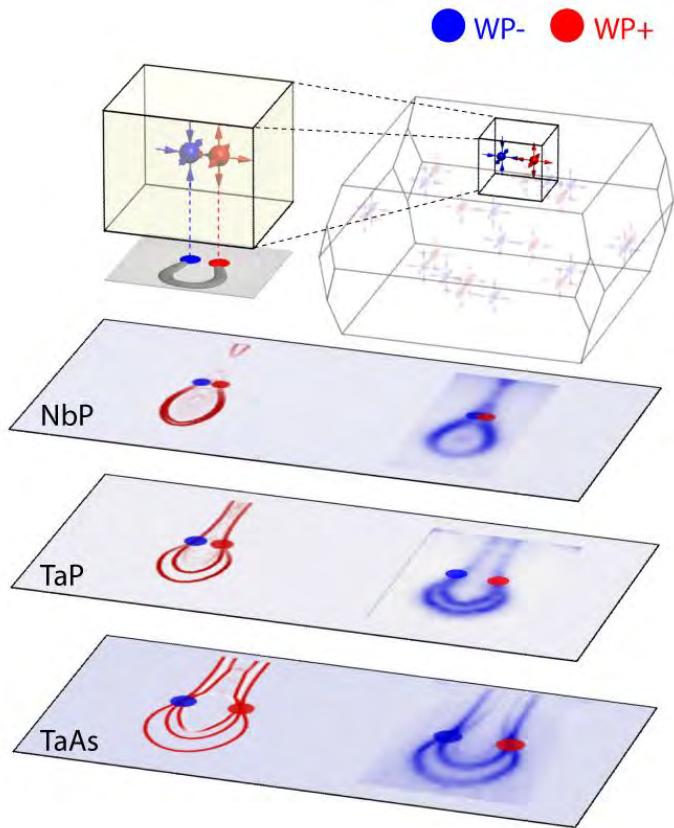
## Evolution of band structures with SOC



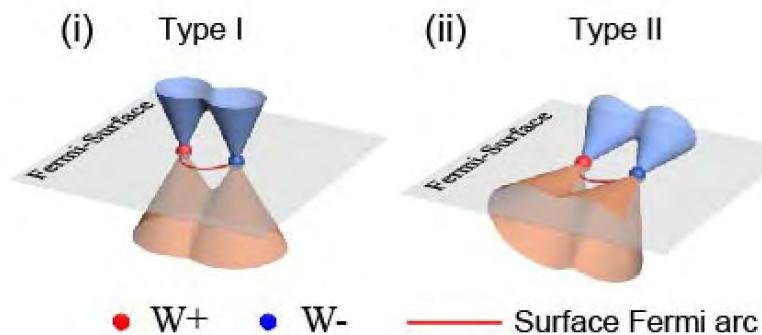
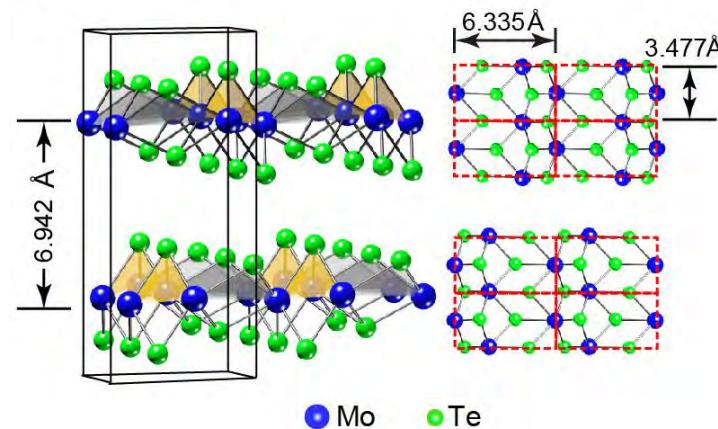
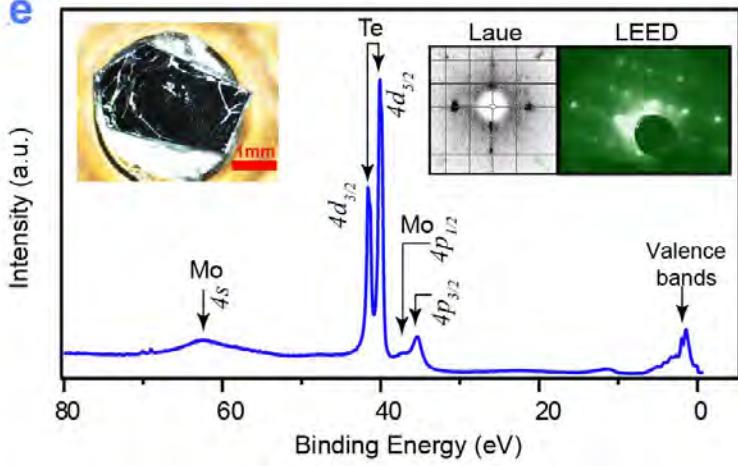
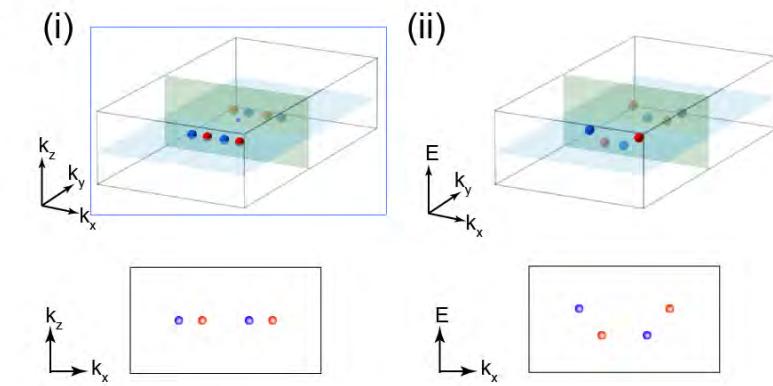
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Z. K. Liu, et. al., *Nature Materials*, 15, 27 (2016)

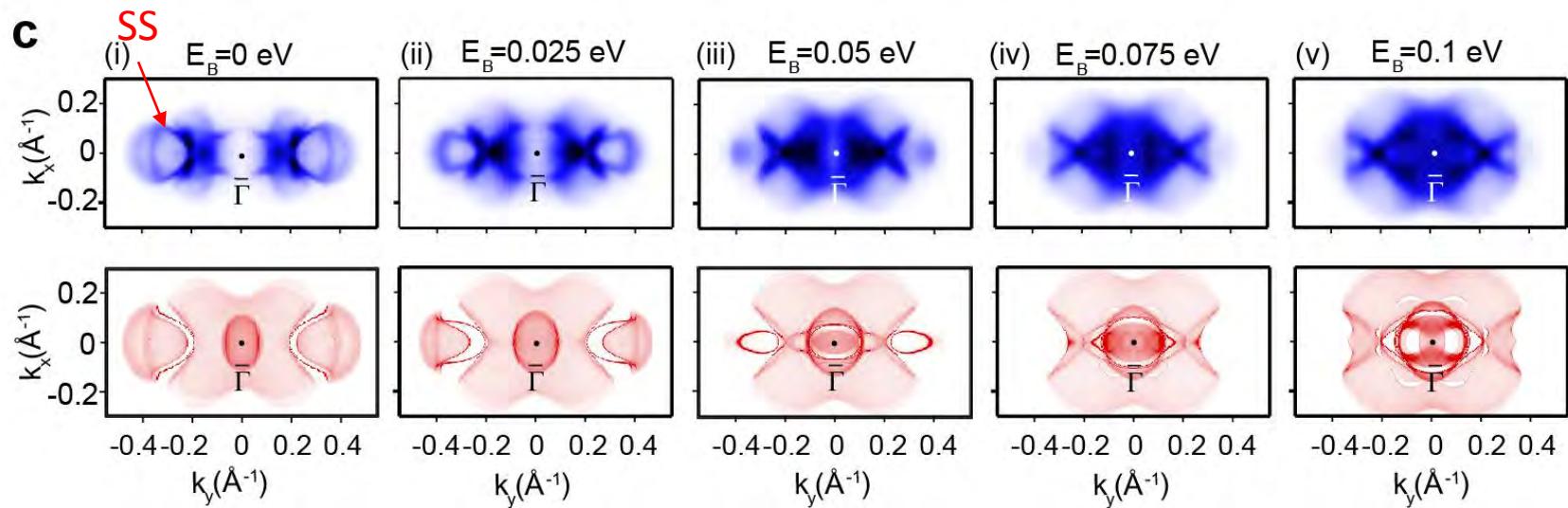
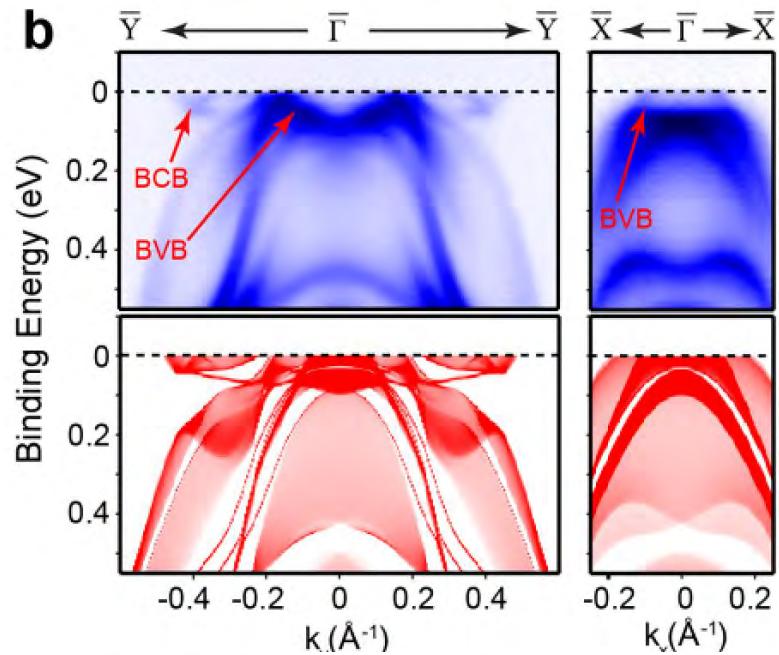
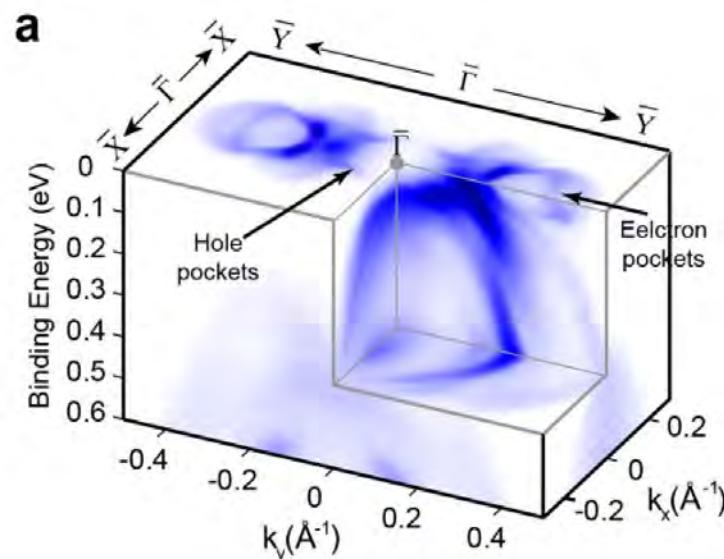
## Evolution of band structures with SOC



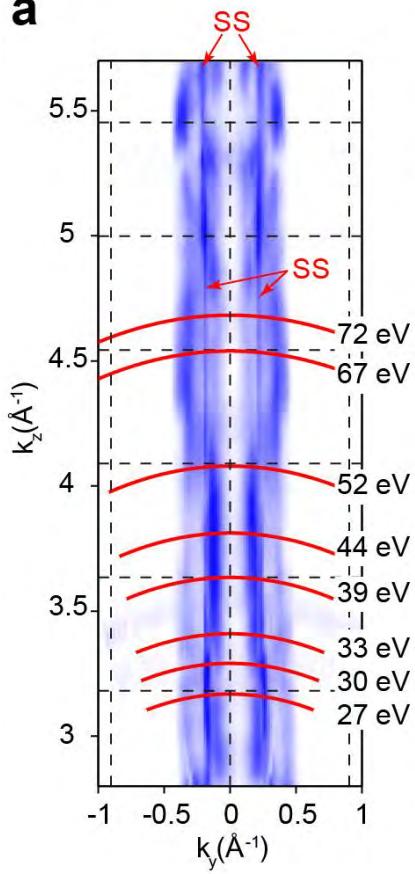
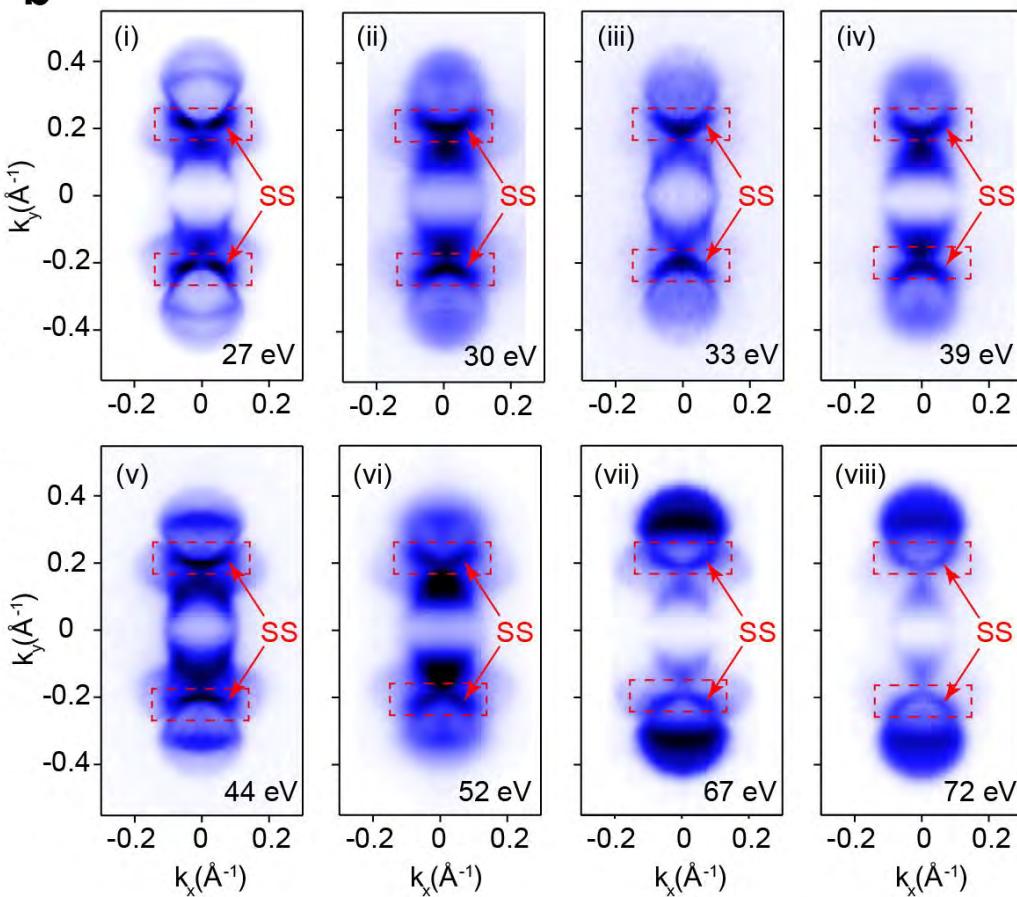
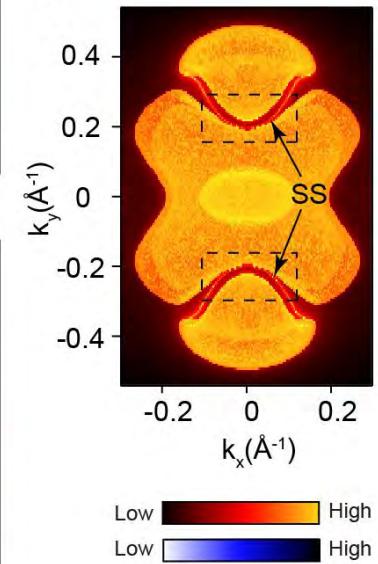
# $\text{MoTe}_2$ , a candidate for type II Weyl Fermion

**a****d****e****b**

# MoTe<sub>2</sub>, electronic structure



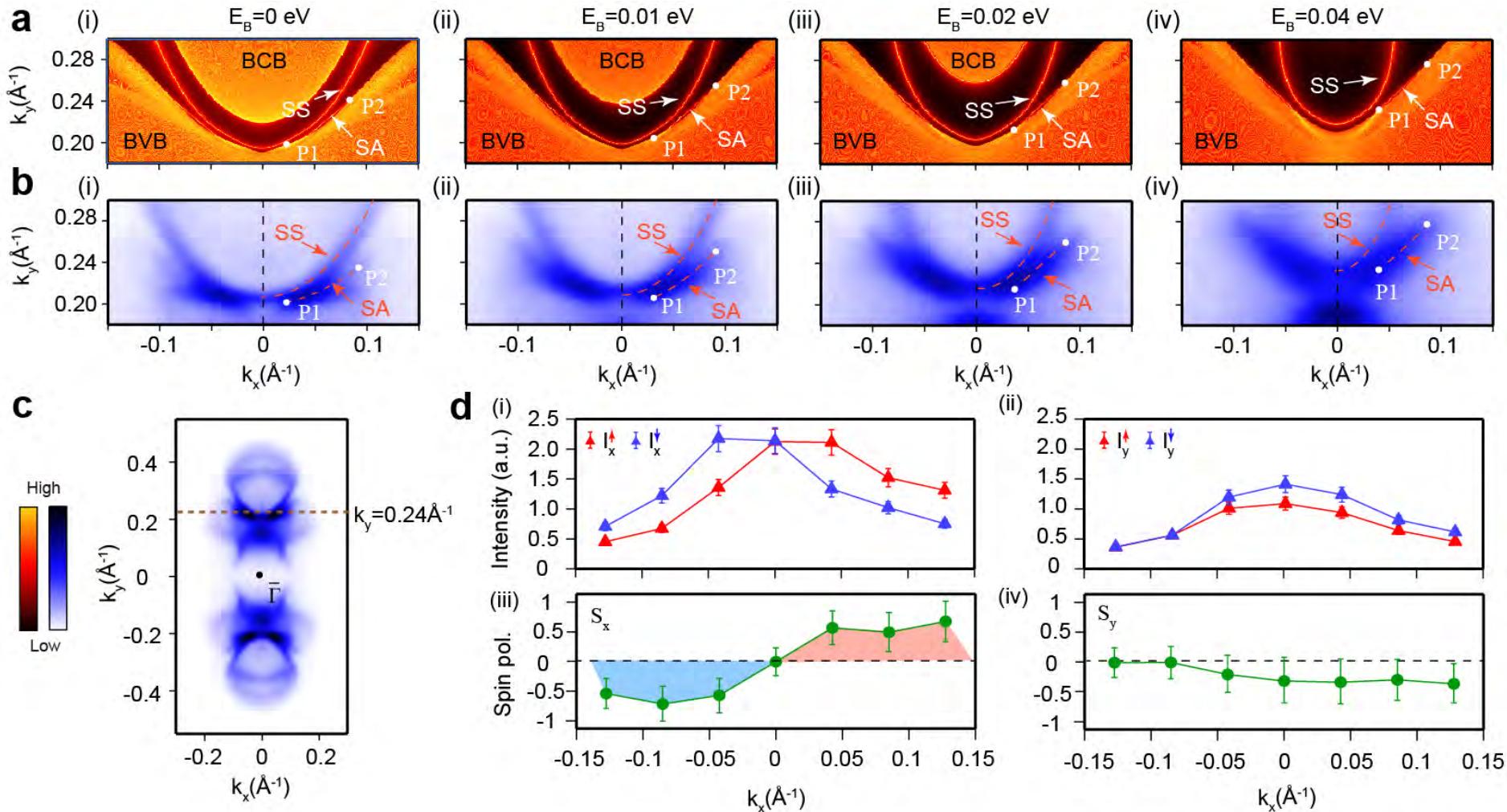
# Identification of the SS

**a****b****c**

Low  
High

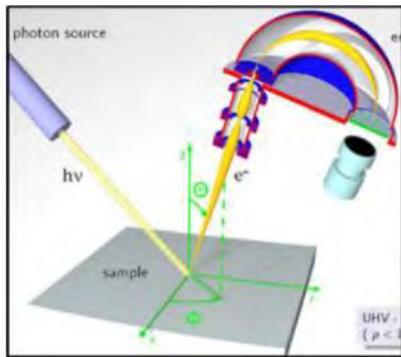
Low  
High

# MoTe<sub>2</sub>, Signature of the Fermi Arc feature

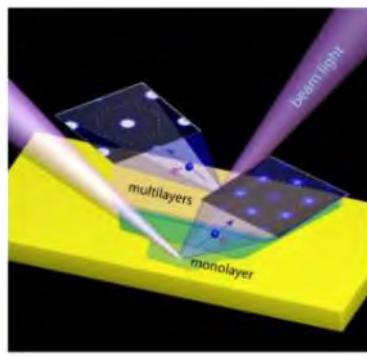


# Multi-dimension ARPES technique

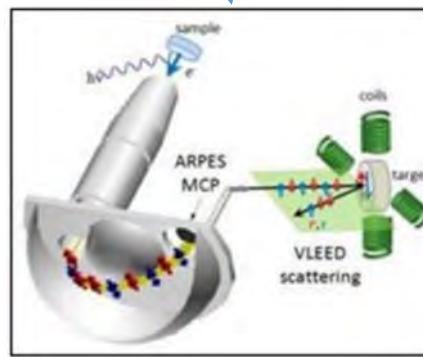
$$f(k, E, r, \sigma, t)$$



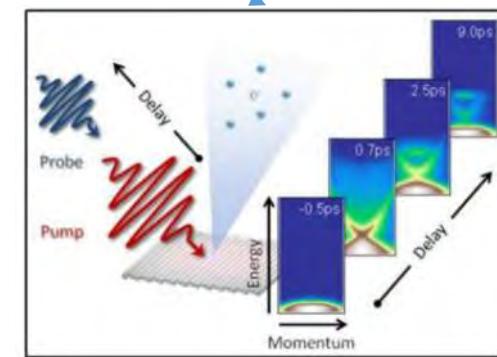
ARPES



Spatial  
Resolved  
ARPES

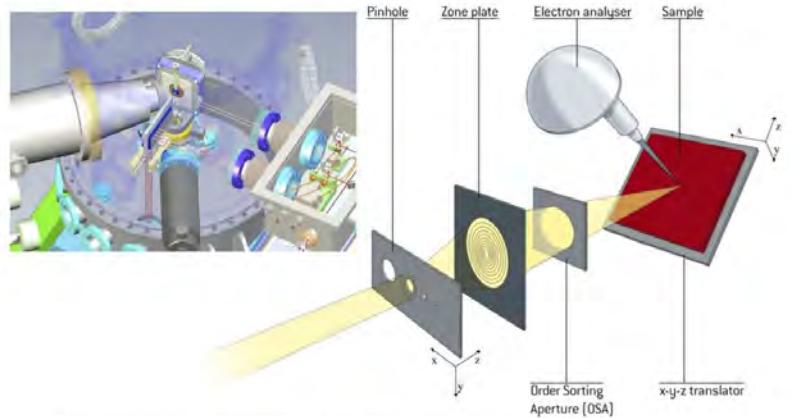


Spin  
Resolved  
ARPES



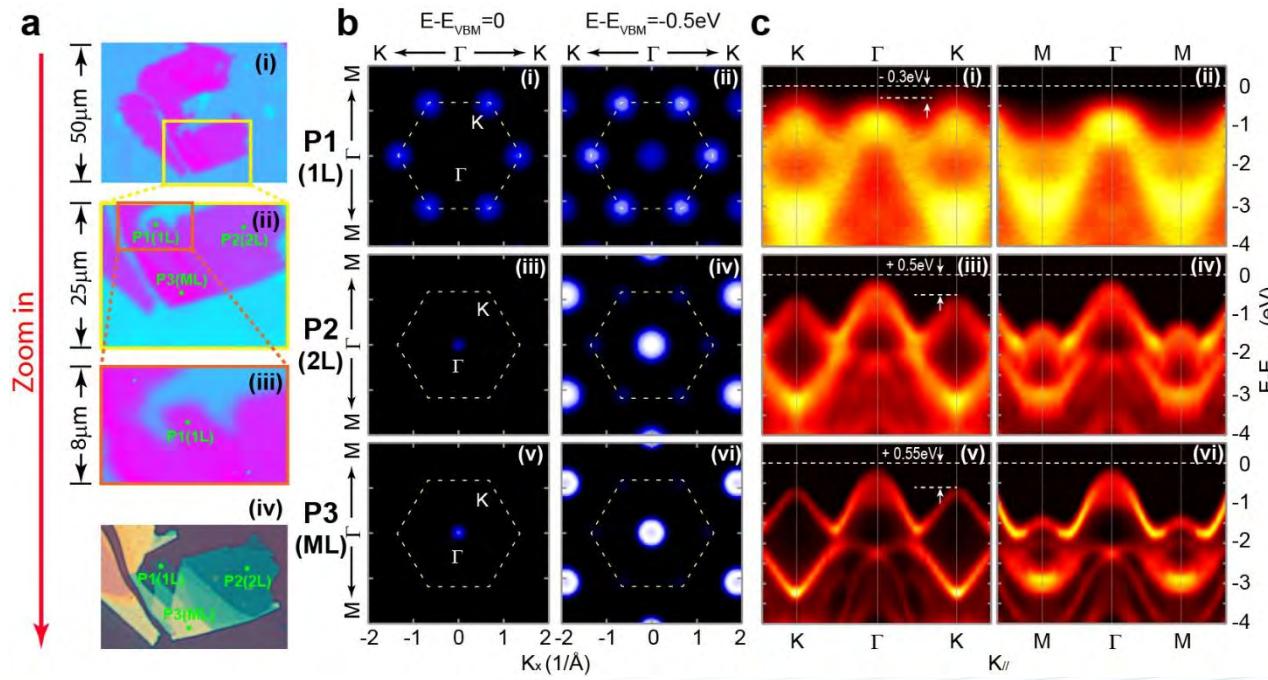
Time  
Resolved  
ARPES

# Spatial Resolved Photoemission (NanoARPES)

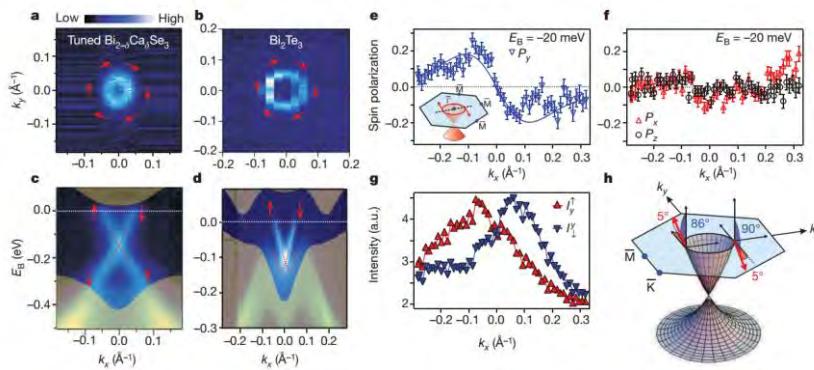


A. Bostwick et al.,  
Synchrotron radiation  
news, Vol. 25, No. 5,  
2012

Figure 2: A schematic of the internal workings of the SOLEIL nanoARPES. The figure illustrates the general principles of ZP focusing.

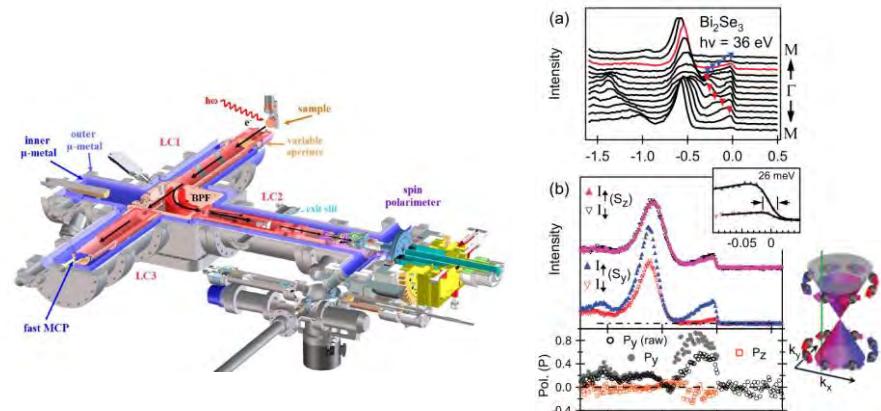


# Spin Resolved Photoemission (SpinARPES)



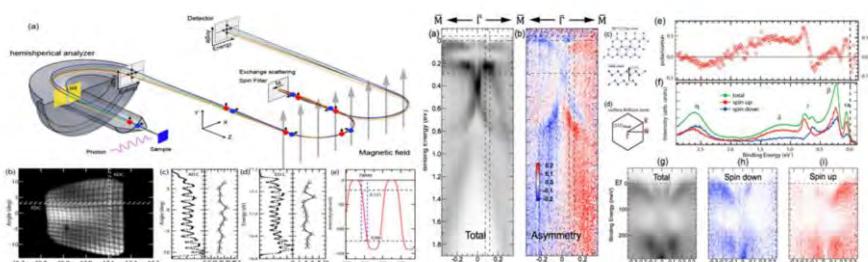
D. Hsieh et al., Nature 460, 1101-1105 (2009)

**0D, Mott Detector**



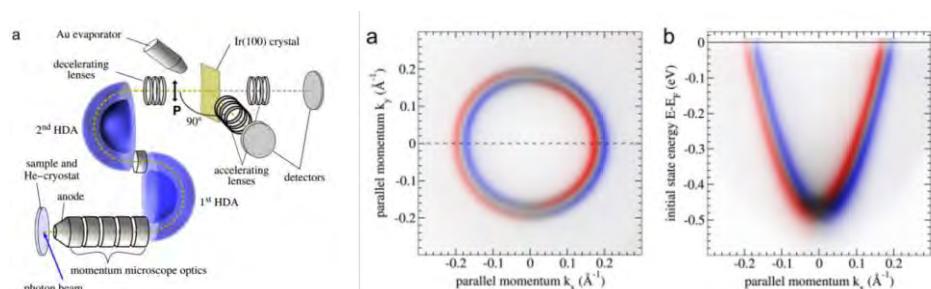
C. Jozwiak, et. al., Phys. Rev. B. 84, 165113 (2011)

**1D, Exchange scattering**



**2D, Multi-channel exchange scattering**

F. Ji et al., Phys. Rev. Lett. 116, 177601 (2016)

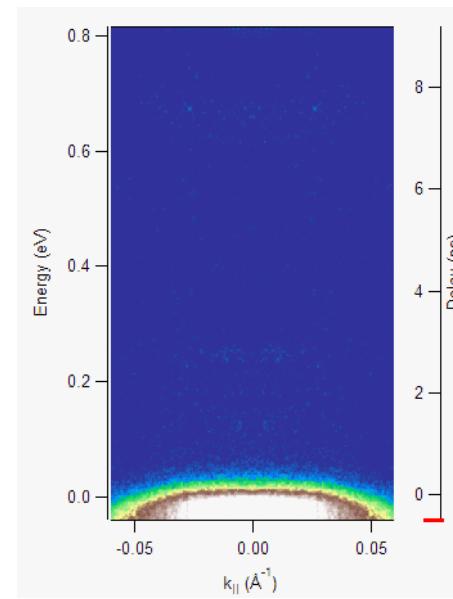
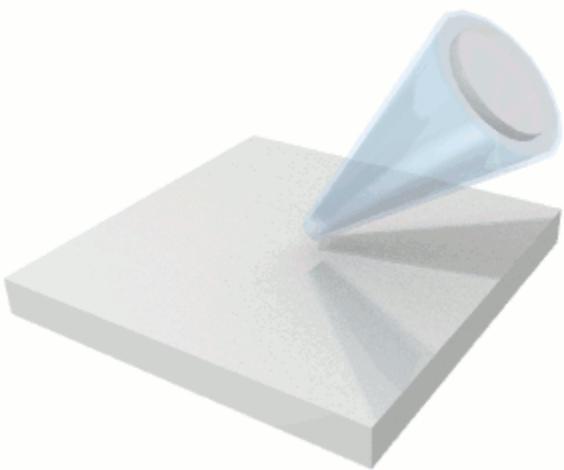


**2D, PEEM+VLEED**

C. Tusche, et al., Ultramicroscopy, 159, 520 (2015)

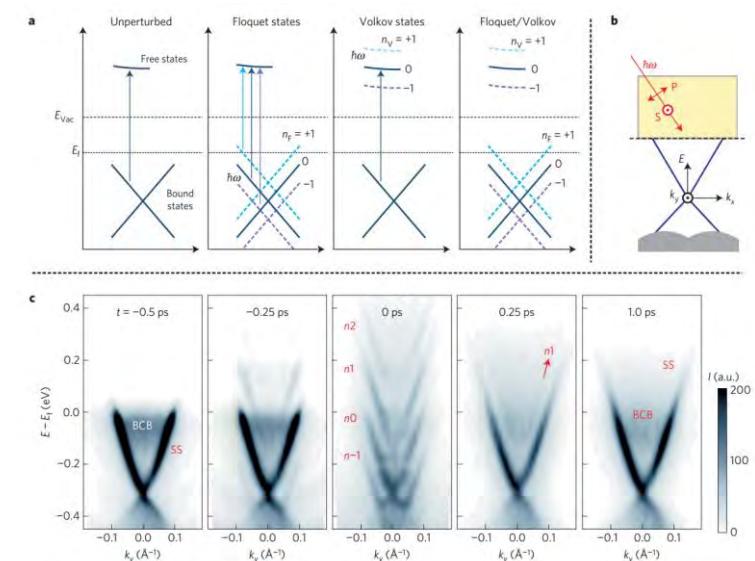
# Time Resolved Photoemission

## Ultrafast Dynamics of the Surface States in $\text{Bi}_2\text{Se}_3$



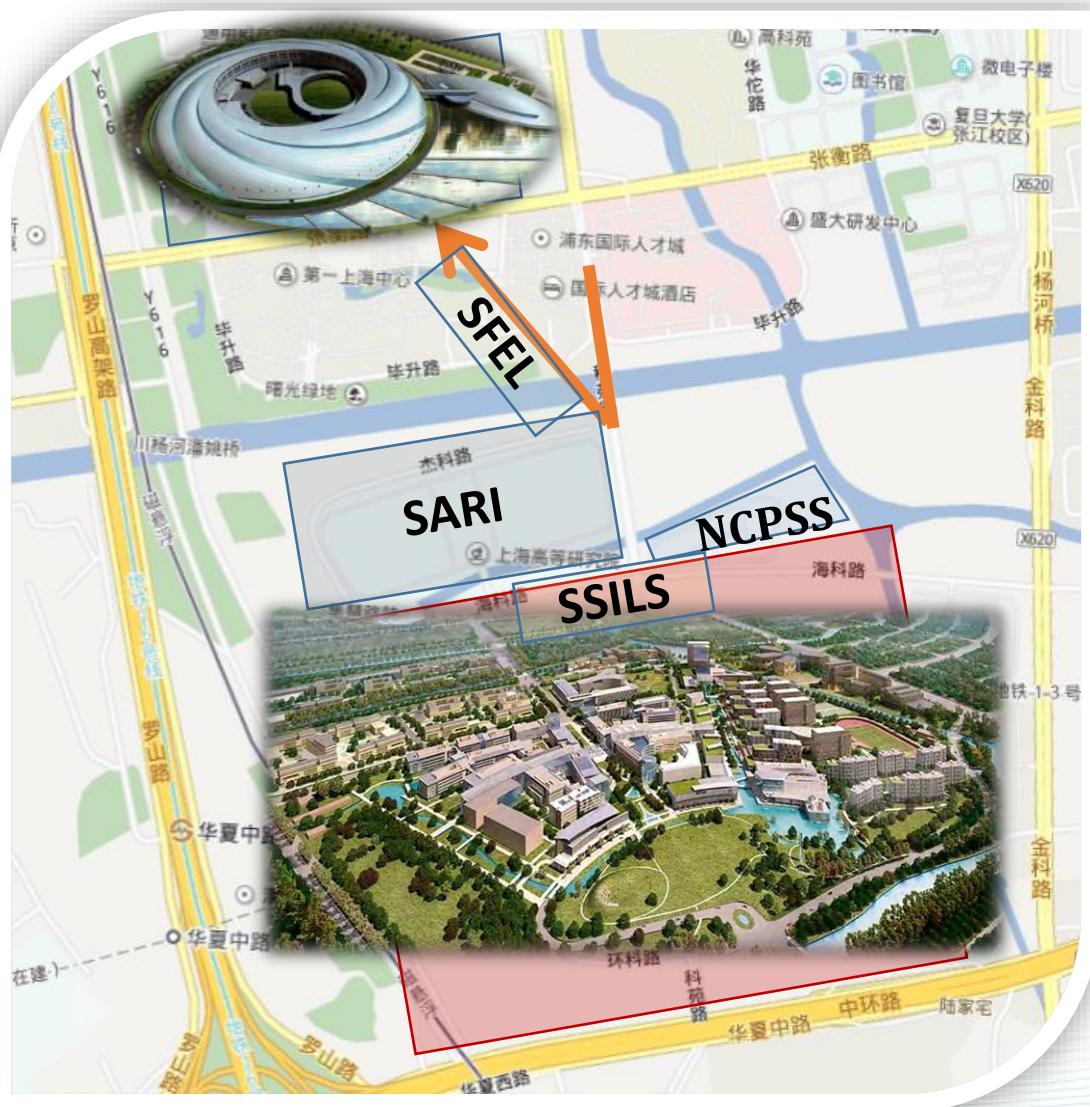
J. A. Sobota et al., Phys.  
Rev. Lett. 108, 117403  
(2012)

## Floquent Surface States in $\text{Bi}_2\text{Se}_3$



F. Mahmood et al.,  
Nature Physics 12, 306–310 (2016)

# ShanghaiTech University



- Located in Pudong, Shanghai
- 30 mins from Pudong International Airport
- 2 kms away from Shanghai Synchrotron
- At the heart of national science facilities
  
- Founded by the Shanghai Government and Chinese Academy of Science in 2013
- Small Scale, Research Oriented University

**SSRF: Shanghai Synchrotron Radiation Facility**

**SFEL: Shanghai Free Electron Laser**

**SSILS: Shanghai Super Intense Laser Source**

**SARI: Shanghai Advanced Research Institute**

**NCPSS: National Center for Protein Science**

# Division of Condensed Matter Physics and Photon Science

## Interface and Photon Science



+ 6 Adj.  
Prof.

ME<sup>2</sup> BL

## Quantum Material



+ 1 Adj.  
Prof.

S<sup>2</sup> BL

## Theory



Local Clusters,  
Super Comp.  
Center

## Photon Sci. Joint Lab



王美晓

## SSILS Joint Lab



姜甲明

## SIMIT Joint Lab



宋艳汝

## Project Management



Lei Shi

**SSI**LS  
S<sup>2</sup> BL  
S-XFEL

Detector  
Initiatives

**SSI**LS

**S-XFEL**  
Detector  
Initiatives

# Current major projects

- **ME<sup>2</sup> (Materials for Energy and Environment) beamline project at SSRF**
- **S<sup>2</sup> beamline (Spatially and Spin resolved ARPES beamline) at SSRF**
- **Shanghai Super Intense Laser Source (SSILS) at ShanghaiTech University**
- **S-XFEL User Facility Upgrade**



**ME<sup>2</sup>beamline  
(SIMIT, SSRF)**



**S<sup>2</sup> beamline  
(SSRF)**



**SSI LS**



**Shanghai - FEL**

# Thank you and Welcome to Shanghai

